

# TPS546B24A 2.95V~18V、20A、最大 4× スタックブル、PMBus® 降圧コンバータ

## 1 特長

- 分割レールをサポート: PVIN: 2.95V~18V、AVIN: 2.95V~18V (スイッチングのために VDD5 に 4V を入力する場合)
- 5.5mΩ/1.8mΩ の MOSFET を内蔵
- 選択可能な内部補償付きの平均電流モード制御
- 2×、3×、4× スタック可能で最大 80A の電流共有、出力ごとに 1 つのアドレスをサポート
- 選択可能な出力: ピン・ストラップで 0.5V~5.5V、または PMBus の VOUT\_COMMAND を使用して 0.25V~5.5V
- 豊富な PMBus コマンド・セット、V<sub>OUT</sub>、I<sub>OUT</sub>、および内部ダイ温度のテレメトリを含む
- 内部 FB 分圧抵抗を使用する差動リモート・センス機能、T<sub>J</sub> が -40°C~+150°C の範囲内で V<sub>OUT</sub> 誤差 1% 未満
- PMBus による AVS およびマーギニング機能
- MSEL ピンによる PMBus デフォルト値のピン設定
- 225kHz~1.5MHz で 12 のスイッチング周波数を選択可能 (8 つのピン・ストラップ・オプション)
- 周波数同期入力 / 同期出力
- ブリバイアス出力をサポート
- 強結合インダクタをサポート
- 7mm × 5mm × 1.5mm、40 ピン QFN、0.5mm ピッチ
- WEBENCH® Power Designer により、TPS546B24A を使用するカスタム設計を作成

## 2 アプリケーション

- データ・センター・スイッチ、ラック・サーバー
- アクティブ・アンテナ・システム、リモート無線 / ベースバンド・ユニット
- 自動試験装置、CT、PET、MRI
- ASIC、SoC、FPGA、DSP コア、I/O 電圧

## 3 概要

TPS546B24A は高度に統合された非絶縁型 DC/DC コンバータであり、7mm × 5mm のパッケージで高周波動作と 20A の電流出力を実現します。2 個、3 個、4 個の TPS546B24A を相互に接続して、単一出力で最大 80A を供給できます。VDD5 ピンを介して外部 5V 電源で内蔵 5V LDO をオーバードライブできるため、コンバータの効率向上と消費電力低減が可能です。

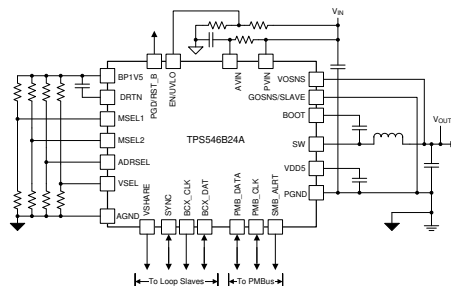
TPS546B24A は入力フィードフォワードによる独自の固定周波数電流モード制御を採用しており、内部補償部品を選択可能であるため、システム・サイズを最小化し、幅広い出力容量で安定性を確保できます。

1MHz クロックをサポートする PMBus インターフェイスは、出力電圧、出力電流、内部ダイ温度などの主要パラメータを監視するためだけでなく、コンバータを設定するための便利な標準化されたデジタル・インターフェイスを提供します。フォルト条件への応答は、システム要件に応じて、再起動、ラッチオフ、無視のいずれかに設定できます。スタックしたデバイス間のバックチャネル通信により、1 つの出力レールに電力供給するすべての TPS546B24A コンバータが 1 つのアドレスを共有できるため、システム・ソフトウェア / ファームウェア設計を簡素化できます。出力電圧、スイッチング周波数、ソフトスタート時間、過電流フォルト制限などの主要なパラメータは、PMBus 通信を使わずに BOM 選定で設定することもでき、プログラムなしでのパワーオンをサポートしています。

### 製品情報

型番 <sup>(1)</sup>	パッケージ	本体サイズ (公称)
TPS546B24A	LQFN-CLIP (40)	7.00mm × 5.00mm

- (1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



### アプリケーション概略



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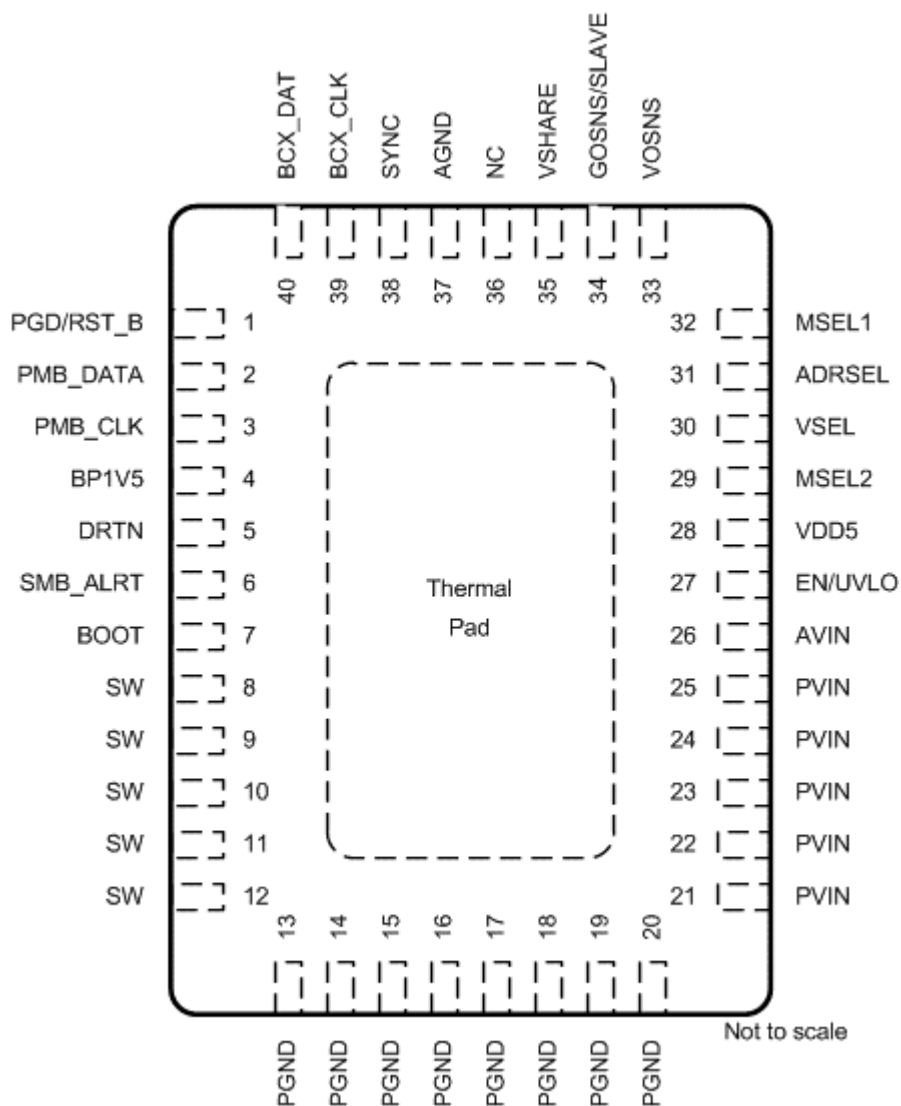
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## 4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

<b>Changes from Revision * (February 2020) to Revision A (September 2020)</b>	<b>Page</b>
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## 5 Pin Configuration and Functions



5-1. 40-Pin LQFN-CLIP With Exposed Thermal Pad RVF Package (Top View)

### Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	PGD/RST_B	I/O	Open-drain power good or (21h) <i>VOUT_COMMAND</i> RESET#. As determined by user-programmable RESET# bit in (EDh) <i>MFR_SPECIFIC_29 (MISC_OPTIONS)</i> . The default pin function is an open-drain power-good indicator. When configured as RESET#, an internal pullup can be enabled or disabled by the PULLUP# bit in (EDh) <i>MFR_SPECIFIC_29 (MISC_OPTIONS)</i> .
2	PMB_DATA	I/O	PMBus DATA pin. See <a href="#">Current PMBus Specifications</a> .
3	PMB_CLK	I	PMBus CLK pin. See <a href="#">Current PMBus Specifications</a> .
4	BP1V5	O	Output of the 1.5-V internal regulator. This regulator powers the digital circuitry and should be bypassed with a minimum of 1 µF to DRTN with an X5R or better ceramic capacitor rated for a minimum of 6 V. BP1V5 is not designed to power external circuit.
5	DRTN	—	Digital bypass return for bypass capacitor for BP1V5. Internally connected to AGND. Do not connect to PGND or AGND.
6	SMB_ALRT	O	SMBus alert pin. See SMBus specification.

PIN		I/O	DESCRIPTION
NO.	NAME		
7	BOOT	I	Bootstrap pin for the internal flying high side driver. Connect a typical 100-nF X5R or better ceramic capacitor rated for a minimum of 10 V from this pin to SW. To reduce the voltage spike at SW, an optional BOOT resistor of up to 8 $\Omega$ can be placed in series with the BOOT capacitor to slow down turn-on of the high-side FET.
8	SW	I/O	Switched power output of the device. Connect the output averaging filter and bootstrap to this group of pins.
9			
10			
11			
12			
13	PGND	—	Power stage ground return. These pins are internally connected to the thermal pad.
14			
15			
16			
17			
18			
19			
20			
21	PVIN	I	Input power to the power stage. Low-impedance bypassing of these pins to PGND is critical. PVIN to PGND should be bypassed with X5R or better ceramic capacitors rated for at least 1.5x the maximum PVIN voltage. In addition, a minimum of one 0402 2.2-nF - 10-nF X7R or better ceramic capacitance rated for at least 1.5x the maximum PVIN voltage should be placed as close to the PVIN and PGND pins or under the PVIN pins to reduce the high-frequency bypass impedance.
22			
23			
24			
25			
26	AVIN	I	Input power to the controller. Bypass with a minimum 1- $\mu$ F X5R or better ceramic capacitor rated for at least 1.5x the maximum AVIN voltage to AGND. If AVIN is connected to the same input as PVIN or VDD5, a minimum 10- $\mu$ s R-C filter between PVIN or VDD5 and AVIN is recommended to reduce switching noise on AVIN.
27	EN/UVLO	I	Enable switching as the PMBus CONTROL pin. EN/UVLO can also be connected to a resistor divider to program input voltage UVLO.
28	VDD5	O	Output of the 5-V internal regulator. This regulator powers the driver stage of the controller and should be bypassed with a minimum of 4.7- $\mu$ F X5R or better ceramic capacitor rated for a minimum of 10 V to PGND at the thermal pad. Low impedance bypassing of this pin to PGND is critical.
29	MSEL2	I	Connect this pin to a 1% tolerance or better resistor divider between BP1V5 and AGND for different options of soft-start time, overcurrent fault limit, and multi-phase information. See <a href="#">Programming MSEL2</a> or <a href="#">Programming MSEL2 for a Slave Device (GOSNS Tied to BP1V5)</a> if GOSNS is tied to BP1V5.
30	VSEL	I	Connect this pin to a 1% tolerance or better resistor divider between BP1V5 and AGND for different options of internal voltage feedback divider and default output voltage. See <a href="#">Programming VSEL</a> .
31	ADRSEL	I	Connect this pin to a 1% tolerance or better resistor divider between BP1V5 and AGND for different options of PMBus addresses and frequency sync (including determination of SYNC pin as SYNC IN or SYNC OUT function). See <a href="#">Programming ADRSEL</a> .
32	MSEL1	I	Connect this pin to a 1% tolerance or better resistor divider between BP1V5 and AGND for different options of switching frequency and internal compensation parameters. See <a href="#">Programming MSEL1</a> .
33	VOSNS	I	The positive input of the remote sense amplifier. For a stand-alone device or the loop master device in a multi-phase configuration, connect VOSNS pin to the output voltage at the load. For the loop slave device in a multi-phase configuration, the remote sense amplifier is not required for output voltage sensing or regulation and this pin can be left floating. If used to monitor another voltage with the Phased <a href="#">READ_VOUT</a> command, VOSNS should be maintained between 0 V and 0.75 V with a <1-k $\Omega$ resistor divider due to the internal resistance to GOSNS, which is connected to BP1V5.
34	GOSNS/SLAVE	I	The negative input of the remote sense amplifier for loop master device or should be pulled up high to indicate loop slave. For a standalone device or the loop master device in a multi-phase configuration, connect the GOSNS pin to the ground at the load. For the loop slave device in a multi-phase configuration, the GOSNS pin must be pulled up to BP1V5 to indicate the device a loop slave.
35	VSHARE	I/O	Voltage sharing signal for multi-phase operation. For standalone device, the VSHARE pin must be left floating. VSHARE can be bypassed to AGND with up to 50 pF of capacitance.

PIN		I/O	DESCRIPTION
NO.	NAME		
36	NC	-	Not internally connected. Connect to PGND at the thermal pad.
37	AGND	-	Analog ground return for controller. Connect the AGND pin directly to the thermal pad on the PCB board.
38	SYNC	I/O	For frequency synchronization, can be programmed as SYNC IN or SYNC OUT pin by ADRSEL pin or the <a href="#">(E4h) MFR_SPECIFIC_20 (SYNC_CONFIG)</a> PMBus Command. The SYNC pin can be left floating when not used.
39	BCX_CLK	I/O	Clock for back-channel communications between stacked devices
40	BCX_DAT	I/O	Data for back-channel communications between stacked devices
—	Thermal pad	—	Package thermal pad, internally connected to PGND. The thermal pad must have adequate solder coverage for proper operation.

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup>

		MIN	MAX	UNIT
Input voltage	PVIN	−0.3	18	V
Input voltage	PVIN, < 2-ms transient	−0.3	19	V
Input voltage	PVIN – SW (PVIN to SW differential)	−0.3	24	V
	PVIN – SW (PVIN to SW differential, < 10-ns transient because of SW ringing)	−5	24	
Input voltage	AVIN	−0.3	20	V
	BOOT	−0.3	35	V
	BOOT – SW (BOOT to SW differential)	−0.3	5.5	V
	EN/UVLO, VOSNS, SYNC, VSEL, MSEL1, MSEL2, ADRSEL	−0.3	5.5	V
	VSHARE, GOSNS/SLAVE	−0.3	1.98	V
	PMB_CLK, PMB_DATA, BCX_CLK, BCX_DAT	−0.3	5.5	V
Output voltage	SW	−1	24	V
Output voltage	SW < 10-ns transient	−5	24	V
Output voltage	VDD5, SMB_ALRT, PGD/RST_B	−0.3	5.5	V
	BP1V5	−0.3	1.65	V
T <sub>J</sub> operating junction temperature		−40	150	°C
T <sub>stg</sub> Storage temperature		−55	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. .  
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>AVIN</sub>	Controller input voltage	2.95	12	18	V
V <sub>PVIN</sub>	Power stage input voltage	2.95	12	18	V
V <sub>SW(peak)</sub>	Peak Switch Node Voltage with respect to PGND			18	V
T <sub>J</sub>	Junction temperature	−40		150	°C

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS546X24A	UNIT
		PQFN (RVF)	
		40 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance JEDEC	25.3	°C/W
R <sub>θJA</sub>	Junction-to-ambient thermal resistance EVM <sup>(2)</sup>	12	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	26.3	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	8.5	°C/W

THERMAL METRIC <sup>(1)</sup>		TPS546X24A	UNIT
		PQFN (RVF)	
		40 PINS	
$\Psi_{JT}$	Junction-to-top characterization parameter	2.0	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	9.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	1.0	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).  
(2) EVM thermal resistance measured on TPS546D24AEVM-2PH. 8-layer, 2-oz Cu per layer evaluation board.

## 6.5 Electrical Characteristics

$T_J = -40^{\circ}\text{C}$  to  $150^{\circ}\text{C}$ ,  $V_{PVIN} = V_{AVIN} = 12\text{ V}$ ,  $f_{SW} = 550\text{ kHz}$ ; zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
INPUT SUPPLY							
V <sub>AVIN</sub>	Input supply voltage range			2.95		16	V
V <sub>PVIN</sub>	Power stage voltage range			2.95		16	
I <sub>AVIN</sub>	Input operating current	Converter not switching			12.5	17	mA
AVIN UVLO							
V <sub>AVINuvlo</sub>	Analog input voltage UVLO for power on reset (PMBus communication)	enable threshold			2.5	2.7	V
	Analog input voltage UVLO for disable			2.09	2.3		V
	Analog input voltage UVLO hysteresis				250		mV
t <sub>delay(uvlo_PMBus)</sub>	Delay from AVIN UVLO to PMBus ready to communicate	AVIN = 3 V			10		ms
PVIN UVLO							
VIN_ON	Power input turn on voltage	Factory default setting		2.75			V
		Programmable range		2.75		15.75	
		Resolution		0.25			
		Accuracy		–5%		5%	
VIN_OFF	Power input turnoff voltage	Factory default setting		2.5			V
		Programmable range		2.5		15.5	
		Resolution		0.25			
		Accuracy		–5%		5%	
ENABLE AND UVLO							
V <sub>ENuvlo</sub>	EN/UVLO Voltage rising threshold			1.05		1.1	V
	EN/UVLO Voltage falling threshold			0.9			
V <sub>ENhys</sub>	EN/UVLO Voltage hysteresis	No external resistors on EN/UVLO		70			mV
I <sub>ENhys</sub>	EN/UVLO hysteresis current	V <sub>EN/UVLO</sub> = 1.1 V		4.5	5.5	6.5	µA
	EN/UVLO hysteresis current	V <sub>EN/UVLO</sub> = 0.9 V		-100		-5	nA
REMOTE SENSE AMPLIFIER							
Z <sub>RSA</sub>	Remote sense input impedance	VOSNS – GOSNS = 1V	VOSNS to GOSNS	85	130	165	kΩ
V <sub>IRNG(GOSNS)</sub>	GOSNS input range for regulation accuracy <sup>(1)</sup>	VOSNS – GOSNS = 1V, VOUT_SCALE_LOOP ≤ 0.5		–0.05		0.05	V
V <sub>IRNG(VOSNS)</sub>	VOSNS input range for regulation accuracy <sup>(1)</sup>	GOSNS = AGND, VOUT_SCALE_LOOP ≤ 0.5		–0.1		5.5	V

$T_J = -40^{\circ}\text{C}$  to  $150^{\circ}\text{C}$ ,  $V_{PVIN} = V_{AVIN} = 12\text{ V}$ ,  $f_{SW} = 550\text{ kHz}$ ; zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
REFERENCE VOLTAGE AND ERROR AMPLIFIER							
V <sub>REF</sub>	Reference voltage <sup>(1)</sup>	Default setting		0.4			V
		Reference voltage range <sup>(1)</sup>		0.25		0.75	V
		Reference voltage resolution <sup>(1)</sup>		2 <sup>−12</sup>			V
V <sub>OUT(ACC)</sub>	Output voltage accuracy	V <sub>OUT</sub> = 1000 mV	−40°C ≤ T <sub>J</sub> ≤ 150°C <sup>(2)</sup>	0.992		1.008	V
		V <sub>OUT</sub> = 500 mV		0.492		0.508	V
		V <sub>OUT</sub> = 1500 mV		1.490		1.510	V
		V <sub>OUT</sub> = 1000 mV	0°C ≤ T <sub>J</sub> ≤ 125°C <sup>(2)</sup>	0.994		1.006	V
		V <sub>OUT</sub> = 500 mV		0.494		0.506	V
		V <sub>OUT</sub> = 1500 mV		1.492		1.508	V
		V <sub>OUT</sub> = 1000 mV	0°C ≤ T <sub>J</sub> ≤ 85°C <sup>(2)</sup>	0.995		1.005	V
		V <sub>OUT</sub> = 500 mV		0.495		0.505	V
		V <sub>OUT</sub> = 1500 mV		1.493		1.507	V
G <sub>mEA</sub>	Programmable error amplifier transconductance			25		200	μS
	Resolution <sup>(1)</sup>	Four settings: 25 uS, 50 uS, 100 uS, 200 uS		25			
	Unloaded Bandwidth <sup>(1)</sup>			8			MHz
R <sub>pEA</sub>	Programmable parallel resistor range			5		315	kΩ
	Resolution <sup>(1)</sup>			5			
C <sub>intEA</sub>	Programmable integrator capacitor range			1.25		18.75	pF
	Resolution <sup>(1)</sup>			1.25			pF
C <sub>pEA</sub>	Programmable parallel capacitor range			6.25		193.75	pF
	Resolution <sup>(1)</sup>			6.25			
CURRENT GM AMPLIFIER							
G <sub>mBUF</sub>	Programmable current error amplifier transconductance			25		200	μS
	Resolution <sup>(1)</sup>	Four settings: 25 μS, 50 μS, 100 μS, 200 μS		25			
	Unloaded bandwidth <sup>(1)</sup>			17			MHz
R <sub>pBUF</sub>	Programmable parallel resistor range			5		315	kΩ
	Resolution <sup>(1)</sup>			5			
R <sub>intBUF</sub>	Programmable integrator resistor range <sup>(1)</sup>			800		1600	kΩ
	Resolution <sup>(1)</sup>			800			
C <sub>intBUF</sub>	Programmable integrator capacitor range			0.3125		4.6875	pF
	Resolution <sup>(1)</sup>			0.3125			
C <sub>pBUF</sub>	Programmable parallel capacitor range			3.125		96.875	pF
	Resolution <sup>(1)</sup>			3.125			
OSCILLATOR							
f <sub>sw</sub>	Adjustment range <sup>(2)</sup>			225		1500	kHz
	Switching frequency <sup>(2)</sup>			500	550	600	
SYNCHRONIZATION							



$T_J = -40^{\circ}\text{C}$  to  $150^{\circ}\text{C}$ ,  $V_{PVIN} = V_{AVIN} = 12\text{ V}$ ,  $f_{SW} = 550\text{ kHz}$ ; zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V <sub>IH(sync)</sub>	High-level input voltage			1.35			V
V <sub>IL(sync)</sub>	Low-level input voltage					0.8	
t <sub>pw(sync)</sub>	Sync input minimum pulse width	f <sub>sw</sub> = 225 kHz to 1500 kHz				200	ns
Δf <sub>SYNC</sub>	SYNC pin frequency range from FREQUENCY_SWITCH frequency <sup>(1)</sup>			−20		20	%
V <sub>OH(sync)</sub>	Sync output high voltage	100-μA load		VDD5 − 0.85V		VDD5	V
V <sub>OL(sync)</sub>	Sync output low voltage	2.4-mA load				0.4	V
t <sub>PLL</sub>	PLL lock time	Fsw = 550 kHz, SYNC clock frequency 495 kHz - 605 kHz <sup>(1)</sup>				65	μs
PhaseErr	Phase interleaving error <sup>(5)</sup>	f <sub>sw</sub> < 1.1 MHz				9	Degree
		f <sub>sw</sub> ≥1.1 MHz				23	ns
RESET							
V <sub>IH(reset)</sub>	High-level input voltage <sup>(1)</sup>			1.35			V
V <sub>IL(reset)</sub>	Low-level input voltage					0.8	
t <sub>pw(reset)</sub>	Minimum RESET_B pulse width					200	ns
R <sub>pullup(reset)</sub>	Internal pull-up resistance	V <sub>RESET</sub> = 0.8V	RESET# = 1	25	34	55	kΩ
V <sub>pullup(reset)</sub>	Internal Pull-up Voltage	I <sub>RESET</sub> = 10 μA	RESET# = 1	VDD5 - 0.5			V
VDD5 REGULATOR							
V <sub>VDD5</sub>	Regulator output voltage	Default, I <sub>VDD5</sub> = 10 mA		4.5	4.7	4.9	V
	Programmable range <sup>(1)</sup>			3.9		5.3	V
	Resolution				200		mV
V <sub>VDD5(do)</sub>	Regulator dropout voltage	V <sub>AVIN</sub> − V <sub>VDD5</sub> , V <sub>AVIN</sub> = 4.5 V, I <sub>VDD5</sub> = 25 mA			130	285	mV
V <sub>VDD5ON(IF)</sub>	Enable voltage on VDD5 for pin-strapping				2.62	2.85	V
V <sub>VDD5OFF(IF)</sub>	Disable voltage on VDD5 for pin-strapping			2.25	2.48		V
V <sub>VDD5ON(SW)</sub>	Switching enable voltage upon VDD5					4.05	V
V <sub>VDD5OFF(SW)</sub>	Switching disable voltage upon VDD5			3.10			V
V <sub>VDD5UV(hyst)</sub>	Regulator UVLO voltage hysteresis			400			mV
BOOTSTRAP							
V <sub>BOOT(drop)</sub>	Bootstrap voltage drop	I <sub>BOOT</sub> = 20 mA, VDD5 = 4.5 V				225	mV
BP1V5 REGULATOR							
V <sub>BP1V5</sub>	1.5-V regulator output voltage	V <sub>AVIN</sub> ≥ 4.5 V, I <sub>BP1V5</sub> = 5 mA		1.42	1.5	1.58	V
I <sub>BP1V5SC</sub>	1.5-V regulator short-circuit current <sup>(1)</sup>			30			mA
PWM							
t <sub>ON(min)</sub>	Minimum controllable pulse width <sup>(1)</sup>					20	ns
t <sub>OFF(min)</sub>	PWM Minimum off-time <sup>(1)</sup>				400	500	ns
SOFT START							

$T_J = -40^{\circ}\text{C}$  to  $150^{\circ}\text{C}$ ,  $V_{PVIN} = V_{AVIN} = 12\text{ V}$ ,  $f_{SW} = 550\text{ kHz}$ ; zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>ON_RISE</sub>	Soft-start time	Factory default setting		3		ms
		Programmable range <sup>(1) (3)</sup>	0		31.75	
		Resolution		0.25		
		Accuracy, TON_RISE = 3 ms	−10%		15%	
t <sub>ON_MAX_FLT_LT</sub>	Upper limit on the time to power up the output	Factory default setting <sup>(4)</sup>		0		ms
		Programmable range <sup>(1) (4)</sup>	0		127.5	
		Resolution		0.5		
		Accuracy <sup>(1)</sup>	−10%		15%	
t <sub>ON_DELAY</sub>	Turn-on delay	Factory default setting		0		ms
		Programmable range <sup>(1)</sup>	0		127.5	
		Resolution		0.5		
		Accuracy <sup>(1)</sup>	−10%		15%	
SOFT STOP						
t <sub>OFF_FALL</sub>	Soft-stop time	Factory default setting <sup>(3)</sup>		0.5		ms
		Programmable range <sup>(1) (3)</sup>	0		31.75	
		Resolution		0.25		
		Accuracy, TOFF_FALL = 1 ms	−10%		15%	
t <sub>OFF_DELAY</sub>	Turn-off delay	Factory default setting		0		ms
		Programmable range <sup>(1)</sup>	0		127.5	
		Resolution		0.5		
		Accuracy <sup>(1)</sup>	−10%		15%	
V <sub>PVINOVF</sub>	Power Input overvoltage fault limit	Factory default		21		V
		Programmable range	6		20	
		Resolution		1		
V <sub>PVINUVW</sub>	Power Input undervoltage warning limit	Factory default		2.5		V
		Programmable range	5		15.75	
		Resolution		0.25		
POWER STAGE						
R <sub>HS</sub>	High-side power device on-resistance	V <sub>BOOT</sub> - V <sub>SW</sub> = 4.5V, T <sub>J</sub> = 25°C		5.5		mΩ
		V <sub>BOOT</sub> - V <sub>SW</sub> = 3 V, T <sub>J</sub> = 25°C		8.5		mΩ
R <sub>LS</sub>	Low-side power device on-resistance	V <sub>VDD5</sub> = 4.5 V, T <sub>J</sub> = 25°C		1.8		mΩ
		V <sub>VDD5</sub> = 3 V, T <sub>J</sub> = 25°C		3.0		mΩ
R <sub>swpd</sub>	SW internal pull-down resistance		3	30	35	kΩ
V <sub>wkdr(on)</sub>	Weak high-side gate drive triggering threshold upon PVIN rising			14.75		V
V <sub>wkdr(off)</sub>	Weak high-side gate drive recovering threshold upon PVIN falling			14.35		V
t <sub>DEAD(LtoH)</sub>	Power stage driver dead-time from Low-side off to High-side on	V <sub>VDD5</sub> = 4.5 V, T <sub>J</sub> = 25°C <sup>(1)</sup>		6		ns
t <sub>DEAD(HtoL)</sub>	Power stage driver dead-time from High-side off to Low-side on	V <sub>VDD5</sub> = 4.5 V, T <sub>J</sub> = 25°C <sup>(1)</sup>		6		ns
CURRENT SHARING						

$T_J = -40^{\circ}\text{C}$  to  $150^{\circ}\text{C}$ ,  $V_{PVIN} = V_{AVIN} = 12\text{ V}$ ,  $f_{SW} = 550\text{ kHz}$ ; zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I <sub>SHARE(acc)</sub>	Output current sharing accuracy of two devices defined as the ratio of the current difference between two devices to the sum of the two	I <sub>OUT</sub> ≥ 10 A per device <sup>(5)</sup>	-10%		10%	
	Output current sharing accuracy of two devices defined as the current difference between each device and the average of all devices	I <sub>OUT</sub> < 10 A per device <sup>(5)</sup>	-1		1	A
I <sub>SHARE(ratio)</sub>	Current Share Ratio between TPS546B24A and TPS546D24A	I <sub>OUT(B24A + D24A)</sub> = 30A <sup>(5)</sup>		0.5		
V <sub>VSHARE</sub>	VSHARE fault trip threshold			0.1		V
	VSHARE fault release threshold			0.2		
LOW-SIDE CURRENT LIMIT PROTECTION						
t <sub>OFF(OC)</sub>	Off time between restart attempts <sup>(1)</sup>	Factory default setting		7 × t <sub>ON_RISE</sub>		ms
	Range		1 × t <sub>ON_RISE</sub>	7 × t <sub>ON_RISE</sub>		
IO_OC_FLT_L MT	Output current overcurrent fault threshold	Factory default setting		26		A
		Programmable range	4		31	
		Resolution		1		
I <sub>NEGOC</sub>	Negative output current overcurrent protection threshold			-10		
IO_OC_WRN_L MT	Output current overcurrent warning threshold	Factory default setting		20		A
		Programmable range	4		31	
		Resolution		1		
I <sub>HSOC</sub>	Output current overcurrent fault accuracy	I <sub>OUT</sub> = 10 A	-1		2	A
		I <sub>OUT</sub> = 20 A <sup>(5)</sup>	-2		4	
HIGH-SIDE SHORT CIRCUIT PROTECTION						
I <sub>HSOC</sub>	Ratio of High-side short-circuit protection fault threshold over Low-side overcurrent limit	(V <sub>BOOT</sub> – V <sub>SW</sub> ) = 4.5V, T <sub>J</sub> = 25°C <sup>(5)</sup>	105%	150%	200%	
	High-side current sense blanking time			100		ns
POWER GOOD (PGOOD) AND OVERVOLTAGE/UNDERVOLTAGE WARNING						
R <sub>PGD</sub>	PGD pulldown resistance	I <sub>PGD</sub> = 5 mA		30	50	Ω
I <sub>PGD(OH)</sub>	Output high open drain leakage current into PGD pin	V <sub>PGD</sub> = 5 V			15	μA
V <sub>PGD(OL)</sub>	PGD pin output low level voltage at no supply voltage	V <sub>AVIN</sub> = 0, I <sub>PGD</sub> = 80 μA			0.8	V

$T_J = -40^{\circ}\text{C}$  to  $150^{\circ}\text{C}$ ,  $V_{PVIN} = V_{AVIN} = 12\text{ V}$ ,  $f_{SW} = 550\text{ kHz}$ ; zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V <sub>OVW</sub>	Overvoltage warning threshold (PGD threshold on VOSNS rising)	Factory default, at VOUT_COMMAND (VOC) = 1 V		106%	110%	114%	VOC
	Range			103%	116%		
	Resolution			1%			
V <sub>UWV</sub>	Undervoltage warning threshold (PGD threshold on VOSNS falling)	Factory default, at VOUT_COMMAND (VOC) = 1 V		86%	90%	94%	
	Range			84%	97%		
	Resolution			1%			
V <sub>PGD(rise)</sub>	PGD release threshold on VOSNS rising and undervoltage warning de-assertion threshold	Factory default, at VOUT_COMMAND (VOC) = 1 V		95%			
V <sub>PGD(fall)</sub>	PGD threshold on VOSNS falling and overvoltage warning de-assertion threshold	Factory default, at VOUT_COMMAND (VOC) = 1 V		105%			
OUTPUT OVERVOLTAGE AND UNDERVOLTAGE FAULT PROTECTION							
V <sub>OVF</sub>	Overvoltage fault threshold	Factory default, at VOUT_COMMAND (VOC) = 1 V	Factory default, at VOUT_COMMAND (VOC) = 1 V	111%	115%	119%	VOC
	Range	Factory default, at VOUT_COMMAND (VOC) = 1 V	Factory default, at VOUT_COMMAND (VOC) = 1 V	105%	140%		
	Resolution	Factory default, at VOUT_COMMAND (VOC) = 1 V	Factory default, at VOUT_COMMAND (VOC) = 1 V	2.5%			
V <sub>UVF</sub>	Undervoltage fault threshold	Factory default, at VOUT_COMMAND (VOC) = 1 V	Factory default, at VOUT_COMMAND = 1.00 V	81%	85%	89%	
	Range	Factory default, at VOUT_COMMAND = 1.00 V	Factory default, at VOUT_COMMAND = 1.00 V	60%	95%		
	Resolution	Factory default, at VOUT_COMMAND = 1.00 V	Factory default, at VOUT_COMMAND = 1.00 V	2.5%			
V <sub>OVF(fix)OFF</sub>	Fixed overvoltage fault threshold	Factory default, at VOUT_COMMAND (VOC) = 1 V	Factory default, at VOUT_COMMAND = 1.00 V	1.15	1.2	1.25	V
	Recovery threshold <sup>(1)</sup>	Factory default, at VOUT_COMMAND = 1.00 V	Factory default, at VOUT_COMMAND = 1.00 V	0.4			
OUTPUT VOLTAGE TRIMMING							
V <sub>OUTRES</sub>		Default Resolution of VOUT_COMMAND, Trim and Margin, VOUT_SCALE_LOOP = 0.5		1.90	1.95	2.00	mV
		Programmable range <sup>(1)</sup>		2 <sup>-12</sup>		2 <sup>-5</sup>	V
VOUT_TRANS_RT	Output voltage transition rate	Factory default setting		1			mV/μs
		Programmable range <sup>(1)</sup>		0.063		15.933	
		Accuracy		-10%		10%	
VOUT_SCL_LP	Feedback loop scaling factor <sup>(1)</sup>	Factory default setting		0.5			
		Programmable range, 4 discrete settings		0.125		1	

$T_J = -40^{\circ}\text{C}$  to  $150^{\circ}\text{C}$ ,  $V_{PVIN} = V_{AVIN} = 12\text{ V}$ ,  $f_{SW} = 550\text{ kHz}$ ; zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
VOUT_CMD	Output voltage programmable values	Factory default setting		0.8			V
		Programmable range	VOUT_SCALE_LOOP = 1 <sup>(5)</sup>	0.25	0.75	V	
			VOUT_SCALE_LOOP = 0.5	0.25	1.5		
			VOUT_SCALE_LOOP = 0.25 <sup>(5)</sup>	0.25	3		
			VOUT_SCALE_LOOP = 0.125 <sup>(5)</sup>	0.25	6		
TEMPERATURE SENSE AND THERMAL SHUTDOWN							
T <sub>SD</sub>	Bandgap thermal shutdown temperature <sup>(1)</sup>			150	170		°C
T <sub>HYST</sub>	Bandgap thermal shutdown hysteresis <sup>(1)</sup>			25			
OT_FLT_LMT	Internal overtemperature fault limit <sup>(1)</sup>	Factory default setting		150			
		Programmable range		0	160		
		Resolution		1			
OT_WRN_LMT	Internal overtemperature warning limit <sup>(1)</sup>	Factory default setting		125			
		Programmable range		0	160		
		Resolution		1			
T <sub>OT(hys)</sub>	Internal overtemperature fault, warning hysteresis <sup>(1)</sup>	Factory default setting		25			
MEASUREMENT SYSTEM							
M <sub>VOUT(rng)</sub>	Output voltage measurement range <sup>(1)</sup>			0		6	V
M <sub>VOUT(acc)</sub>	Output voltage measurement accuracy	250 mV < V <sub>OUT</sub> < 6 V		−2%		2%	
M <sub>VOUT(lsb)</sub>	Output voltage measurement bit resolution <sup>(1)</sup>				244		μV
M <sub>IOUT(rng)</sub>	Output current measurement range <sup>(1)</sup>			−5		30	A
M <sub>IOUT(acc)</sub>	Output current measurement accuracy <sup>(5)</sup>	I <sub>OUT</sub> ≤ 5 A, T <sub>J</sub> = 25°C		−1	0	1	A
M <sub>IOUT(acc)</sub>	Output current measurement accuracy <sup>(5)</sup>	I <sub>OUT</sub> = 10A, −40°C ≤ T <sub>J</sub> ≤ 150°C		−1.5	0	1.5	A
M <sub>IOUT(acc)</sub>	Output current measurement accuracy <sup>(5)</sup>	I <sub>OUT</sub> = 20A, −40°C ≤ T <sub>J</sub> ≤ 150°C		−2	0	2	A
M <sub>IOUT(acc)</sub>	Output current measurement accuracy <sup>(5)</sup>	I <sub>OUT</sub> = 10A, 0°C ≤ T <sub>J</sub> ≤ 85°C		−1.3	0	1.3	A
M <sub>IOUT(acc)</sub>	Output current measurement accuracy <sup>(5)</sup>	I <sub>OUT</sub> = 20A, 0°C ≤ T <sub>J</sub> ≤ 85°C		−1.5	0	1.5	A
M <sub>IOUT(lsb)</sub>	Output current measurement bit resolution <sup>(1)</sup>				2 <sup>−6</sup>		A
M <sub>PVIN(rng)</sub>	Input voltage measurement range <sup>(1)</sup>			0		20	V
M <sub>PVIN(acc)</sub>	Input voltage measurement accuracy	4 V< PVIN < 20 V		−3		3	%
M <sub>PVIN(lsb)</sub>	Input voltage measurement bit resolution <sup>(1)</sup>				2 <sup>−6</sup>		V
M <sub>TSNS(acc)</sub>	Internal temperature sense accuracy <sup>(5)</sup>	−40°C ≤ T <sub>J</sub> ≤ 150°C		−3		3	°C
M <sub>TSNS(lsb)</sub>	Internal temperature sense bit resolution <sup>(1)</sup>				0.25		
PMBUS INTERFACE + BCX							

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 $T_J = -40^{\circ}\text{C}$  to  $150^{\circ}\text{C}$ ,  $V_{PVIN} = V_{AVIN} = 12\text{ V}$ ,  $f_{SW} = 550\text{ kHz}$ ; zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{IH(PMBUS)}$	High-level input voltage on PMB_CLK, PMB_DATA, BCX_CLK, BCX_DAT		1.35			V
$V_{IL(PMBUS)}$	Low-level input voltage on PMB_CLK, PMB_DATA, BCX_CLK, BCX_DAT				0.8	
$I_{IH(PMBUS)}$	Input high level current into PMB_CLK, PMB_DATA		-10		10	$\mu\text{A}$
$I_{IL(PMBUS)}$	Input low level current into PMB_CLK, PMB_DATA		-10		10	$\mu\text{A}$
$V_{OL(PMBUS)}$	Output low level voltage on PMB_DATA, SMB_ALRT, BCX_DAT	$V_{AVIN} > 4.5\text{ V}$ , input current to PMB_DATA, SMB_ALRT, BCX_DAT = 20 mA			0.4	V
$I_{OH(PMBUS)}$	Output high level open drain leakage current into PMB_DATA, SMB_ALRT	Voltage on PMB_DATA, SMB_ALRT = 5.5 V			10	$\mu\text{A}$
$I_{OL(PMBUS)}$	Output low level open drain sinking current on PMB_DATA, SMB_ALRT, BCX_DAT	Voltage on PMB_DATA, SMB_ALRT, BCX_DAT = 0.4 V	20			mA
$f_{PMBUS\_CLK}$	PMBus operating frequency range	GOSNS = AGND	10		1000	kHz
$C_{PMBUS}$	PMBUS_CLK & PMBUS_DATA pin input capacitance <sup>(1)</sup>	$V_{pin} = 0.1\text{ V}$ to $1.35\text{ V}$			5	pF
$N_{WR\_NVM}$	Number of NVM writeable cycles <sup>(1)</sup>	$-40^{\circ}\text{C}$ to $150^{\circ}\text{C}$	1000			cycle
$t_{CLK\_STCH(max)}$	Maximum Allowable Clock Stretch <sup>(1)</sup>				6	ms

(1) Specified by design. Not production tested.

(2) The parameter covers 2.95 V to 18 V of AVIN.

(3) The setting of TON\_RISE and TOFF\_FALL of 0 ms means the unit to bring its output voltage to the programmed regulation value of down to 0 as quickly as possible, which results in an effective TON\_RISE and TOFF\_FALL time of 0.5 ms (fastest time supported).

(4) The setting of TON\_MAX\_FAULT\_LIMIT and TOFF\_MAX\_WARN\_LIMIT of 0 means disabling TON\_MAX\_FAULT and TOFF\_MAX\_WARN response and reporting completely.

 (5) Not production tested. Guaranteed by correlation. AVIN = PVIN = 12 V, VOUT = 1 V  $f_{SW} = 325\text{ kHz}$  L = 320 nH

## 6.6 Typical Characteristics

$V_{PIN} = V_{AVIN} = 12\text{ V}$ ,  $T_A = 25^\circ\text{C}$ ,  $f_{sw} = 650\text{ kHz}$  (unless otherwise specified). Safe operating area curves were measured using a Texas Instruments evaluation module (EVM).

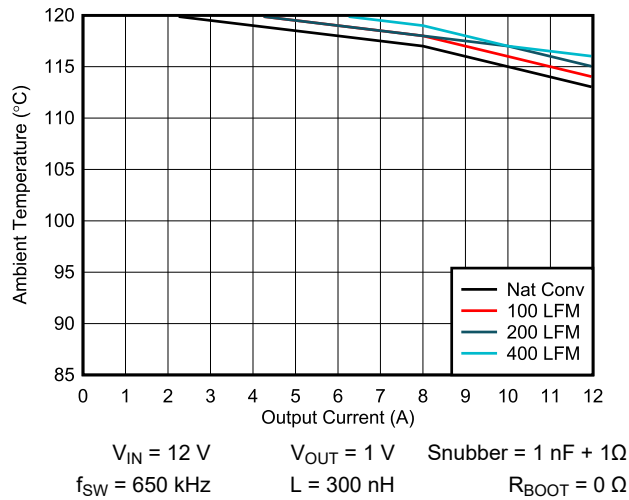


Figure 6-1. TPS546B24A Safe Operating Area

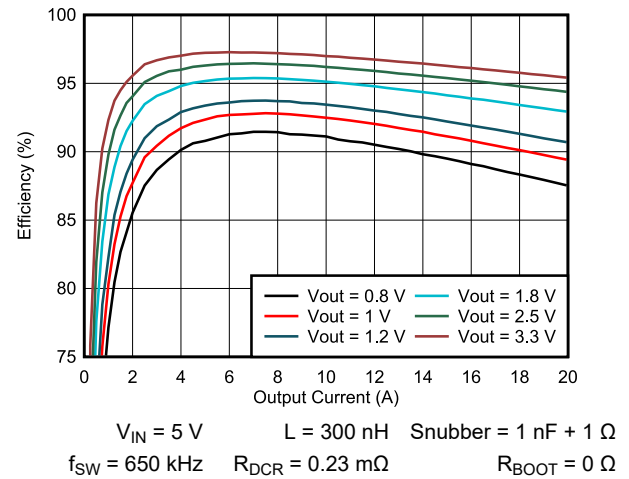


Figure 6-2. TPS546B24A Efficiency vs Output Current

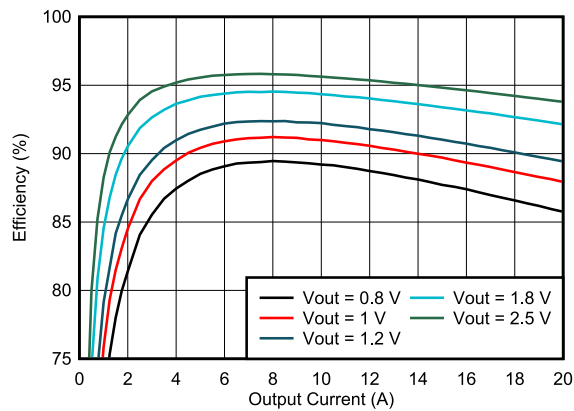


Figure 6-3. TPS546B24A Efficiency vs Output Current

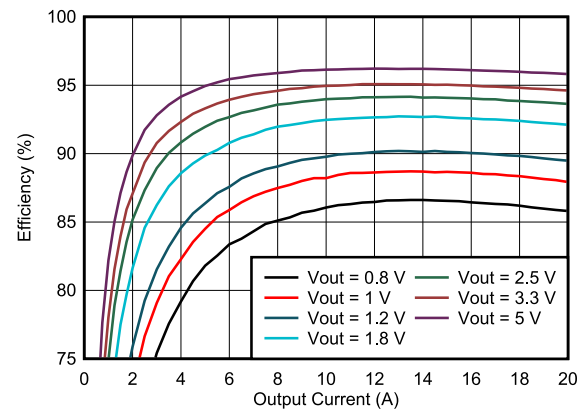


Figure 6-4. TPS546B24A Efficiency vs Output Current

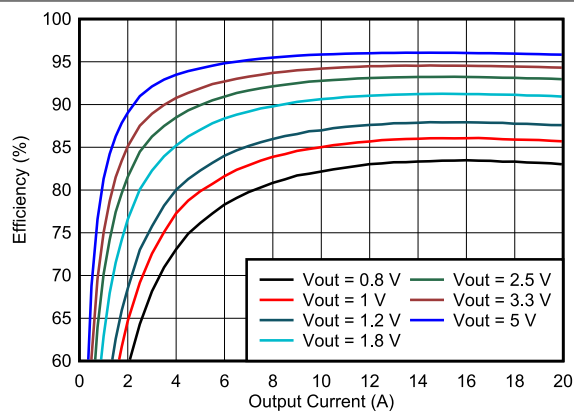


Figure 6-5. TPS546B24A Efficiency vs Output Current

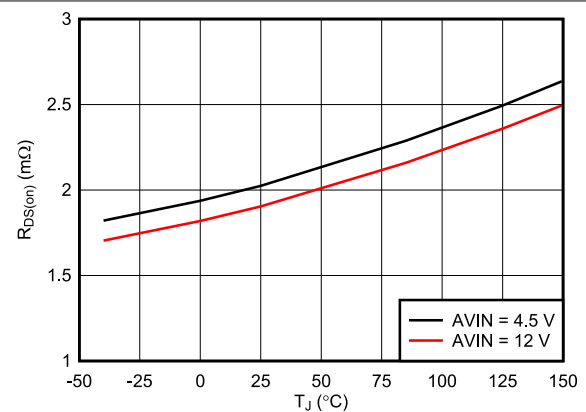
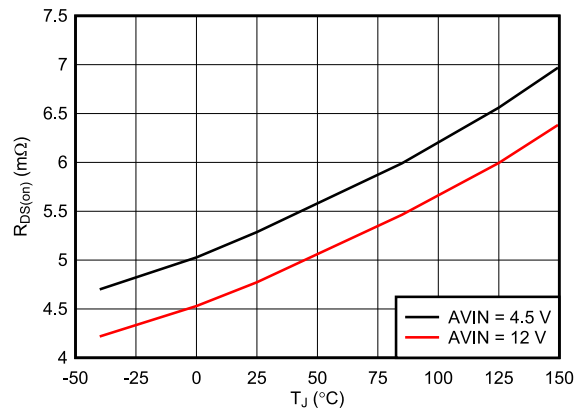
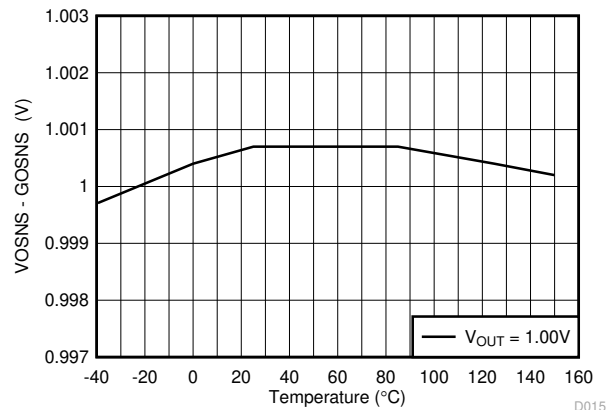


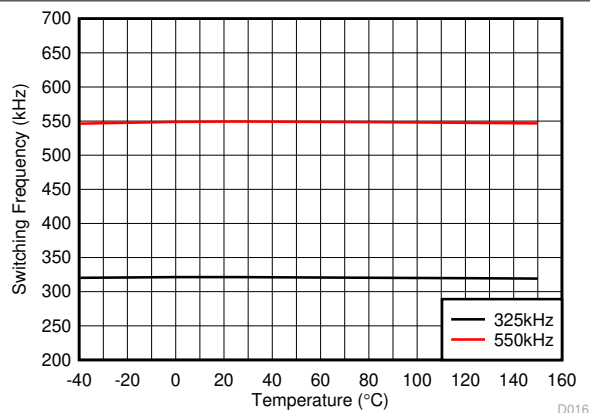
Figure 6-6. Low-Side MOSFET On-Resistance ( $R_{DS(on)}$ ) vs Junction Temperature



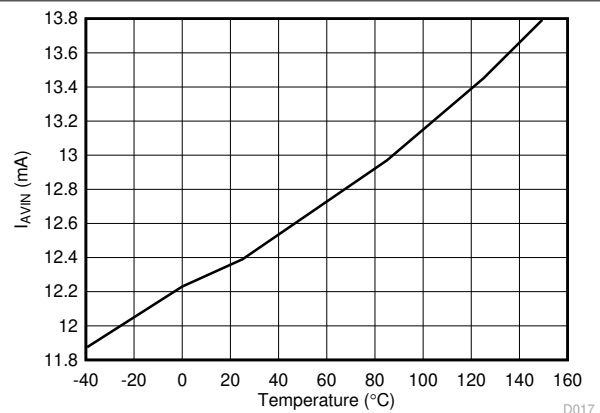
**6-7. High-Side MOSFET On-Resistance ( $R_{DS(on)}$ ) vs Junction Temperature**



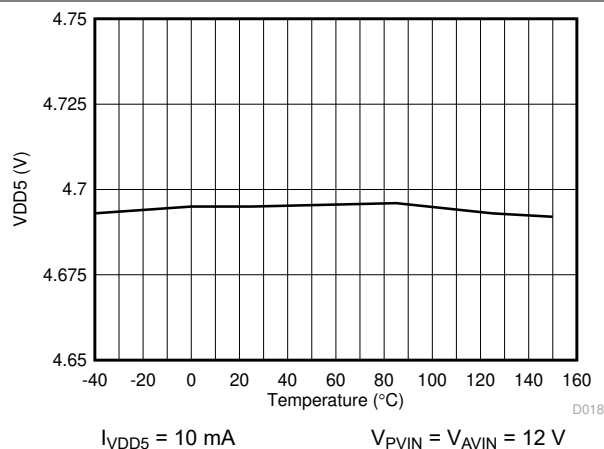
**6-8. Output Voltage vs Junction Temperature**



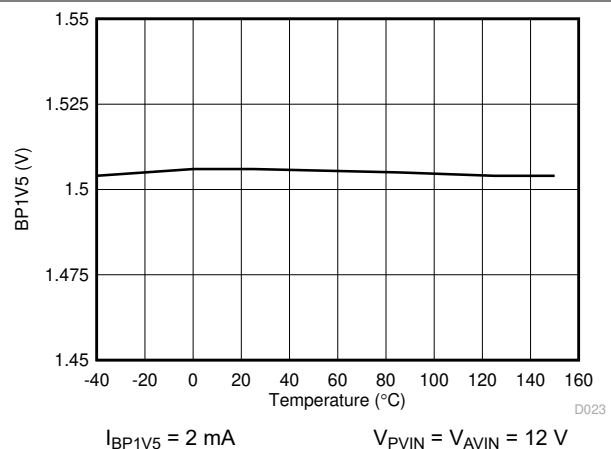
**6-9. Switching Frequency vs Junction Temperature**



**6-10. Non-Switching Input Current ( $I_{AVIN}$ ) vs Junction Temperature**

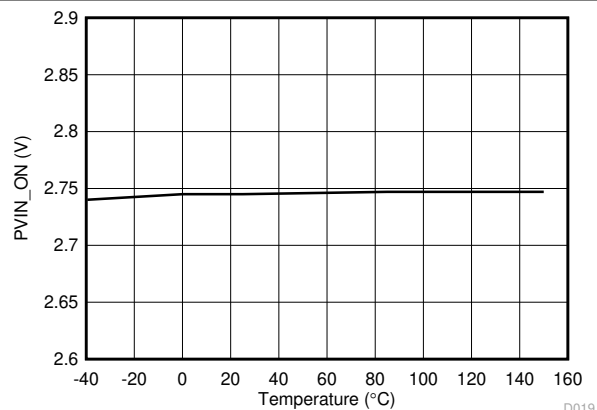


**6-11. VDD5 Voltage vs Junction Temperature**



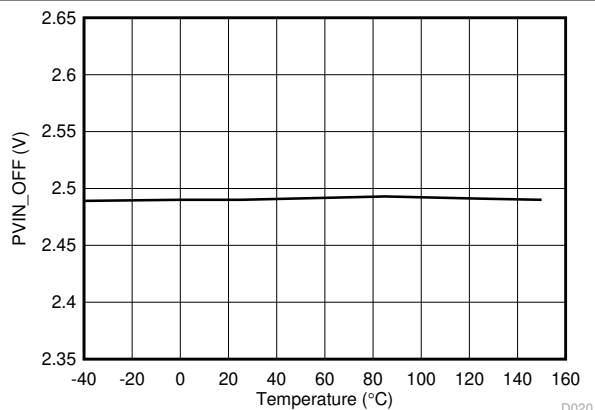
**6-12. BP1V5 Voltage vs Junction Temperature**





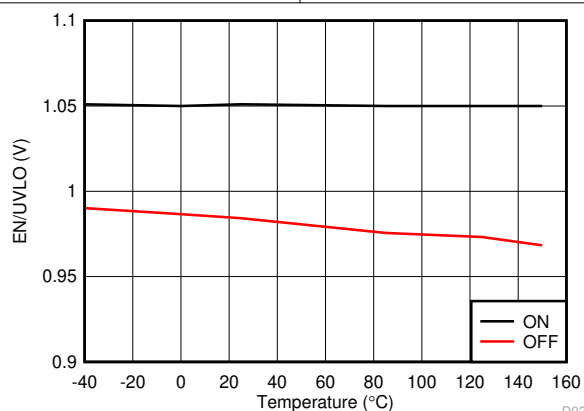
VIN\_ON = 2.75 V

6-13. Turnon Voltage vs Junction Temperature



VIN\_OFF = 2.5 V

6-14. Turnoff Voltage vs Junction Temperature



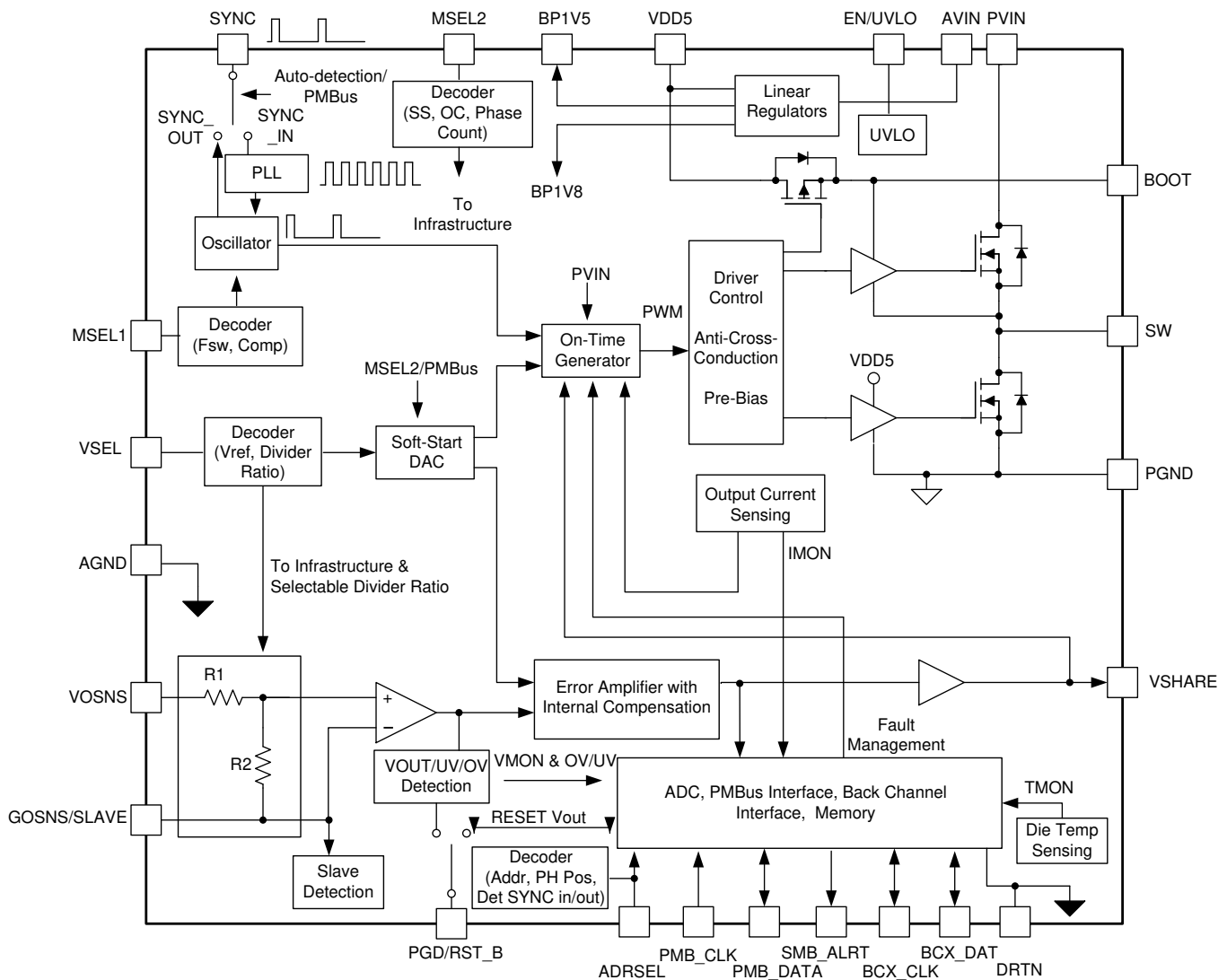
6-15. EN/UVLO Thresholds vs Junction Temperature

## 7 Detailed Description

### 7.1 Overview

The TPS546B24A uses a fixed-frequency, proprietary current-mode control. The switching frequency can be selected from pre-set values through pin-strapping and PMBus programming. The output voltage is sensed through a true differential remote sense amplifier and internal resistor divider, then compared to an internal voltage reference by an error amplifier. An internal oscillator initiates the turnon of the high-side power switch. The error amplifier output is buffered and shared through VSHARE among stacked devices. This shared voltage is compared to the sensed switch node current to drive a linear voltage ramp modulator with input voltage, output voltage, and switching frequency feedforward to regulate the average switch-node current. As a synchronous buck converter, the device normally works in continuous conduction mode (CCM) under all load conditions. The compensation components are integrated into the TPS546B24A devices, and programmable through the PMBus command **(B1h) USER\_DATA\_01 (COMPENSATION\_CONFIG)** or with the external pin **MSEL1** to select pre-set values based on switching frequency and output LC filters.

### 7.2 Functional Block Diagram



## 7.3 Feature Description

### 7.3.1 Average Current-Mode Control

The TPS546B24A device uses an average current-mode control architecture with independently programmable current error integration and voltage error integration loops. This architecture provides similar performance to peak current-mode control without restricting the minimum on-time or minimum-off time control, allowing the gain selection of the current loop to effectively set the slope compensation. For help selecting compensation values, customers can use the [TPS546x24A Compensation and Pin-Strap Resistor Calculator](#) design tool.

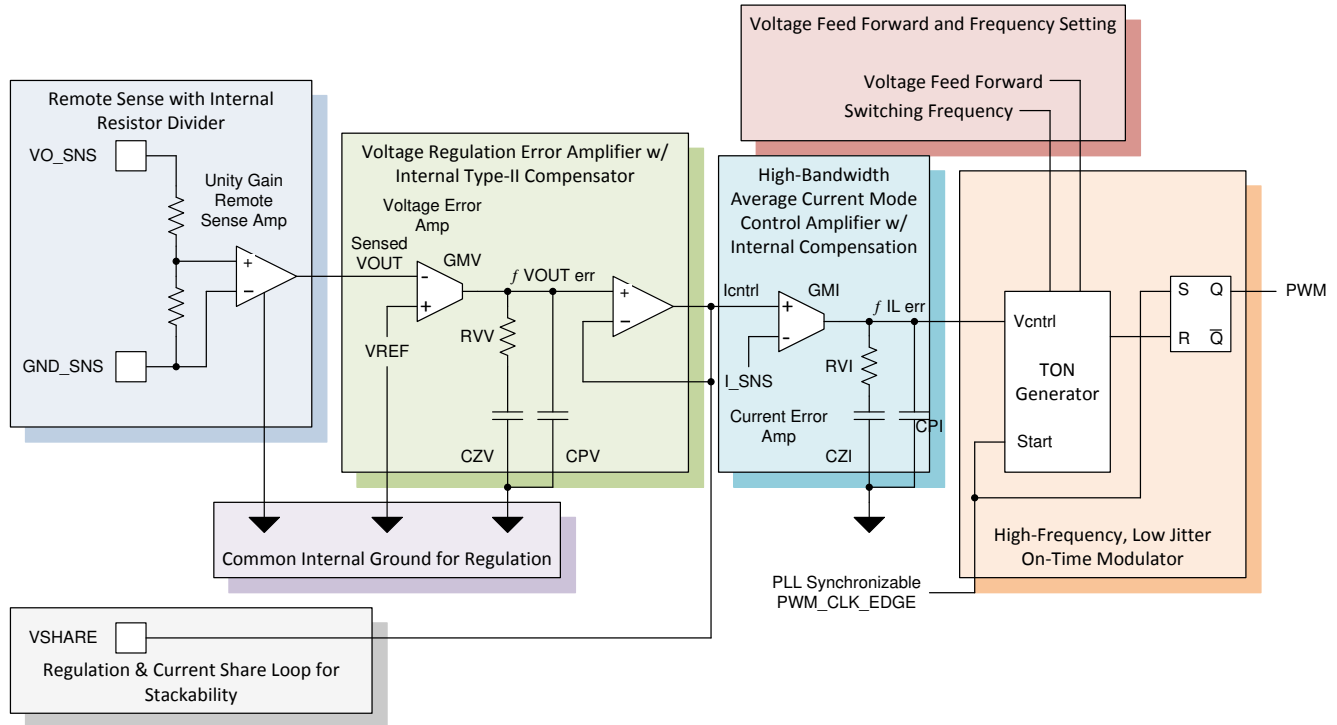


FIG 7-1. Average Current Mode Control Block Diagram

#### 7.3.1.1 On-Time Modulator

The input voltage feedforward modulator converts the integrated current error signal, ILerr, into an inductor on-time that provides a controlled volt-second balance across the inductor over each full switching period that simplifies the current error integration loop design. The modulator produces a full-cycle averaged small signal Vcntrl to  $dI_L/dt$  transfer function given by 式 1:

$$\frac{dI_L}{dV_{cntrl}} = \frac{V_{IN}}{V_{ramp}} \times \frac{1}{L} = \frac{5.5}{L} \quad (1)$$

Thus the inductor current modulator gain is given by 式 2:

$$\frac{dI_L}{dV_{cntrl}}(f) = \frac{V_{IN}}{V_{ramp}} \times \frac{1}{L \times f} = \frac{5.5}{L \times f} \quad (2)$$

This natural integration 1/f function allows the current loop to be compensated by the mid-band gain of the error current integrator.

### 7.3.1.2 Current Error Integrator

The current error integrator adjusts the modulator control voltage to match the sensed inductor current,  $I_{\text{sns}}$ , to the current voltage at the VSHARE pin. The integrator is tuned through the GMI, RVI, CZI, CPI, and CZI\_MUL parameters in [\(B1h\) USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#). Thanks to the natural integration of the  $1/f$  function of the current control gain, the bandwidth of the current control loop can be adjusted with the mid-band gain of the integrator,  $\text{GMI} \times \text{RVI}$ .

The current loop crossover occurs at the frequency when the full loop gain is equal to 1 according to [式 3](#):

$$|I_{\text{LOOP}}(f)| \times \frac{V_{\text{PVIN}}}{V_{\text{ramp}}} \times \text{CSA} \times \frac{1}{1.7 \times \pi \times f \times L} = 1 \quad (3)$$

Solving for the mid-band gain of the current loop, you find [式 4](#):

$$I_{\text{LOOP}}_{\text{MB}} = \text{GMI} \times \text{RVI} = \frac{V_{\text{ramp}}}{V_{\text{PVIN}}} \times \frac{1.7}{\text{CSA}} \times L \times \pi \times f_{\text{coi}} \quad (4)$$

While Nyquist Theorem suggests that a bandwidth of  $\frac{1}{2} f_{\text{SW}}$  is possible, inductor tolerances and phase delays in the current sense, modulator, and H-bridge power FETs make  $f_{\text{SW}}/4$  a more practical target, which simplifies the target current loop midband gain to achieve a current loop bandwidth of  $f_{\text{SW}}/4$  to [式 5](#):

$$I_{\text{LOOP}}_{\text{MB}} = \text{GMI} \times \text{RVI} = \frac{V_{\text{ramp}}}{V_{\text{IN}}} \times \frac{1}{\text{CSA}} \times L \times \pi \times \frac{f_{\text{SW}}}{4} = \frac{\pi}{4 \times 5.5 \times 12.31 \times 10^{-3}} \times L \times f_{\text{SW}} = 11.6 \times L \times f_{\text{SW}} \quad (5)$$

An integrator from DC to the low-frequency zero,  $\text{RVI} \times \text{CZI}$ , compensates for the valley voltage of the modulator ramp and the nominal offset of the output voltage. A high-frequency filter pole,  $\text{RVI} \times \text{CPI}$  between half the switching frequency and the switching frequency reduces high-frequency noise from VSHARE and minimizes pulse-width jitter.

To avoid loop interactions, the integrating zero frequency should be below the voltage loop cross-over frequency, while the high-frequency pole should be between  $\frac{1}{2}$  the switching frequency and the switching frequency to limit high-frequency noise and jitter in the current loop without imposing additional phase loss in the voltage loop.

The closed loop average current mode control allows the current sense amplifier, on-time modulator, H-bridge power FETs, and inductor to operate as a transconductance amplifier with forward gain of  $1/\text{CSA}$  or 81.25 A/V with a bandwidth equal to  $F_{\text{coi}}$ .

### 7.3.1.3 Voltage Error Integrator

The voltage error integrator regulates the output voltage by adjusting the current control voltage, VSHARE, similar to any current mode control architecture. A transconductance amplifier compares the sense feedback voltage to a programmed reference voltage to set the current control voltage VSHARE to maintain the desired output voltage. While a regulated current source feeding an output capacitance provides a natural, stable integrator, mid-band gain is often desired to improve the loop bandwidth and transient response.

With a transconductance set by the current sense gain, the voltage loop cross-over occurs when the full loop gain equal 1 according to [式 6](#).

$$V_{\text{OUT\_SCALE\_LOOP}} \times |V_{\text{LOOP}}(f)| \times \frac{1}{\text{CSA}} \times |Z_{\text{OUT}}(f)| = 1 \quad (6)$$

To prevent the current integration loop bandwidth from negatively impacting the phase margin of the voltage loop, the voltage loop should have a target bandwidth of  $F_{\text{coi}} / 2.5$ . With a current mode loop of  $f_{\text{SW}}/4$ , the voltage loop mid-band gain should be [式 7](#):

$$V_{LOOP\_MB} = GMV \times RVV = \frac{1}{V_{OUT\_SCALE\_LOOP}} \times \frac{CSA}{Z_{OUT} \left( \frac{f_{SW}}{10} \right)} \quad (7)$$

An integrator pole is necessary to maintain accurate DC regulation, and the zero-frequency set by  $RVV \times CZV$  should be set below the lowest cross-over frequency with the largest output capacitor intended to be supported at the output, but not more than 1/2 the target voltage loop crossover frequency  $f_{COV}$ .

A high frequency noise pole, intended to keep switching noise out of the current loop should also be employed, with a high-frequency pole set by  $RVV \times CPV$  should be set between  $f_{SW}/4$  and  $f_{SW}$ .

For pin programmed options of compensation components, see [表 7-9](#).

For PMBus programming of compensation values, see [\(B1h\) USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#).

### 7.3.2 Linear Regulators

The TPS546B24A devices have three internal linear regulators receiving power from AVIN and providing suitable bias (1.5 V, 1.8 V, and 5 V) for the internal circuitry of the device. External bypass pins for VDD5 and BP1V5 must be bypassed to their respective grounds for the converter to function properly. BP1V5 requires a minimum of 1  $\mu$ F of capacitance connected to DRTN. VDD5 requires a minimum 4.7  $\mu$ F of capacitance connected to PGND. Once AVIN, 1.5-V, 1.8-V, and 5-V reach their respective UVLOs, the device initiates a power-on reset, after which the device can be communicated with through PMBus for configuration and users can store defaults to the NVM.

The VDD5 has internally-fixed undervoltage lockout of 3.9 V (typ.) to enable power-stage conversion. The VDD5 regulator can also be fed by external supply to reduce internal power dissipation and improve efficiency by eliminating the loss in the internal LDO, or to allow operation with AVIN less than 4 V. The external supply should be higher voltage than the LDO regulation voltage programmed by [\(B5h\) USER\\_DATA\\_05 \(POWER\\_STAGE\\_CONFIG\)](#).

Place bypass capacitors as close as possible to the device pins, with a minimum return loop back to their respective ground. Keep the return loop away from fast switching voltage and main current path — see [Layout](#) for details. Poor bypassing can degrade the performance of the regulator.

The use of the internal regulators to power other circuits is not recommended because the loads placed on the regulators might adversely affect operation of the controller.

### 7.3.3 AVIN and PVIN Pins

The device allows for a variety of applications by using the AVIN and PVIN pins together or separately. The AVIN pin voltage supplies the internal control circuits of the device. The PVIN pin voltage provides the input voltage to the switching power stage. When connected to a single supply, the input voltage for AVIN and PVIN can range from 4 V to 16 V. If the PVIN is connected to separate supply from AVIN, the PVIN voltage can be 2.95 V to 16 V, and AVIN has to meet 4-V minimum and 18-V maximum to drive the control and driver. If AVIN is connected to the same supply as PVIN or VDD5, TI recommends a minimum 10- $\mu$ s R-C filter with a 1- $\Omega$  to 10- $\Omega$  resistor and AVIN bypass capacitor between AVIN and PVIN to reduce PVIN switching noise on the AVIN input.

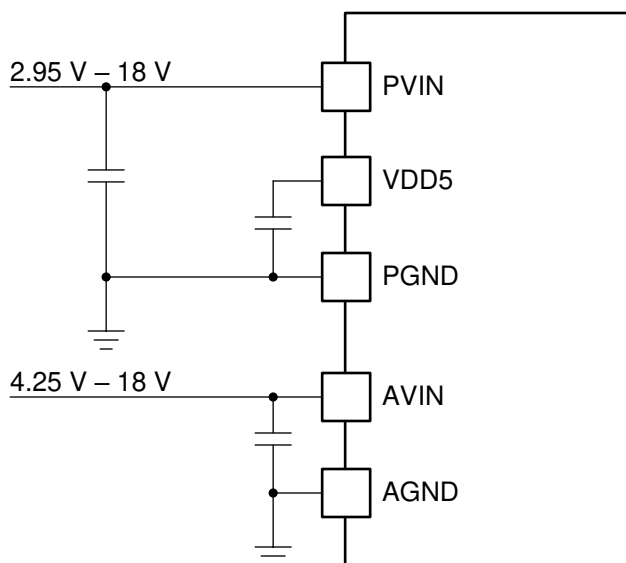


Figure 7-2. TPS546B24A Separate PVIN and AVIN connections

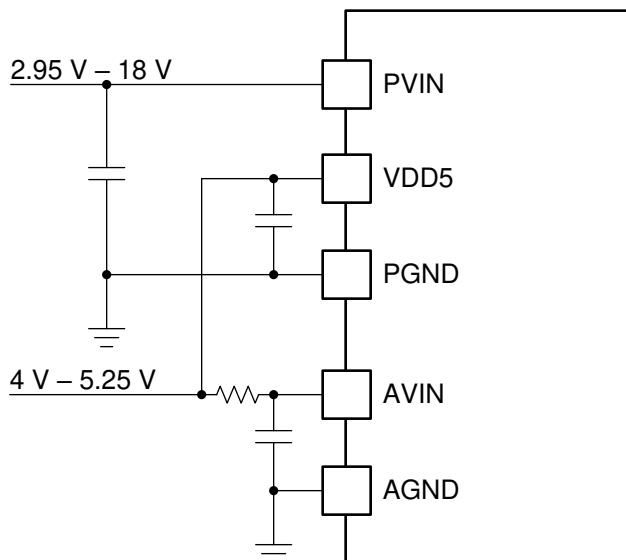


Figure 7-3. TPS546B24A Separate PVIN and AVIN connections with VDD5

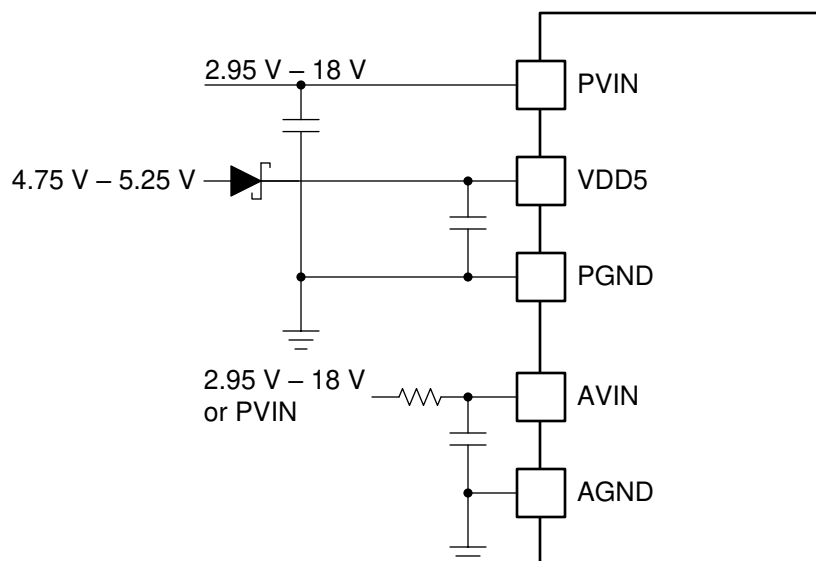


FIG 7-4. TPS546B24A Separate PVIN, AVIN, and VDD5 Connections

### 7.3.4 Input Undervoltage Lockout (UVLO)

The TPS546B24A provides four independent UVLO functions for the broadest range of flexibility in start-up control. While only the fixed AVIN UVLO is required to enable PMBus connectivity as well as VOUT and TEMPERATURE monitoring, all four UVLO functions must be met before switching can be enabled.

#### 7.3.4.1 Fixed AVIN UVLO

The TPS546B24A has internally fixed UVLO of 2.5 V (typical) on AVIN to enable the digital core and initiate power on reset, including pin detection. The off-threshold on AVIN is 2.3 V (typ).

#### 7.3.4.2 Fixed VDD5 UVLO

The TPS546B24A has an internally-fixed UVLO of 3.9 V (typ) on VDD5 to enable drivers and output voltage conversion. The off-threshold on VDD5 is 3.5 V.

#### 7.3.4.3 Programmable PVIN UVLO

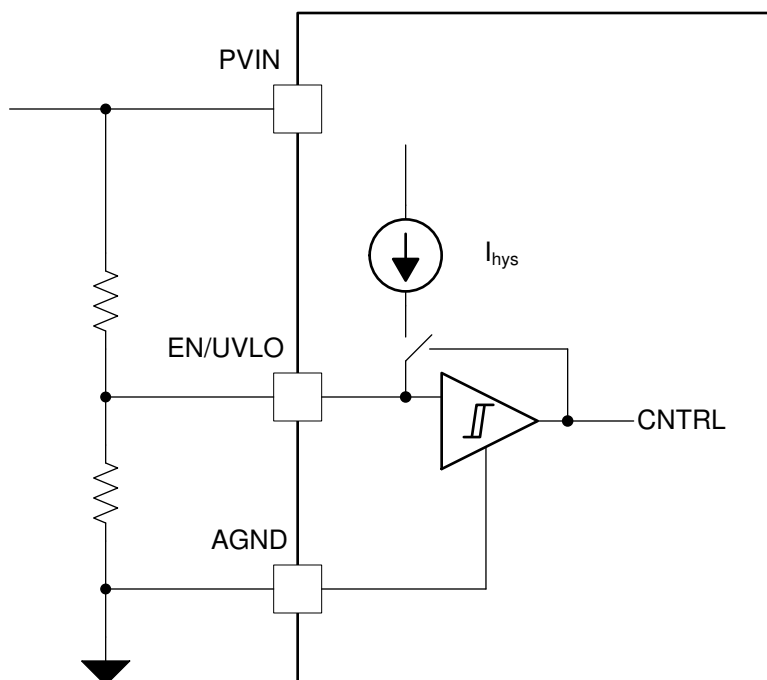
Two PMBus commands ((35h) *VIN\_ON* and (36h) *VIN\_OFF*) allow the user to set PVIN voltage turnon and turnoff thresholds independently, with 0.25-V resolution from 2.75 V to 15.75 V (6-bit) for (35h) *VIN\_ON* and from 2.5 V to 15.5 V (6-bit) for (36h) *VIN\_OFF*.

#### Note

If (36h) *VIN\_OFF* is programmed higher than (35h) *VIN\_ON*, the TPS546B24A rapidly switches between enabled and disabled while PVIN remains below (36h) *VIN\_OFF*. Propagation delays between enable and disable can result in the converter starting (61h) *TON\_RISE* and (65h) *TOFF\_FALL* in such conditions.

#### 7.3.4.4 EN/UVLO Pin

The TPS546B24A also offers a precise threshold and hysteresis current source on the EN/UVLO pin so that it can be used to program an additional UVLO to any external voltage greater than 1.05 V (typ.), including AVIN, PVIN, or VDD5. For an added level of flexibility, the EN/UVLO pin can be disabled or its logic inverted through the PMBUS Command (02h) *ON\_OFF\_CONFIG*, which allows the pin to be connected to AGND to ensure the output is not enabled until PMBus programming has been completed.



7-5. TPS546B24A UVLO Voltage Divider

### 7.3.5 Start-Up and Shutdown

The start-up and shutdown of the device is controlled by several PMBus programmable values including:

- (01h) OPERATION
- (02h) ON\_OFF\_CONFIG
- (60h) TON\_DELAY
- (61h) TON\_RISE
- (64h) TOFF\_DELAY
- (65h) TOFF\_FALL

With the default (02h) ON\_OFF\_CONFIG settings, the timing is as shown in 7-6. See the [Supported PMBus Commands](#) for full details on the implementation.



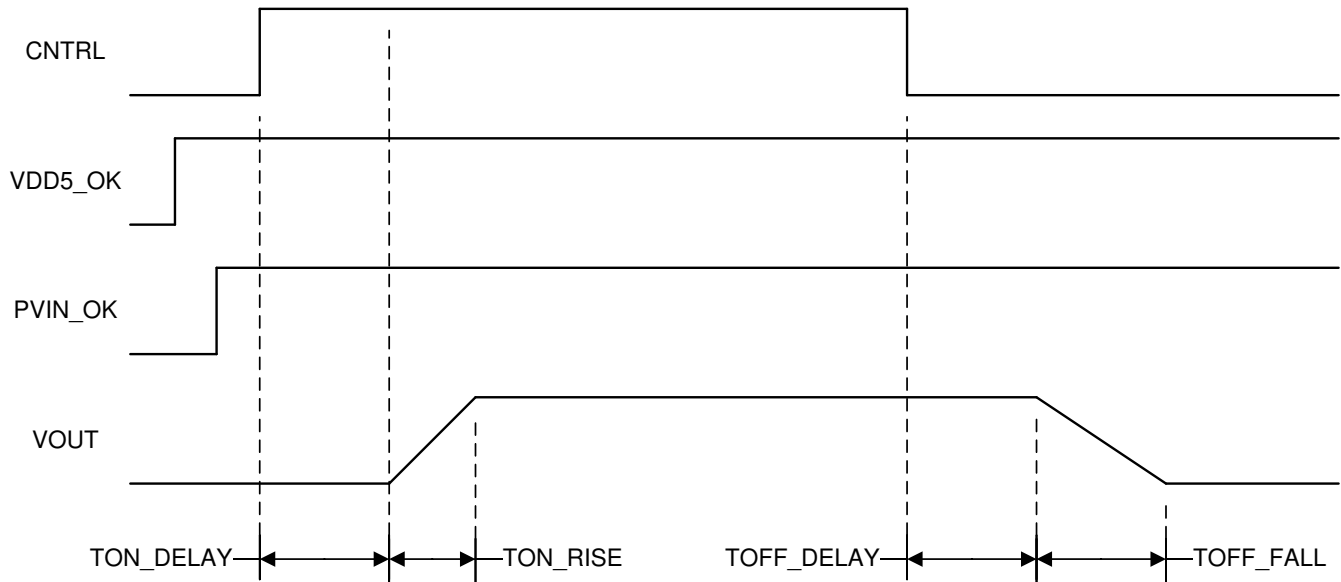


图 7-6. TPS546B24A Start-up and Shutdown

#### Note

The TPS546B24A requires time between the AVIN and VDD5 reaching their UVLO levels for pin-detection and PMBus Communication and valid sensing of EN/UVLO and PVIN\_OK. Once AVIN and VDD5 exceed their lower UVLO thresholds (2.9-V typ.), the TPS546B24A starts its power-on-reset, self-calibration, and pin-detection. This time delay,  $t_{\text{delay}(\text{uvlo\_PMBus})}$  (6 ms typ.) must be complete before PVIN\_OK or EN/UVLO sensing is enabled.

If VDD5<sub>PS\_ON</sub>, PVIN\_OK, and EN/UVLO are above their thresholds before the end of  $t_{\text{delay}(\text{uvlo\_PMBus})}$ , (60h) **TON\_DELAY** will start after  $t_{\text{delay}(\text{uvlo\_PMBus})}$  completes.

If VDD5<sub>PS\_ON</sub>, PVIN\_OK, or EN/UVLO are below their thresholds when  $t_{\text{delay}(\text{uvlo\_PMBus})}$  completes, (60h) **TON\_DELAY** will start when VDD5\_OK, PVIN\_OK, and EN/UVLO are all above their thresholds.

### 7.3.6 Differential Sense Amplifier and Feedback Divider

The TPS546B24A includes a fully integrated, internal, precision feedback divider and remote sense. Using both the selectable feedback divider and precision adjustable reference, output voltages up to 6.0 V can be obtained. The feedback divider can be programmed to divider ratios of 1:1, 1:2, 1:4, or 1:8 using the (29h) **VOUT\_SCALE\_LOOP** command.

The recommended operating range of (21h) **VOUT\_COMMAND** is dependent upon the feedback divider ratio configured (29h) **VOUT\_SCALE\_LOOP** as follows:

表 7-1. Recommended Range

(29h) <b>VOUT_SCALE_LOOP</b>	RECOMMENDED $V_{\text{OUT}}$ RANGE (V)
1	0.25 to 0.75
0.5	0.5 to 1.5
0.25	1 to 3
0.125	2 to 6

Setting (21h) **VOUT\_COMMAND** lower than the recommended range can negatively affect VOUT regulation accuracy while setting (21h) **VOUT\_COMMAND** above the recommended range can limit the actual output voltage achieved.

### Note

If the regulation output voltage is limited by the recommended range of the current (29h) [VOUT\\_SCALE\\_LOOP](#) value, VOUT can be below the intended (43h) [VOUT\\_UV\\_WARN\\_LIMIT](#) or (44h) [VOUT\\_UV\\_FAULT\\_LIMIT](#) without triggering their respective warning or faults due to the limited range of the reference voltage.

## 7.3.7 Set Output Voltage and Adaptive Voltage Scaling (AVS)

The initial output voltage can be set by the [VSEL](#) pin at AVIN power up. As part of power-on reset (POR), the VSEL pin senses both the resistance from the VSEL pin to AGND and the divider ratio of the VSEL pin between B1V5 and AGND. These values program (29h) [VOUT\\_SCALE\\_LOOP](#), (21h) [VOUT\\_COMMAND](#), (2Bh) [VOUT\\_MIN](#), and (24h) [VOUT\\_MAX](#) and select the appropriate settings for the internal feedback divider and precision adjustable reference voltage. Once the TPS546B24A completes its POR and enables PMBus communication, these initial values can be changed through PMBus communication.

- (20h) [VOUT\\_MODE](#)
- (21h) [VOUT\\_COMMAND](#)
- (29h) [VOUT\\_SCALE\\_LOOP](#)
- (22h) [VOUT\\_TRIM](#)
- (25h) [VOUT\\_MARGIN\\_HIGH](#)
- (26h) [VOUT\\_MARGIN\\_LOW](#)
- (01h) [OPERATION](#)
- (02h) [ON\\_OFF\\_CONFIG](#)

The output voltage can be programmed through PMBus and its value is related to the following registers:

- (24h) [VOUT\\_MAX](#)
- (2Bh) [VOUT\\_MIN](#)
- (40h) [VOUT\\_OV\\_FAULT\\_LIMIT](#)
- (42h) [VOUT\\_OV\\_WARN\\_LIMIT](#)
- (43h) [VOUT\\_UV\\_WARN\\_LIMIT](#)
- (44h) [VOUT\\_UV\\_FAULT\\_LIMIT](#)

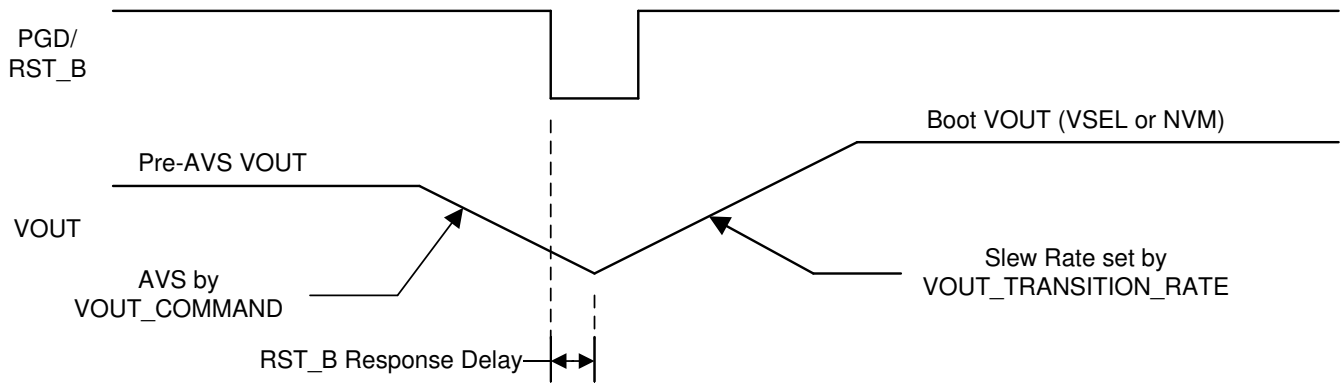
The TPS546B24A defaults to the relative format for the following, but can be changed to use absolute format through the PMBus command (20h) [VOUT\\_MODE](#):

- (25h) [VOUT\\_MARGIN\\_HIGH](#)
- (26h) [VOUT\\_MARGIN\\_LOW](#)
- (40h) [VOUT\\_OV\\_FAULT\\_LIMIT](#)
- (42h) [VOUT\\_OV\\_WARN\\_LIMIT](#)
- (43h) [VOUT\\_UV\\_WARN\\_LIMIT](#)
- (44h) [VOUT\\_UV\\_FAULT\\_LIMIT](#)

Refer to the detailed description of (20h) [VOUT\\_MODE](#) for details.

### 7.3.7.1 Reset Output Voltage

The (21h) [VOUT\\_COMMAND](#) value and the corresponding output voltage can be reset to the last selected power-on reset value set by [VSEL](#) or EEPROM as selected in the (EEh) [MFR\\_SPECIFIC\\_30 \(PIN\\_DETECT\\_OVERRIDE\)](#) command when the PGD/RST\_B pin function is set to RESET# in the (EDh) [MFR\\_SPECIFIC\\_29 \(MISC\\_OPTIONS\)](#) PMBus command. To reset (21h) [VOUT\\_COMMAND](#) to its last Power-On Reset value, when the RESET# optional function is enabled, assert the PGD/RST\_B pin low externally. While RESET# is asserted low, (21h) [VOUT\\_COMMAND](#) values received through PMBus is ACKed but no change in (21h) [VOUT\\_COMMAND](#) is made. When RESET# is selected in (EDh) [MFR\\_SPECIFIC\\_29 \(MISC\\_OPTIONS\)](#), an internal pullup on the PGD/RST\_B pin can be selected by the PULLUP# bit in the same PMBus command to eliminate the need for an external pullup with the RESET# function.



7-7. TPS546B24A Output Voltage Reset

### 7.3.7.2 Soft Start

To control the inrush current needed to charge the output capacitor bank during start-up, the TPS546B24A implements a soft-start time programmed by the (61h) [TON\\_RISE](#) command. When the device is enabled, the reference voltage ramps from 0 V to the final level defined by the following at a slew rate defined by the (61h) [TON\\_RISE](#) command:

- (21h) [VOUT\\_COMMAND](#)
- (29h) [VOUT\\_SCALE\\_LOOP](#)
- (22h) [VOUT\\_TRIM](#)
- (25h) [VOUT\\_MARGIN\\_HIGH](#)
- (26h) [VOUT\\_MARGIN\\_LOW](#)
- (01h) [OPERATION](#)

The TPS546B24A devices support several soft-start times from 0 ms to 31.75 ms in 250-μs steps (7 bits) selected by the (61h) [TON\\_RISE](#) command. The  $t_{ON\_RISE}$  time is selectable by pin-strapping through the [MSEL2](#) pin (eight options), PMBus programming, or both.

During soft start, when the PWM pulse width is shorter than the minimum controllable on-time, pulse skipping can be seen and the output can show larger ripple voltage than normal operation.

### 7.3.8 Prebiased Output Start-Up

The TPS546B24A limits current from being discharged from a pre-biased output voltage during start-up by preventing the low-side FET from forcing the SW node low until after the first PWM pulse turns on the high-side FET. Once VOSNS voltage exceeds the increasing reference voltage and high-side SW pulses start, the TPS546B24A limits the synchronous rectification during each SW period with a narrow on-time. The maximum low-side MOSFET on-time slowly increases on a cycle-by-cycle basis until 128 switch periods have elapsed and the synchronous rectifier runs fully complementary to the high-side MOSFET. This limits the sinking of current from a pre-biased output, and ensures the output voltage start-up and ramp-to regulation sequences are monotonically increasing.

In the event of a pre-biased output voltage greater than (40h) [VOUT\\_OV\\_FAULT\\_LIMIT](#), the TPS546B24A responds as soon as it completes POR and VDD5 is greater than its own 3.9-V UVLO, even if conversion is disabled by EN/UVLO or the PMBus (01h) [OPERATION](#) command.

### 7.3.9 Soft Stop and (65h) TOFF\_FALL Command

When enabled by (02h) [ON\\_OFF\\_CONFIG](#) or (01h) [OPERATION](#), the TPS546B24A implements (65h) [TOFF\\_FALL](#) command to force a controlled decrease of the output voltage from regulation to 0. There can be negative inductor current forced during the (65h) [TOFF\\_FALL](#) time to discharge the output voltage. The setting of (65h) [TOFF\\_FALL](#) of 0 ms means the unit to bring its output voltage down to 0 as quickly as possible, which results in an effective (65h) [TOFF\\_FALL](#) time of 0.5 ms. When disabled in the (02h) [ON\\_OFF\\_CONFIG](#) for the turnoff controlled by EN/UVLO pin or bit 6 of (01h) [OPERATION](#) if the regulator is turned off by (01h)

**OPERATION** command, both high-side and low-side FET drivers are turned off immediately and the output voltage slew rate is controlled by the discharge from the external load.

This feature is disabled for EN/UVLO in (02h) **ON\_OFF\_CONFIG** by default.

### 7.3.10 Power Good (PGOOD)

When conversion is enabled and  $t_{ON\_RISE}$  complete, if the output voltage remains between (43h) **VOUT\_UV\_WARN\_LIMIT** and (42h) **VOUT\_OV\_WARN\_LIMIT**, the PGOOD open-drain output is released and allowed to rise to an externally supplied logic level. Upon any fault condition with a shutdown response, the PGOOD open-drain output is asserted, forcing PGOOD low by default. See 表 7-4 for the possible sources to pull down the PGOOD pin.

The PGOOD signal can be connected to the EN/UVLO pin of another device to provide additional controlled turnon and turnoff sequencing.

### 7.3.11 Set Switching Frequency

An internal oscillator generates a 225-kHz to 1.5-MHz clock for PWM switching with 16 discrete programmable options. The switching frequency is selectable by pin-strapping through the resistor divider of **MSEL1** (8 options) and/or PMBus programming (16 options) using the (33h) **FREQUENCY\_SWITCH** command, listed in 表 7-2.

表 7-2. Oscillator  $f_{SW}$  Options

AVAILABLE $f_{SW}$ OPTIONS (kHz)	$f_{SW}$ PIN-STRAPPING OPTIONS (kHz)
225	
275	275
325	325
375	
450	450
550	550
650	650
750	
900	900
1100	1100
1300	
1500	1500

### 7.3.12 Frequency Synchronization

The oscillator can be synchronized to external clock (SYNC IN) or output a clock to synchronize other devices (SYNC out) on the SYNC pin. To support phase shifted clock for both multi-rail interleaving and multi-phase operation, the internal oscillator can be phase-shifted from the SYNC pin by 0, 90, 120, 180, 240, or 270 degrees for 1, 2, 3, or 4 phase operation. The SYNC IN or SYNC OUT function, and phase position of single phase or stand-alone devices can be selected by pin-strapping through resistor divider on at the **ADRSEL** pin, or by the resistor from the **MSEL2** pin to AGND for multi-phase slave devices.

In single output multi-phase stack configurations, the SYNC phase offset is programmed along with device count and phase position using the **MSEL2** pin. Slave devices in multi-phase stacks are always configured as SYNC\_IN while the master device can be configured for auto-detect, SYNC\_IN, or SYNC\_OUT through the resistor divider on the ADRSEL pin.

表 7-3. Pin Programmed Phase Positions through Resistor Divider (Single Phase Stand-Alone)

RDIV CODE (PIN STRAPPING)	PHASE POSITION (DEGREE)	SYNC IN/OUT
Open (No resistor to BP1V5)	0	Auto-detect In/Out
0, 1	0	In
2, 3	90	In
4, 5	120	In

**表 7-3. Pin Programmed Phase Positions through Resistor Divider (Single Phase Stand-Alone)**  
(continued)

RDIV CODE (PIN STRAPPING)	PHASE POSITION (DEGREE)	SYNC IN/OUT
6, 7	180	In
8, 9	240	In
10,11	270	In
12, 13	0	Out
14, 15	180	Out

After initial power up and pin detection, if SYNC IN/OUT is set as auto-detection configuration, the TPS546B24A senses the SYNC pin to determine if there is any external SYNC clock. Switching or a consistent pullup on the SYNC pin sets the device for SYNC\_IN while a consistent pulldown on SYNC sets the device for SYNC\_OUT. The TPS546B24A devices programmed to be loop slaves are always programmed to be SYNC IN.

When configured for SYNC\_IN, if SYNC input pulses are missed for two cycles, or the oscillator frequency drops below 50% of the free-running switching frequency, the device determines that SYNC clock is lost. If the TPS546B24A is part of a multi-phase stack, the converter shuts down and remains disabled until a SYNC signal is reestablished to prevent damage due to the loss of synchronization. Single phase stand-alone devices continues to operate at approximately 70% of the nominal frequency.

### 7.3.13 Loop Slave Detection

The GOSNS/SLAVE pin voltage is detected at power up. When it is pulled high to BP1V5, the device is recognized as loop slave. When the GOSNS/SLAVE pin is connected to the Output Ground, the TPS546B24A is configured as a loop master.

### 7.3.14 Current Sensing and Sharing

Both high-side and low-side FET use a SenseFET architecture for current sensing to achieve accurate and temperature compensated current monitoring. This SenseFET architecture uses the parasitic resistance of the FETs to achieve lossless current sense with no external components.

When multiple (2×, 3×, or 4×) devices operate in multi-phase application, all devices share the same internal control voltage through VSHARE pin. The sensed current in each phase is regulated by the VSHARE voltage by internal transconductance amplifier, to achieve loop compensation and current balancing between different phases. The amplifier output voltage is compared with an internal PWM ramp to generate the PWM pulse.

### 7.3.15 Telemetry

The telemetry sub-system in the controller core supports direct measurements of input voltage, output voltage, output current, and die temperature. The ADC supports internal rolling window averaging with rolling windows up to 16 previous measurements for accurate measurements of these key system parameters. Each ADC conversion requires less than 500 μs, allowing each telemetry value to be updated within 2 ms.

The current sense telemetry, which senses the low-side FET current at the start and end of each low-side FET on-time and averages the two measurements to monitor the average inductor current over-report current if the inductor current is non-linear during the low-side FET on-time, such as when the inductor is operating above its saturation current.

### 7.3.16 Overcurrent Protection

Both low-side overcurrent (OC) and high-side short circuit protection are implemented.

The low-side overcurrent fault and warning thresholds are programmed through PMBus and sensed across cycle-by-cycle average current through the low-side MOSFET and compared to the set warning or fault threshold while High-side pulses are terminated on a cycle-by-cycle basis, if the peak current through the high-side MOSFET exceeds the 1.5× the programmed low-side threshold.

When either a low-side overcurrent or high-side short circuit threshold is exceeded during a switching cycle, an OCP fault counter is incremented. If no overcurrent condition is detected in a switching cycle, the counter is

decremented. If the counter exceeds the delay selected by the (47h) *IOUT\_OC\_FAULT\_RESPONSE* PMBus value (default = 3) overcurrent fault condition is declared and the output shuts down. Restart and timing is also defined as part of (47h) *IOUT\_OC\_FAULT\_RESPONSE*.

The output OC fault thresholds and fault response are set through PMBUS. The OC fault response can be set to shutdown, restart, or ignore.

### 7.3.17 Overvoltage/Undervoltage Protection

The voltage on VOSNS pin is monitored to provide output voltage overvoltage (OV) and undervoltage (UV) protection. When VOSNS voltage is higher than OV fault threshold, OV fault is declared and the low-side FET is turned on to discharge the output voltage and eliminate the OV condition. The low-side FET remains on until the VOSNS voltage is discharged to 200 mV divide by the internal feedback divider as programmed by (29h) *VOUT\_SCALE\_LOOP*. Once the output voltage is discharged, the output is disabled and the converter times out and restarts according to the (41h) *VOUT\_OV\_FAULT\_RESPONSE* PMBus command. When VOSNS voltage is lower than UV fault threshold, UV fault is declared. After an initial delay programmed by the (45h) *VOUT\_UV\_FAULT\_RESPONSE* PMBus command, the output is disabled and the converter times out and restarts according to the (45h) *VOUT\_UV\_FAULT\_RESPONSE* PMBus command.

The output UV/OV fault thresholds and fault response are set through PMBUS. The UV/OV fault response can be set to shutdown, restart, or continue operating without interruption.

### 7.3.18 Overtemperature Management

There are two schemes of overtemperature protections in the TPS546B24A device:

1. On-chip die temperature sensor for monitoring and overtemperature protection (OTP)
2. The bandgap based thermal shutdown (TSD) protection. TSD provides OT fail-safe protection in the event of a failure of the temperature telemetry system, but can be disabled through (50h) *OT\_FAULT\_RESPONSE* for high temperature testing

The overtemperature protection (OTP) threshold is set through PMBus and compares the (8Dh) *READ\_TEMPERATURE\_1* telemetry to the (51h) *OT\_WARN\_LIMIT* and (4Fh) *OT\_FAULT\_LIMIT*. The overtemperature (OT) fault response can be set to shutdown, restart, or continue operating without interruption.

### 7.3.19 Fault Management

For the response on OC fault, OT fault, and thermal shutdown for multi-phase stack, the shutdown response has the highest priority, followed by restart response. Continue operating without interruption response has the lowest priority.

When multiple faults occur in rapid succession, it is possible for the first fault to occur to mask the second fault. If the first fault to be detected is configured to continue operating without interruption, and the second fault is configured to shutdown and restart, the second fault will shutdown but can fail to restart as programmed.

**表 7-4. Fault Protection Summary**

FAULT OR WARNING	PROGRAMMING	FAULT RESPONSE SETTING	FET BEHAVIOR	ACTIVE DURING $t_{ON\_RISE}$	SMB_ALERT	MASKABLE	PGOOD LOGIC
Internal OT fault	(4Fh) <i>OT_FAULT_LIMIT</i>	Shutdown	Both FETs off	Yes	Y	Y	Low
		Restart	Both FETs off, restart				High
		Ignore	FETS still controlled by PWM				
Internal OT warning	(51h) <i>OT_WARN_LIMIT</i>	Shutdown or restart on Fault	FETS still controlled by PWM	Yes	Y	Y	High
		Ignore fault					
TSD	Threshold fixed internally	Shutdown	Both FETs off	Yes	Y	Y	Low
		Restart	Both FETs off, restart				High
		Ignore	FETS still controlled by PWM				
Low Side OC fault	(46h) <i>IOUT_OC_FAULT_LIMIT</i>	Shutdown	3 PWM counts, then both FETs off	Yes	Y	Y	Low
		Restart	3 PWM counts, then both FETs off, restart after [DELAY]* $t_{ON\_RISE}$				High
		Ignore	FETS still controlled by PWM				

**表 7-4. Fault Protection Summary (continued)**

FAULT OR WARNING	PROGRAMMING	FAULT RESPONSE SETTING	FET BEHAVIOR	ACTIVE DURING $t_{ON\_RISE}$	SMB_ALERT	MASKABLE	PGOOD LOGIC
Low Side OC warning	(4Ah) IOUT_OC_WARN_LIMIT	Shutdown or restart on Fault	FETS still controlled by PWM	Yes	Y	Y	High
		Ignore fault					
Negative OC fault (lower priority than OVF)	N/A	Enable	Turn off LS FET	Yes	Y	Y	Low
		Disable	FETS still controlled by PWM				High
High side OC fault	(46h) IOUT_OC_FAULT_LIMIT	Shutdown	3 cycles of pulse-by-pulse current limiting followed by both FETs off	Yes	Y	Y	Low
		Restart	3 cycles of pulse-by-pulse current limiting followed by both FETs off, restart after [DELAY]* $t_{ON\_RISE}$				
		Ignore	FETS still controlled by PWM				High
Vout OV fault	(40h) VOUT_OV_FAULT_LIMIT	Shutdown	LS FET latched ON or turned on till V <sub>OUT</sub> reaches 200mV/ VOUT_SCALE_LOOP; HS FET OFF	No	Y	Y	Low
		Restart	LS FET latched ON or turned on till V <sub>OUT</sub> reaches 200mV/ VOUT_SCALE_LOOP; HS FET OFF, restart after [DELAY] * $t_{ON\_RISE}$				
		Ignore	FETS still controlled by PWM				High
V <sub>OUT</sub> OVF fix	(40h) VOUT_OV_FAULT_LIMIT	Shutdown	LS FET latched ON or turned on till V <sub>OUT</sub> reaches 200mV/ VOUT_SCALE_LOOP; HS FET OFF	Yes	Y	Y	Low
		Restart	LS FET latched ON or turned on till V <sub>OUT</sub> reaches 200mV/ VOUT_SCALE_LOOP; HS FET OFF, restart after [DELAY]* $t_{ON\_RISE}$				
		Ignore	FETS still controlled by PWM				High
Vout OV warning	(42h) VOUT_OV_WARN_LIMIT	Shutdown or restart on Fault	FETS still controlled by PWM	No	Y	Y	High
		Ignore Fault					
Vout UV fault	(44h) VOUT_UV_FAULT_LIMIT	Shutdown	Both FETs off	No	Y	Y	Low
		Restart	Both FETs off, restart after [DELAY]* $t_{ON\_RISE}$				
		Ignore	FETS still controlled by PWM				High
Vout UV warning	(43h) VOUT_UV_WARN_LIMIT	Shutdown or restart on Fault	FETS still controlled by PWM	No	Y	Y	Low
		Ignore fault					
$t_{ON\_MAX}$ fault	(62h) TON_MAX_FAULT_LIMIT	Shutdown	Both FETs off	Yes	Y	Y	Low
		Restart	Both FETs off, restart after [DELAY]* $t_{ON\_RISE}$				
		Ignore	FETS still controlled by PWM				High
PVin UVLO	(35h) VIN_ON, (36h) VIN_OFF	Shutdown	Both FETs off	Yes	Y	Y	Low
PVIN OV FAULT	(55h) VIN_OV_FAULT_LIMIT	Shutdown	Both FETs off	Yes	Y	Y	Low
		Restart	Both FETs off, restart				
		Ignore	FETS still controlled by PWM				High
BCX_fault	N/A	N/A	FETS still controlled by PWM	Yes	Y	Y	High
Pin Strap_NonConverge	N/A	VSEL	Both FETs off, pull low VSHARE	No (active before $t_{ON\_RISE}$ )	N	N/A	Low
		MSEL1					
		MSEL2					
		ADRSEL					
SYNC_Fault	N/A	Loop master or stand-alone device	FETS still controlled by PWM	Yes	N	N/A	High
		Slave device	Both FETs off, pull low VSHARE				Low
SYNC_High/Low	N/A	Loop master or stand-alone device	FETS still controlled by PWM	Yes	N	N/A	High
		Slave device	Both FETs off, pull low VSHARE				Low



### 7.3.20 Back-Channel communication

To allow multiple devices with a shared output to communicate through a single PMBus address and single PMBus slave, the TPS546B24A uses a back-channel communication implemented through BCX\_CLK and BCX\_DAT pins. During POR, all of the devices connected to VSHARE must also be connected to BCX\_CLK and BCX\_DAT and have appropriate (ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) settings. Any programming error among the devices of a stack will result in a POR fault and prevent enabling of conversion.

During POR, the loop master reads the programmed values from the loop slaves to ensure all expected slaves are present and correctly phase-shifted. Then, the Master will load critical operating parameters such as the following to the slave devices to ensure correct operation of the STACK:

- (B1h) USER\_DATA\_01 (COMPENSATION\_CONFIG)
- (33h) FREQUENCY\_SWITCH
- (61h) TON\_RISE
- (21h) VOUT\_COMMAND

During operation, the master device receives and responds to all PMBus communication, and slave devices do not need to be connected to the PMBus. If the master receives commands that require updates to the PMBus registers of the slave, the master relays these commands to the slaves. Additionally, the master periodically polls slave devices for status and telemetry information to maintain an accurate record of the telemetry and STATUS information for the full stack of devices.

Most PMBus communication should be directed to all phases by leaving the (04h) PHASE PMBus command at its Power On Reset default value of FFh. If a specific device must be communicated with, the (04h) PHASE command can be changed to address a specific device within the stack, as set by the order value of the (37h) INTERLEAVE command programmed during POR.

When commands are directed to individual slaves, write commands are queued by the master to be sent to the slaves through the BCX if other BCX communication is in progress. Queued write commands are written to the slaves in the order the master receives them. To avoid unnecessary delays on the PMBus and excessive clock stretching, read transactions targeting individual slaves are not queued, and will be processed as soon as the BCX bus is available. As a result, it is possible for a read command targeting an individual slave immediately following a write command can be processed before the preceding write command. To ensure accurate read-back, users must allow a minimum of 4 ms between writing a value to an individual slave and reading that same value back from the same slave.

### 7.3.21 Switching Node (SW)

The SW pin connects to the switching node of the power conversion stage. It acts as the return path for the highside gate driver. When configured as a synchronous buck stage, the voltage swing on SW normally traverses from below ground to well above the input voltage. Parasitic inductance in the high-side FET and the output capacitance (COSS) of both power FETs form a resonant circuit that can produce high frequency (> 100 MHz) ringing on this node. The voltage peak of this ringing, if not controlled, can be significantly higher than the input voltage. Ensure that the peak ringing amplitude does not exceed the absolute maximum rating limit for the pin.

In many cases, a series resistor and capacitor snubber network connected from the switching node to PGND can be helpful in damping the ringing and decreasing the peak amplitude. Provide provisions for snubber network components in the layout of the printed circuit board. If testing reveals that the ringing amplitude at the SW pin exceeds the limit, then include snubber components.

### 7.3.22 PMBus General Description

Timing and electrical characteristics of the PMBus interface specification can be found in the *PMB Power Management Protocol Specification, Part 1, revision 1.3* available at <http://pmbus.org>. The TPS546B24A device supports both the 100-kHz, 400-kHz, and 1-MHz bus timing requirements.

The TPS546B24A uses clock stretching during PMBus communication, but only stretches the clock during specific bits of the transaction.



- The TPS546B24A does not stretch the clock during the address byte of any transaction.
- The TPS546B24A can stretch the clock between bit 0 of the command byte and its ACK response.
- The TPS546B24A stretches the clock after bit 0 of the read address of a read transaction.
- The TPS546B24A stretches the clock between bit 0 of the last byte of data and its ACK response
- The TPS546B24A can stretch the clock between bit 1 and bit zero of every fourth byte of data for blocks with more than four bytes of data.

Communication over the PMBus interface can either support the packet error checking (PEC) scheme or not. If the master supplies clock (CLK) pulses for the PEC byte, PEC is used. If the CLK pulses are not present before a STOP, the PEC is not used. If PEC will always be used, consider enabling Require PEC in [\(EDh\) MFR\\_SPECIFIC\\_29 \(MISC\\_OPTIONS\)](#) to configure the TPS546B24A to reject any write transaction that does not include CLK pulses for a PEC byte.

The device supports a subset of the commands in the *PMBus 1.3 Power Management Protocol Specification*. See [Supported PMBus Commands](#) for more information

The TPS546B24A also supports the SMB\_ALERT response protocol. The SMB\_ALERT response protocol is a mechanism by which the TPS546B24A can alert the bus master that it has experienced an alert and has important information for the host. The host should process this event and simultaneously accesses all slaves on the bus that support the protocol through the alert response address. All slaves that are asserting SMB\_ALERT should acknowledge this request with their PMBus Address. The host performs a modified receive byte operation to get the address of the slave. At this point, the master can use the PMBus status commands to query the slave that caused the alert. For more information on the SMBus alert response protocol, see the system management bus (SMBus) specification. Persistent faults associated with status registers other than [\(7Eh\) STATUS\\_CML](#) will reassert SMB\_ALERT after responding to the host alert response address.

The TPS546B24A contains non-volatile memory that is used to store configuration settings and scale factors. The settings programmed into the device are not automatically saved into this non-volatile memory. The [\(15h\) STORE\\_USER\\_ALL](#) command must be used to commit the current PMBus settings to non-volatile memory as device defaults. The settings that are capable of being stored in non-volatile memory are noted in their detailed descriptions.

All pin programmable values can be committed to non-volatile memory. The POR default selection between pin programmable values and non-volatile memory can be selected by the manufacturer specific [\(EEh\) MFR\\_SPECIFIC\\_30 \(PIN\\_DETECT\\_OVERRIDE\)](#) command.

### 7.3.23 PMBus Address

The PMBus specification requires that each device connected to the PMBus have a unique address on the bus. The TPS546B24A PMBus address is determined by the value of the resistor connected between [ADRSEL](#) and AGND and is programmable over the range from 0x10 – 0x2F, providing 32 unique PMBus addresses.

### 7.3.24 PMBus Connections

The TPS546B24A supports the 100-kHz, 400-kHz, and 1-MHz bus speeds. Connection for the PMBus interface must follow the high power DC specifications given in section 3.1.3 in the SMBus specification V2.0 for the 400-kHz bus speed or the low power DC specifications in section 3.1.2. The complete SMBus specification is available from the SMBus web site, [smiforum.org](http://smiforum.org)

The PMBus interface pins: PMB\_CLK, PMB\_DATA, and SMB\_ALRT require external pullup resistors to a 1.8-V to 5.5-V termination. Pullup resistors should be sized to meet the minimize rise-time required for the desired PMBus clock speed but should not source more current than the lowest rated CLK, DATA, or SMB\_ALRT pin on the bus when the bus voltage is forced to 0.4 V. The TPS546B24A supports a minimum of 20 mA of sink current on PMB\_CLK, PMB\_DATA, and SMB\_ALRT.

## 7.4 Device Functional Modes

### 7.4.1 Programming Mode

The TPS546B24A devices can operate in programming mode when AVIN and VDD5 are powered above their lower UVLO but VDD5 and PVIN are not powered above their UVLO to enable conversion. In programing mode, the TPS546B24A accepts and respond to PMBus commands but does not enable switching or conversion. While

PMBus commands can be accepted and processed with VDD5 lower than 3 V, NVM programming through the [\(15h\) STORE\\_USER\\_ALL](#) command must not be used when VDD5 is less than 3 V.

Programming mode allows the TPS546B24A to complete POR and to be configured through PMBus from a 3.3-V supply without PVIN present.

## 7.4.2 StandAlone/Master/Slave Mode Pin Connections

The TPS546B24A can be programmed as a Stand-Alone device (Single Output, Single Phase) Master device of a single-output multi-phase stack of devices, or a Slave device to a master of a multi-phase stack. The details of the recommended pin connects for each configuration is given in [表 7-5](#).

**表 7-5. Stand-Alone/Master/Slave pin connections**

PIN	STAND ALONE	MASTER	SLAVE
GOSNS	Ground at Output Regulation Point	Ground at Output Regulation Point	BP1V5
VOSNS	Vout at Output Regulation Point	Vout at Output Regulation Point	Float or connect to divider for other voltage to be monitored
EN/UVLO	Enable/Control or Resistor Divider from PVIN	Enable/Control or Resistor Divider from PVIN	Connect to EN/UVLO of the Master
MSEL1	<a href="#">Programming MSEL1</a>	<a href="#">Programming MSEL1</a>	Short to PGND (Thermal Pad)
MSEL2	<a href="#">Programming MSEL2</a>	<a href="#">Programming MSEL2</a>	<a href="#">Programming MSEL2 for a Slave Device (GOSNS Tied to BP1V5)</a>
VSEL	<a href="#">Programming VSEL</a>	<a href="#">Programming VSEL</a>	Short to PGND (Thermal Pad)
ADRSEL	<a href="#">Programming ADRSEL</a>	<a href="#">Programming ADRSEL</a>	Short to PGND (Thermal Pad)
VSHARE	Float or Bypass to AGND with capacitor	Connect to VSHARE of the Slave	Connect to VSHARE of the Master
SYNC	Float or External Sync	External Sync or Slave SYNC	Connect to SYNC of the Master
PMB_CLK	Connect to System PMBus or PGND (Thermal Pad) if not used	Connect to System PMBus or PGND (Thermal Pad) if not used	Short to PGND (Thermal Pad)
PMB_DATA	Connect to System PMBus or PGND (Thermal Pad) if not used	Connect to System PMBus or PGND (Thermal Pad) if not used	Short to PGND (Thermal Pad)
SMB_ALRT	Connect to System PMBus or PGND (Thermal Pad) if not used	Connect to System PMBus or PGND (Thermal Pad) if not used	Short to PGND (Thermal Pad)
BCX_CLK	Short to PGND (Thermal Pad)	Connect to Slaves BCX_CLK	Connect to BCX_CLK of the Master
BCX_DAT	Short to PGND (Thermal Pad)	Connect to Slaves BCX_DAT	Connect to BCX_DAT of the Master
PGOOD/RST_B	Connect to System PGD or RESET# or PGND (Thermal Pad) if not used	Connect to System PGD or RESET# or PGND (Thermal Pad) if not used	Short to PGND (Thermal Pad)

## 7.4.3 Continuous Conduction Mode

The TPS546B24A devices operate in continuous conduction mode (CCM) at a fixed frequency, regardless of the output current. During soft start, some of the low-side MOSFET on-times are limited to prevent excessive current sinking in the event the device is started with a prebiased output. After the first PWM pulse, and with each successive PWM pulse, this limit is increased to allow more low-side FET on-time and transition to CCM. Once this transition has completed, the low-side MOSFET and the high-side MOSFET on-times are fully complementary.

## 7.4.4 Operation With CNTL Signal (EN/UVLO)

According to the value in the [\(02h\) ON\\_OFF\\_CONFIG](#) command, the TPS546B24A devices can be commanded to use the EN/UVLO pin to enable or disable regulation, regardless of the state of the [\(01h\) OPERATION](#) command. The EN/UVLO pin can be configured as either active high or active low (inverted) logic. To use EN/UVLO pin as a programmable UVLO, the polarity set by [\(02h\) ON\\_OFF\\_CONFIG](#) must be positive logic.

### 7.4.5 Operation with Control

According to the value in the (02h) [ON\\_OFF\\_CONFIG](#) register, the TPS546B24A devices can be commanded to use the (01h) [OPERATION](#) command to enable or disable regulation, regardless of the state of the EN/UVLO pin.

### 7.4.6 Operation with CNTL and Control

According to the value in the (02h) [ON\\_OFF\\_CONFIG](#) command, the TPS546B24A devices can be commanded to require both a CNTL signal from the EN/UVLO pin, and the (01h) [OPERATION](#) command to enable or disable regulation.

## 7.5 Programming

### 7.5.1 Supported PMBus Commands

The commands listed in [表 7-6](#) are implemented as described to conform to the PMBus 1.3 specification. [表 7-6](#) also lists the default for the bit behavior and register values.

**表 7-6. Supported PMBus Commands and Default Values**

CMD CODE (HEX)	COMMAND NAME (PMBus 1.3 SPEC)	DEFAULT VALUE
01h	<a href="#">OPERATION</a>	04h
02h	<a href="#">ON_OFF_CONFIG</a>	17h
03h	<a href="#">CLEAR_FAULTS</a>	n/a
04h	<a href="#">PHASE</a>	FFh
10h	<a href="#">WRITE_PROTECT</a>	00h
15h	<a href="#">STORE_USER_ALL</a>	n/a
16h	<a href="#">RESTORE_USER_ALL</a>	n/a
19h	<a href="#">CAPABILITY</a>	D0h
1Bh	<a href="#">SMBALERT_MASK</a>	n/a
20h	<a href="#">VOUT_MODE</a>	97h
21h	<a href="#">VOUT_COMMAND</a>	019Ah
22h	<a href="#">VOUT_TRIM</a>	0000h
24h	<a href="#">VOUT_MAX</a>	0C00h
25h	<a href="#">VOUT_MARGIN_HIGH</a>	021Ah
26h	<a href="#">VOUT_MARGIN_LOW</a>	01E6h
27h	<a href="#">VOUT_TRANSITION_RATE</a>	E010h
29h	<a href="#">VOUT_SCALE_LOOP</a>	C840h
2Bh	<a href="#">VOUT_MIN</a>	0100h
33h	<a href="#">FREQUENCY_SWITCH</a>	01C2h
35h	<a href="#">VIN_ON</a>	F00Bh
36h	<a href="#">VIN_OFF</a>	F00Ah
37h	<a href="#">INTERLEAVE</a>	0020h
38h	<a href="#">IOUT_CAL_GAIN</a>	C880h
39h	<a href="#">IOUT_CAL_OFFSET</a>	E000h
40h	<a href="#">VOUT_OV_FAULT_LIMIT</a>	024Dh
41h	<a href="#">VOUT_OV_FAULT_RESPONSE</a>	BDh
42h	<a href="#">VOUT_OV_WARN_LIMIT</a>	022Eh
43h	<a href="#">VOUT_UV_WARN_LIMIT</a>	01CCh
44h	<a href="#">VOUT_UV_FAULT_LIMIT</a>	01B2h
45h	<a href="#">VOUT_UV_FAULT_RESPONSE</a>	BEh
46h	<a href="#">IOUT_OC_FAULT_LIMIT</a>	F068h
47h	<a href="#">IOUT_OC_FAULT_RESPONSE</a>	FFh

**表 7-6. Supported PMBus Commands and Default Values (continued)**

CMD CODE (HEX)	COMMAND NAME (PMBus 1.3 SPEC)	DEFAULT VALUE
4Ah	IOUT_OC_WARN_LIMIT	F050h
4Fh	OT_FAULT_LIMIT	0096h
50h	OT_FAULT_RESPONSE	BCh
51h	OT_WARN_LIMIT	007Dh
55h	VIN_OV_FAULT_LIMIT	0015
56h	VIN_OV_FAULT_RESPONSE	3Ch
58h	VIN_UV_WARN_LIMIT	F00Ah
60h	TON_DELAY	F800h
61h	TON_RISE	F00Ch
62h	TON_MAX_FAULT_LIMIT	F800h
63h	TON_MAX_FAULT_RESPONSE	3Bh
64h	TOFF_DELAY	F800h
65h	TOFF_FALL	F002h
78h	STATUS_BYTE	00h
79h	STATUS_WORD	00h
7Ah	STATUS_VOUT	00h
7Bh	STATUS_IOUT	00h
7Ch	STATUS_INPUT	00h
7Dh	STATUS_TEMPERATURE	00h
7Eh	STATUS_CML	00h
7Fh	STATUS_OTHER	00h
80h	STATUS_MFR_SPECIFIC	00h
88h	READ_VIN	n/a
8Bh	READ_VOUT	n/a
8Ch	READ_IOUT	n/a
8Dh	READ_TEMPERATURE_1	n/a
98h	PMBUS_REVISION	33h
99h	MFR_ID	00 00 00h
9Ah	MFR_MODEL	00 00 00h
9Bh	MFR_REVISION	00 00 00h
9Eh	MFR_SERIAL	00 00 00h
ADh	IC_DEVICE_ID	54 49 54 6B 24 41h
AEh	IC_DEVICE_REV	40 00h
B1h	USER_DATA_01 (COMPENSATION_CONFIG)	22 18 C2 1D 06h
B5h	USER_DATA_05 (POWER_STAGE_CONFIG)	70h
D0h	MFR_SPECIFIC_00 (TELEMETRY_CONFIG)	03 03 03 03 03 00h
DAh	MFR_SPECIFIC_10 (READ_ALL)	n/a
DBh	MFR_SPECIFIC_11 (STATUS_ALL)	n/a
E3h	MFR_SPECIFIC_19 (PGOOD_CONFIG)	009Fh
E4h	MFR_SPECIFIC_20 (SYNC_CONFIG)	F0h
ECh	MFR_SPECIFIC_28 (STACK_CONFIG)	0000h
EDh	MFR_SPECIFIC_29 (MISC_OPTIONS)	0000h
EEh	MFR_SPECIFIC_30 (PIN_DETECT_OVERRIDE)	1F2Fh
EFh	MFR_SPECIFIC_31 (SLAVE_ADDRESS)	24h
F0h	MFR_SPECIFIC_32 (NVM_CHECKSUM)	E9E0h

**表 7-6. Supported PMBus Commands and Default Values (continued)**

CMD CODE (HEX)	COMMAND NAME (PMBus 1.3 SPEC)	DEFAULT VALUE
F1h	<a href="#">MFR_SPECIFIC_33 (SIMULATE_FAULTS)</a>	0000h
FCh	<a href="#">MFR_SPECIFIC_44 (FUSION_ID0)</a>	02D0h
FDh	<a href="#">MFR_SPECIFIC_45 (FUSION_ID1)</a>	54 49 4C 4F 43 4Bh

## 7.5.2 Pin Strapping

The TPS546B24A provides four IC pins that allow the initial PMBus programming value on critical PMBus commands to be selected by the resistors connected to that pin without requiring PMBus communication. Whether a specific PMBus command is initialized to the value selected by the detected resistance or stored NVM memory is determined by the commands bit in the PIN\_DETECT\_OVERRIDE PMBus Command. The four pins and the commands they program for a Master or Stand-alone device (GOSNS connected to Ground) are provided in [表 7-7](#).

Each pin can be programmed in one of four ways:

- Pin shorted to AGND with less than 20  $\Omega$
- Pin floating or tied to BP1V5 with more than 1 M $\Omega$
- Pin bypassed to AGND through a 1% or better tolerance resistor according to R2G code only (16 Resistor Options)
- Pin bypassed to AGND through a 1% or better tolerance resistor according to R2G code and to BP1V5 according to Divider Code (16 Resistor x 16 Resistor Divider Options)

Due to the flexibility of programming options with up to 274 configurations per pin, it is recommended that designers consider using one of the available design tools, such as [TPS546x24A Compensation and Pin-Strap Resistor Calculator](#) to assist with proper programming resistor selection.

**表 7-7. TPS546B24A Pin Programming Summary**

PIN	RESISTORS	PMBus REGISTERS
<a href="#">MSEL1</a>	Resistor to AGND	<a href="#">COMPENSATION_CONFIG</a>
	Resistor Divider	<a href="#">COMPENSATION_CONFIG</a> , <a href="#">FREQUENCY_SWITCH</a>
<a href="#">MSEL2</a>	Resistor to AGND	<a href="#">IOUT_OC_WARN_LIMIT</a> , <a href="#">IOUT_OC_FAULT_LIMIT</a> , <a href="#">STACK_CONFIG</a>
	Resistor Divider	<a href="#">TON_RISE</a>
<a href="#">VSEL</a>	Both	<a href="#">VOUT_COMMAND</a> , <a href="#">VOUT_SCALE_LOOP</a> , <a href="#">VOUT_MAX</a> , <a href="#">VOUT_MIN</a>
<a href="#">ADRSEL</a>	Resistor to AGND	<a href="#">SLAVE_ADDRESS</a>
	Resistor Divider	<a href="#">SLAVE_ADDRESS</a> , <a href="#">SYNC_CONFIG</a> , <a href="#">INTERLEAVE</a>

### Note

Resistor divider values of "none" can be implemented with no resistor to BP1V5 or use a 1-M $\Omega$  resistor to BP1V5 for improved reliability and noise immunity.

Slave Devices with GOSNS tied to BP1V5 only use the resistor from [MSEL2](#) to AGND to program the following:

- [\(4Ah\) IOUT\\_OC\\_WARN\\_LIMIT](#)
- [\(46h\) IOUT\\_OC\\_FAULT\\_LIMIT](#)
- [\(ECh\) MFR\\_SPECIFIC\\_28 \(STACK\\_CONFIG\)](#)
- [\(37h\) INTERLEAVE](#)

The slave receives all other pin programmed values from the master over BCX as part of the power-on reset function.

### Note

The high precision Pin-Detection programming which provides 8-bit resolution for each pin in the TPS546B24A can be sensitive to PCB contamination from flux, moisture, and debris. As such, users should consider committing Pin Programmed values to User Non-Volatile memory and disable future use of Pin Strapped values as part of the product flow. The programming sequence to commit Pin Programmed PMBus register values to NVM and disable future use of Pin Strapped programming is:

- Select [MSEL1](#), [MSEL2](#), [VSEL](#) and [ADRSEL](#) programming resistors to program the desired PMBus register values.
- Power AVIN and VDD5 above their UVLOs to initiate pin detection and enable PMBus communication.
- Update any PMBus register values not programmed to their final value by Pin Detection.
- Write the value 0000h using the Write Word protocol to [\(EEh\) MFR\\_SPECIFIC\\_30 \(PIN\\_DETECT\\_OVERRIDE\)](#).
- Send the command code 15h using the Send Byte protocol to initialize a [\(15h\) STORE\\_USER\\_ALL](#) function.
- Allow a minimum 100 ms for the device to complete a burn of NVM User Store. Loss of AVIN or VDD5 power during this 100 ms can compromise the integrity of the NVM. Failure to complete the NVM burn can result in a corruption of NVM and a POR fault on subsequent power on resets.

#### 7.5.2.1 Programming MSEL1

The MSEL1 pin programs [\(B1h\) USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#) and [\(33h\) FREQUENCY\\_SWITCH](#). The resistor divider ratio for MSEL1 selects the nominal switching frequency using 表 7-8:

表 7-8. MSEL1 Divider Code for Programming

RESISTOR DIVIDER CODE	<a href="#">COMPENSATION_CONFIG (CONFIG #)</a>	<a href="#">FREQUENCY_SWITCH VALUE (kHz)</a>
None (No Resistor to BP1V5)	7 - 25 (Select Values)	550
0	0-15	275
1	16-31	
2	0-15	325
3	16-31	
4	0-15	450
5	16-31	
6	0-15	550
7	16-31	
8	0-15	650
9	16-31	
10	0-15	900
11	16-31	
12	0-15	1100
13	16-31	
14	0-15	1500
15	16-31	

The resistor to ground for MSEL1 selects the [\(B1h\) USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#) values to program the following voltage loop and current loop gains. For options other than the EEPROM code (MSEL1 shorted to AGND or MSEL1 to AGND resistor code 0), the Current and Voltage loop zero and pole frequencies

are scaled with the programmed switching frequency. The current loop pole frequency is scale located at approximately the switching frequency, while the current loop zero is located at approximately 1/20 the switching frequency. the voltage loop pole is located at approximately ½ the switching frequency and the voltage loop zero is located at approximately 1/100 the switching frequency.

**表 7-9. MSEL1 Resistor to AGND Code with no Divider Programming**

RESISTOR CODE	COMPENSATION (NO DIVIDER)			COMPENSATION (EVEN DIVIDER)			COMPENSATION (ODD DIVIDER)		
	CONFIG #	I LOOP GAIN	V LOOP GAIN	CONFIG #	I LOOP GAIN	V LOOP GAIN	CONFIG #	I LOOP GAIN	V LOOP GAIN
Short	3	2	2	N/A	N/A	N/A	N/A	N/A	N/A
Float	EEPROM	EEPROM	EEPROM	N/A	N/A	N/A	N/A	N/A	N/A
0	7	3	1	0	EEPROM	EEPROM	16	5	0.5
1	8	3	2	1	2	0.5	17	5	1
2	9	3	4	2	2	1	18	5	2
3	10	3	8	3	2	2	19	5	4
4	12	4	1	4	2	4	20	5	8
5	13	4	2	5	2	8	21	6	0.5
6	14	4	4	6	3	0.5	22	6	1
7	15	4	8	7	3	1	23	6	2
8	17	5	1	8	3	2	24	6	4
9	18	5	2	9	3	4	25	6	8
10	19	5	4	10	3	8	26	7	0.5
11	20	5	8	11	4	0.5	27	7	1
12	22	6	1	12	4	1	28	7	2
13	23	6	2	13	4	2	20	7	4
14	24	6	4	14	4	4	30	7	8
15	25	6	8	15	4	8	21	10	2

With both the resistor to ground code and the resistor divider code, use the look-up table to select the appropriate resistors.

#### 7.5.2.2 Programming MSEL2

The resistor divider on MSEL2 pin programs the (61h) *TON\_RISE* value to select the soft-start time used by the TPS546B24A.

**表 7-10. MSEL2 Divider Code for Programming**

RESISTOR DIVIDER CODE	TON_RISE VALUE (ms)
None (No Resistor to BP1V5)	3
Short to AGND	
Float	
0	0.5
1	1
2	3
3	5
4	7
5	10
6	20
7	31.75

The resistor to ground for MSEL2 selects the (4Ah) *IOUT\_OC\_WARN\_LIMIT*, (46h) *IOUT\_OC\_FAULT\_LIMIT*, and (ECh) *MFR\_SPECIFIC\_28 (STACK\_CONFIG)* values using 表 7-11.

**表 7-11. MSEL2 Resistor to AGND Code for IOUT\_OC\_WARN/FAULT\_LIMIT and STACK Programming**

RESISTOR TO AGND CODE	STACK_CONFIG(NUMBER OF SLAVES / # OF PHASES)	OC_FAULT (A) / OC_WARN (A)
Short	0000h (0 Slaves, Stand-alone)	20/26
Float	0001h (1 Slave, 2-phase)	20/26
0	0000h (0 Slaves, Stand-alone)	20/26
1	0001h (1 Slave, 2-phase)	
2	0002h (2 Slaves, 3-phase)	
3	0003h (3 Slaves, 4-phase)	
4	0000h (0 Slaves, Stand-alone)	15/19
5	0001h (1 Slave, 2-phase)	
6	0002h (2 Slaves, 3-phase)	
7	0003h (3 Slaves, 4-phase)	
8	0000h (0 Slaves, Stand-alone)	10/14
9	0001h (1 Slave, 2-phase)	
10	0002h (2 Slaves, 3-phase)	
11	0003h (3 Slaves, 4-phase)	
12	0000h (0 Slaves, Stand-alone)	6/9
13	0001h (1 Slave, 2-phase)	
14	0002h (2 Slaves, 3-phase)	
15	0003h (3 Slaves, 4-phase)	

### 7.5.2.3 Programming VSEL

The resistor divider ratio for VSEL programs the (21h) *VOUT\_COMMAND* range, (29h) *VOUT\_SCALE\_LOOP* divider, (2Bh) *VOUT\_MIN*, and (24h) *VOUT\_MAX* levels according to the following tables.

Select the resistor divider code that contains the desired nominal boot voltage within the range of  $V_{OUT}$  between minimum  $V_{OUT}$  and maximum  $V_{OUT}$ . For voltages from 0.5 V to 1.25 V, a single resistor to ground or a resistor divider can be used.



表 7-12. VSEL Resistor Divider Code for Programming

NOMINAL BOOT VOLTAGE RANGE			RESISTOR DIVIDER CODE
MINIMUM $V_{OUT}$	MAXIMUM $V_{OUT}$	RESOLUTION	
EEPROM (0.8V)	EEPROM (0.8V)	N/A	Float
0.5	1.25	0.050	Open (Bot Resistor Only)
0.6	0.75	0.010	0
0.75	0.9	0.010	1
0.9	1.05	0.010	2
1.05	1.2	0.010	3
1.2	1.5	0.020	4
1.5	1.8	0.020	5
1.8	2.1	0.020	6
2.1	2.4	0.020	7
2.4	3.0	0.040	8
3.0	3.6	0.040	9
3.6	4.2	0.040	10
4.2	4.8	0.040	11
3.6	4.2	0.040	12
4.2	4.8	0.040	13
4.8	5.4	0.040	14
5.4	6.0	0.040	15

With the resistor divider code selected for the range of  $V_{OUT}$ , select the bottom resistor code with the (21h)  $V_{OUT\_COMMAND}$  Offset and (21h)  $V_{OUT\_COMMAND}$  step from [Programming VSEL](#).

表 7-13. VSEL Resistor to AGND Code for Programming

RESISTOR DIVIDER CODE	$V_{OUT\_SCALE\_LOOP}$	$V_{OUT\_MIN}$	$V_{OUT\_MAX}$	$V_{OUT\_COMMAND}$ OFFSET (V)	$V_{OUT\_COMMAND}$ STEP (V)
Short to AGND	0.5	EEPROM (0.5)	EEPROM (1.5)	EEPROM (0.80)	N/A
Float	0.5	0.5	1.5	1.0	N/A
None	0.5	0.5	1.5	0.50	0.050
0	0.5	0.5	1.5	0.6	0.010
1	0.5	0.5	1.5	0.75	0.010
2	0.5	0.5	1.5	0.9	0.010
3	0.5	0.5	1.5	1.05	0.010
4	0.25	1	3	1.2	0.020
5	0.25	1	3	1.5	0.020
6	0.25	1	3	1.8	0.020
7	0.25	1	3	2.1	0.020
8	0.125	2	6	2.4	0.040
9	0.125	2	6	3.0	0.040
10	0.125	2	6	3.6	0.040
11	0.125	2	6	4.2	0.040
12	0.125	2	6	3.6	0.040
13	0.125	2	6	4.2	0.040
14	0.125	2	6	4.8	0.040

**表 7-13. VSEL Resistor to AGND Code for Programming (continued)**

RESISTOR DIVIDER CODE	VOUT_SCALE_LOOP	VOUT_MIN	VOUT_MAX	VOUT_COMMAND OFFSET (V)	VOUT_COMMAND STEP (V)
15	0.125	2	6	5.4	0.040

To calculate the resistor to AGND code, subtract the (21h) *VOUT\_COMMAND* offset from the target output voltage and divide by the (21h) *VOUT\_COMMAND* step.

$$\text{Code} = \frac{V_{\text{OUT}} - \text{VOUT\_COMMAND(Offset)}}{\text{VOUT\_COMMAND(Step)}} \quad (8)$$

### 7.5.2.4 Programming ADRSEL

The resistor divider for the ADRSEL pin selects the range of PMBus Addresses and SYNC direction for the TPS546B24A. For Stand Alone devices with only one device supporting a single output voltage, the ADRSEL divider also selects the Phase Shift between SYNC and the switch node.

**表 7-14. ADRSEL Resistor Divider Code for and SYNC\_IN Programming**

RESISTOR DIVIDER CODE	SLAVE_ADDRESS	SYNC IN / SYNC OUT	STACK_CONFIG = 0x0000 (STAND-ALONE ONLY)	
—	Range	—	PHASE SHIFT	INTERLEAVE
Short to AGND	0x7F (127d)	Auto Detect	0	0x0020
Float	EEPROM (0x24h / 36d)	Auto Detect	0	0x0020
None	16d - 31d	Auto detect	0	0x0020
0	16d - 31d	Sync in	0	0x0040
1	32d - 47d	Sync in	0	0x0040
2	16d - 31d	Sync in	90	0x0041
3	32d - 47d	Sync in	90	0x0041
4	16d - 31d	Sync in	120	0x0031
5	32d - 47d	Sync in	120	0x0031
6	16d - 31d	Sync in	180	0x0042
7	32d - 47d	Sync in	180	0x0042
8	16d - 31d	Sync in	240	0x0032
9	32d - 47d	Sync in	240	0x0032
10	16d - 31d	Sync in	270	0x0043
11	32d - 47d	Sync in	270	0x0043
12	16d - 31d	Sync out	0	0x0020
13	32d - 47d	Sync out	0	0x0020
14	16d - 31d	Sync out	180	0x0042
15	32d - 47d	Sync out	180	0x0042

The resistor to AGND for ADRSEL programs the device PMBus slave address according to 表 7-15:

**表 7-15. ADRSEL Resistor to AGND Code for Programming**

RESISTOR TO AGND CODE	SLAVE ADDRESS (16-31 RANGE)	SLAVE ADDRESS (32-47 RANGE)
0	0x10h (16d)	0x20h (32d)
1	0x11h (17d)	0x21h (33d)
2	0x12h (18d)	0x22h (34d)
3	0x13h (19d)	0x23h (35d)
4	0x14h (10d)	0x24h (36d)

**表 7-15. ADRSEL Resistor to AGND Code for Programming (continued)**

RESISTOR TO AGND CODE	SLAVE ADDRESS (16-31 RANGE)	SLAVE ADDRESS (32-47 RANGE)
5	0x15h (21d)	0x25h (37d)
6	0x16h (22d)	0x26h (38d)
7	0x17h (23d)	0x27h (39d)
8	0x18h (24d)	<b>0x48h (72d)</b>
9	0x19h (25d)	0x29h (41d)
10	0x1Ah (26d)	0x2Ah (42d)
11	0x1Bh (27d)	0x2Bh (43d)
12	0x1Ch (28d)	0x2Ch (44d)
13	0x1Dh (29d)	0x2Dh (45d)
14	0x1Eh (30d)	0x2Eh (46d)
15	0x1Fh (31d)	0x2Fh (47d)

**Note**

When a TPS546B24A device is configured as the Master of a multi-phase stack, it will always occupy the zero-degree position in [\(37h\) INTERLEAVE](#), but the ADRSEL resistor divider can still be used to select Auto Detect, Forced SYNC\_IN, and Forced SYNC\_OUT. When the Master of a multi-phase stack is configured for SYNC\_IN, all devices of the stack will remain disabled until a valid external SYNC signal is provided.

Slave devices in a multi-phase stack are always configured for SYNC\_IN and will declare a SYNC\_FAULT in [\(80h\) STATUS\\_MFR\\_SPECIFIC](#) if enabled before a SYNC input is present or if the SYNC input is lost before being disabled. In order to avoid these false faults due to differences in enable and disable timing between a Master and a Slave device, it is recommended that the Master device of a multi-phase stack be configured for SYNC\_OUT rather than Auto-detect if no external SYNC will be used.

**7.5.2.5 Programming MSEL2 for a Slave Device (GOSNS Tied to BP1V5)**

Configuring a TPS546B24A device as a slave disables all pinstraps except MSEL2, which programs [\(37h\) INTERLEAVE](#) for stacking and [\(ECh\) MFR\\_SPECIFIC\\_28 \(STACK\\_CONFIG\)](#), [\(4Ah\) IOUT\\_OC\\_WARN\\_LIMIT](#), and [\(46h\) IOUT\\_OC\\_FAULT\\_LIMIT](#) with a single resistor to AGND. Note that the master is always device 0.

**表 7-16. Slave MSEL2 Resistor to AGND Code for and Programming**

RESISTOR TO AGND CODE	DEVICE NUMBER, NUMBER OF PHASES	IOUT_OC_WARN_LIMIT (A) / IOUT_OC_FAULT_LIMIT (A)
Short	Device 1, 2-phase	20/26
Float	Device 1, 2-phase	15/19
6	Device 1, 2-phase	20/26
7	Device 1, 2-phase	15/19
4	Device 1, 3-phase	20/26
5	Device 1, 3-phase	15/19
8	Device 2, 3-phase	20/26
9	Device 2, 3-phase	15/19
2	Device 1, 4-phase	20/26
3	Device 1, 4-phase	15/19
14	Device 2, 4-phase	20/26
15	Device 2, 4-phase	15/19
10	Device 3, 4-phase	20/26

**表 7-16. Slave MSEL2 Resistor to AGND Code for and Programming  
(continued)**

RESISTOR TO AGND CODE	DEVICE NUMBER, NUMBER OF PHASES	IOU_OC_WARN_LIMIT (A) / IOU_OC_FAULT_LIMIT (A)
11	Device 3, 4-phase	15/19

#### Note

During the power-on sequence, device 0 (stack master) reads back phase information from all connected slaves, if any slave phase response does not match the [\(Ech\) MFR\\_SPECIFIC\\_28 \(STACK\\_CONFIG\)](#) results of the master, the converter sets the POR fault bit in [\(80h\) STATUS\\_MFR\\_SPECIFIC](#) but does not allow conversion. Once all connected devices respond to Device 0, Device 0 passes remaining pin-strap information to the slaves to ensure matched programming during operation. Adding an additional phase requires adjusting the MSEL2 resistors on the master device and the MSEL2 resistor to ground on all other slave devices.

#### 7.5.2.6 Pin-Strapping Resistor Configuration

表 7-17 和 表 7-18 provide the bottom resistor (pin to AGND) values in ohms, and the top resistor (pin to BP1V5) values in ohms. Select the column with the desired R2G code in the top row and the row with the desired resistor divider code in the left most column. The Pin-to-AGND resistor value is the resistor value in the highlighted row in the first column under the desired R2G code. The Pin-to-BP1V5 resistor value, if used, is the resistor value in the row starting with the desired divider code in the left most column under the desired R2G code and resistor. To ensure accurate pin detection over operating temperature and product life-time, 1% tolerance or better resistors should be used.

**表 7-17. Pin-Strapping Resistor (Ω) Table for R2G Codes 0-7**

R2G code	0	1	2	3	4	5	6	7
Rbot →	4640	5620	6810	8250	10000	12100	14700	17800
Divider Code (↓)	Resistor to BP1V5 Value (Ω)							
0	21500	26100	31600	38300	46400	56200	68100	82500
1	15400	18700	22600	27400	33200	40200	48700	59000
2	11500	14000	16900	20500	24900	30100	36500	44200
3	9090	11000	13300	16200	19600	23700	28700	34800
4	7150	8660	10500	12700	15400	18700	22600	27400
5	5620	6810	8250	10000	12100	14700	17800	21500
6	4640	5620	6810	8250	10000	12100	14700	17800
7	3830	4640	5620	6810	8250	10000	12100	14700
8	3160	3830	4640	5620	6810	8250	10000	12100
9	2610	3160	3830	4640	5620	6810	8250	10000
10	2050	2490	3010	3650	4420	5360	6490	7870
11	1620	1960	2370	2870	3480	4220	5110	6190
12	1270	1540	1870	2260	2740	3320	4020	4870
13	953	1150	1400	1690	2050	2490	3010	3650
14	715	866	1050	1270	1540	1870	2260	2740
15	511	619	750	909	1100	1330	1620	1960

**表 7-18. Pin-Strapping Resistor (Ω) Table for R2G Codes 8-15**

R2G code	8	9	10	11	12	13	14	15
Rbot →	21500	26100	31600	38300	46400	56200	68100	82500

**表 7-18. Pin-Strapping Resistor ( $\Omega$ ) Table for R2G Codes 8-15 (continued)**

Divider Code (↓)	Resistor to BP1V5 Value ( $\Omega$ )							
0	100000	121000	147000	178000	215000	261000	316000	402000
1	71500	86600	105000	127000	154000	187000	226000	274000
2	53600	64900	78700	95300	115000	140000	169000	205000
3	42200	51100	61900	75000	90900	110000	133000	162000
4	33200	40200	48700	59000	71500	86600	105000	127000
5	26100	31600	38300	46400	56200	68100	82500	100000
6	21500	26100	31600	38300	46400	56200	68100	82500
7	17800	21500	26100	31600	38300	46400	56200	68100
8	14700	17800	21500	26100	31600	38300	46400	56200
9	12100	14700	17800	21500	26100	31600	38300	46400
10	9530	11500	14000	16900	20500	24900	30100	26500
11	7500	9090	11000	13300	16200	19600	23700	28700
12	5900	7150	8660	10500	12700	15400	18700	22600
13	4420	5360	6490	7870	9530	11500	14000	16900
14	3320	4020	4870	5900	7150	8660	10500	12700
15	2370	2870	3480	4220	5110	6190	1500	9090

## 7.6 Register Maps

### 7.6.1 Conventions for Documenting Block Commands

According to the SMBus specification, block commands are transmitted across the PMBus interface in ascending order. The description below shows the convention this document follows for documenting block commands.

This document follows the convention for byte ordering of block commands:

When block values are listed as register map tables, they are listed in byte order from top to bottom starting with Byte N and ending with Byte 0.

- Byte 0 (first byte sent) corresponds to bits 7:0.
- Byte 1 (second byte sent) corresponds to bits 15:8.
- Byte 2 (third byte sent) corresponds to bits 23:16.
- ... and so on

When block values are listed as text in hexadecimal, they are listed in byte order, from left to right, starting with Byte 0 and ending with Byte N with a space between each byte of the value. In block 54 49 54 6B 24 41h, the byte order is:

- Byte 0, bits 7:0, = 54h
- Byte 1, bits 15:8, = 49h
- Byte 2, bits 23:16, = 6Bh
- Byte 3, bits 31:24, = 24h
- Byte 4, bits 39:32, = 41h

#### 7-8. Block Command Byte Ordering

47	46	45	44	43	42	41	40
RW	RW	RW	RW	RW	RW	RW	RW
Byte N							
39	38	37	36	35	34	33	32
RW	RW	RW	RW	RW	RW	RW	RW
Byte ...							
31	30	29	28	27	26	25	24
RW	RW	RW	RW	RW	RW	RW	RW
Byte 3							
23	22	21	20	19	18	17	16
RW	RW	RW	RW	RW	RW	RW	RW
Byte 2							
15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
Byte 1							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
Byte 0							

LEGEND: R/W = Read/Write; R = Read only

## 7.6.2 (01h) OPERATION

CMD Address	01h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	No
Updates:	On-the-fly

The (01h) OPERATION command is used to enable or disable power conversion, in conjunction input from the enable pins, according to the configuration of the (02h) ON\_OFF\_CONFIG command. It is also used to set the output voltage to the upper or lower MARGIN levels, and select soft-stop.

**图 7-9. (01h) OPERATION Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	R
ON_OFF	SOFT_OFF	MARGIN				TRANSITION	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-19. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	ON_OFF	RW	0b	Enable/disable power conversion when the (02h) ON_OFF_CONFIG command is configured to require input from the CMD bit for output control. Note that there can be several other requirements that must be satisfied before the power conversion can begin (for example, input voltages above UVLO thresholds, enable pins high if required by (02h) ON_OFF_CONFIG and so forth). 0b: Disable power conversion. 1b: Enable power conversion and enable Ignore Faults on MARGIN.
6	SOFT_OFF	RW	0b	This bit controls the turnoff profile when (02h) ON_OFF_CONFIG is configured to require input from the CMD bit for output voltage control and OPERATION bit 7 transitions from 1b to 0b is ignored when bit 7 is 1b. 0b: Immediate Off. Power conversion stops immediately and the power stage is forced to a high-Z state. 1b: Soft Off. Power conversion continues for the TOFF_DELAY time, then the output voltage is ramped down to 0 V at a slew rate according to TOFF_FALL. Once the output voltage reaches 0 V, power conversions stops.

表 7-19. Register Field Descriptions (continued)

Bit	Field	Access	Reset	Description
5:2	MARGIN	RW	0000b	<p>Sets the margin state.</p> <p>0000b, 0001b, 0010b: Margin OFF. Output voltage target is (21h) <a href="#">VOUT_COMMAND</a>, OV/UV faults behave normally per their respective fault response settings 0.</p> <p>0101b: Margin Low (Ignore Fault if bit 7 is 1b). Output voltage target is (26h) <a href="#">VOUT_MARGIN_LOW</a>. OV/UV faults are ignored. Do not trigger shutdown or STATUS updates if bit 7 is 1b.</p> <p>0110b: Margin Low (Act on Fault). Output voltage target is (26h) <a href="#">VOUT_MARGIN_LOW</a>. OV/UV faults trigger per their respective fault response settings.</p> <p>1001b: Margin High (Ignore Fault if bit 7 is 1b). Output voltage target is (25h) <a href="#">VOUT_MARGIN_HIGH</a>. OV/UV trigger are ignored and do not trigger shutdown or STATUS update if bit 7 is 1b.</p> <p>1010b: Margin High (Act on Fault). Output voltage target is (25h) <a href="#">VOUT_MARGIN_HIGH</a>. OV/UV trigger per their respective fault response settings.</p> <p>Other: Invalid/Unsupported data</p>
1	TRANSITION	R	0b	Not used and always set to 0.
0	Reserved	R	0b	Not used and always set to 0.

Attempts to write (01h) [OPERATION](#) to any value other than those listed above will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits, and notifying the host according to the PMBus 1.3.1 Part II specification, section 10.9.3.



### 7.6.3 (02h) ON\_OFF\_CONFIG

CMD Address	02h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The (02h) ON\_OFF\_CONFIG command configures the combination of enable pin input and serial bus commands needed to enable/disable power conversion. This includes how the unit responds when power is applied to PVIN.

**7-10. (02h) ON\_OFF\_CONFIG Register Map**

7	6	5	4	3	2	1	0
R	R	R	RW	RW	RW	RW	RW
0	0	0	PU	CMD	CP	POLARITY	DELAY

LEGEND: R/W = Read/Write; R = Read only

**表 7-20. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:5	Reserved	R	000b	Not used and always set to 0.
4	PU	RW	NVM	0b: Unit starts power conversion any time the input power is present regardless of the state of the CONTROL pin. 1b: Act on CONTROL. (01h) OPERATION command to start/stop power conversion, or both.
3	CMD	RW	NVM	0b: Ignore (01h) OPERATION Command to start/stop power conversion. 1b: Act on (01h) OPERATION Command (and CONTROL pin if configured by CP) to start/stop power conversion.
2	CP	RW	NVM	0b: Ignore CONTROL pin to start/stop power conversion. The UVLO function of the EN/UVLO pin is not active when CONTROL pin is ignored. 1b: Act on CONTROL pin (and (01h) OPERATION Command if configured by bit [3]) to start/stop power conversion.
1	POLARITY	RW	NVM	0b: CONTROL pin has active low polarity. The UVLO function of the EN/UVLO pin cannot be used when CONTROL has active load polarity. 1b: CONTROL pin has active high polarity.
0	DELAY	RW	NVM	0b: When power conversion is commanded OFF by the CONTROL pin (must be configured to respect the CONTROL pin as above), continue regulating for the (64h) TOFF_DELAY time, then ramp the output voltage to 0 V, in the time defined by (65h) TOFF_FALL. 1b: When power conversion is commanded OFF by the CONTROL pin (must be configured to respect the CONTROL pin as above), stop power conversion immediately.

For the purposes of (02h) ON\_OFF\_CONFIG, the device pin EN/UVLO is the CONTROL pin.

Attempts to write (02h) ON\_OFF\_CONFIG to any value other than those explicitly listed above will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits, and notifying the host according to the PMBus 1.3.1 Part II specification, section 10.9.3.

### 7.6.4 (03h) CLEAR\_FAULTS

CMD Address	03h
Write Transaction:	Send Byte
Read Transaction:	N/A
Format:	Data-less
Phased:	Yes
NVM Back-up:	No
Updates:	On-the-fly

**CLEAR\_FAULTS** is a phased command used to clear any fault bits that have been set. This command simultaneously clears all bits in all status registers of the selected phase, or all phases if PHASE = FFh. At the same time, the device releases its SMB\_ALERT# signal output if SMB\_ALERT# is asserted. **CLEAR\_FAULTS** is a write-only command with no data.

The **CLEAR\_FAULTS** command does not cause a unit that has latched off for a fault condition to restart. If the fault is still present when the bit is cleared, the fault bit is immediately set again and the host is notified by the usual means.

If the device responds to an Alert Response Address (ARA) from the host, it will clear SMB\_ALERT# but not the offending status bit or bits (as it has successfully notified the host and then expects the host to handle the interrupt appropriately). The original fault and any from other sources that occur between the initial assertion of SMB\_ALERT# and the successful response of the device to the ARA are cleared (through **CLEAR\_FAULTS**, OFF-ON toggle, or power reset) before any of these sources are allowed to re-trigger SMB\_ALERT#. However, fault sources which only become active post-ARA trigger SMB\_ALERT#.

**7-11. (03h) CLEAR\_FAULTS Register Map**

7	6	5	4	3	2	1	0
W	W	W	W	W	W	W	W
CLEAR_FAULTS							

LEGEND: R/W = Read/Write; R = Read only

### 7.6.5 (04h) PHASE

CMD Address	04h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	No
Updates:	On-the-fly

The **PHASE** command provides the ability to configure, control, and monitor individual phases. Each **PHASE** contains the Operating Memory and User Store and Default Store for each phase output. The phase selected by the **PHASE** command will be used for all subsequent phase-dependent commands. The phase configuration needs to be established before any phase-dependent command can be successfully executed.

In the TPS546B24A, each **PHASE** is a separate device. The Loop and PMBus Master device, GOSNS/SLAVE connected to ground, will always be PHASE = 00h. Slave devices, GOSNS/SLAVE connected to BP1V5, have their phase assignment defined by their phase position, as defined by INTERLEAVE or MSEL2

**图 7-12. (04h) PHASE Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
PHASE							

LEGEND: R/W = Read/Write; R = Read only

**表 7-21. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:0	PHASE	RW	FFh	00h: All commands address Phase 1. 01h: All commands address Phase 2. 02h: All commands address Phase 3. 03h: All commands address Phase 4. 04h-FEh: Unsupported/Invalid data FFh: Commands are addressed to all phases as a single entity. See the following text for more information.

The range of valid data for **PHASE** also depends on the phase configuration. Attempts to write **(04h) PHASE** to a value not supported by the current phase configuration will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification, section 10.9.3.

### 7.6.6 (10h) WRITE\_PROTECT

CMD Address	10h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [WRITE\\_PROTECT](#) command controls writing to the PMBus device. The intent of this command is to provide protection against accidental changes; it has one data byte that is described below. This command does NOT provide protection against deliberate or malicious changes to a configuration or operation of the device. All supported commands can have their parameters read, regardless of the [WRITE\\_PROTECT](#) settings.

**图 7-13. (10h) WRITE\_PROTECT Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
WRITE_PROTECT							

LEGEND: R/W = Read/Write; R = Read only

**表 7-22. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:0	WRITE_PROTECT	RW	NVM	00h: Enable writes to all commands. 20h: Disables all write access except to the WRITE_PROTECT, <a href="#">OPERATION</a> , ON_OFF_CONFIG, STORE_USER_ALL, and VOUT_COMMAND commands. 40h: Disables all WRITES except to the WRITE_PROTECT, <a href="#">OPERATION</a> , and STORE_USER_ALL commands. 80h: Disables all WRITES except to the WRITE_PROTECT and STORE_USER_ALL commands. Other: Invalid/Unsupported data

Attempts to write [\(10h\) WRITE\\_PROTECT](#) to any invalid value as specified above will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits, and notifying the host according to the PMBus 1.3.1 Part II specification, section 10.9.3.

### 7.6.7 (15h) STORE\_USER\_ALL

CMD Address	15h
Write Transaction:	Send Byte
Read Transaction:	N/A
Format:	Data-less
Phased:	No, PHASE = FFh only
NVM Back-up:	No
Updates:	Not recommended for on-the-fly-use, but not explicitly blocked

The [STORE\\_USER\\_ALL](#) command instructs the PMBus device to copy the entire contents of the Operating Memory to the matching locations in the non-volatile User Store memory. Any items in Operating Memory that do not have matching locations in the User Store are ignored.

NVM Store operations are not recommended while the output voltages are in regulation, although the user is not explicitly prevented from doing so, as interruption can result in a corrupted NVM. PMBus commands issued during this time can cause long clock stretch times, or simply be ignored. TI recommends disabling regulation, and waiting a minimum of 100 ms before continuing, following issuance of NVM store operations.

To prevent storing mismatched register values to NVM, STORE\_USER\_ALL should not be used unless PHASE = FFh.

**7-14. (15h) STORE\_USER\_ALL Register Map**

7	6	5	4	3	2	1	0
W	W	W	W	W	W	W	W
STORE_USER_ALL							

LEGEND: R/W = Read/Write; R = Read only

### 7.6.8 (16h) RESTORE\_USER\_ALL

CMD Address	16h
Write Transaction:	Send Byte
Read Transaction:	N/A
Format:	Data-less
Phased:	No, PHASE = FFh only
NVM Back-up:	No
Updates:	Disables Regulation during RESTORE

The [RESTORE\\_USER\\_ALL](#) command instructs the PMBus device to disable operation and copy the entire contents of the non-volatile User Store memory to the matching locations in the Operating Memory, then Overwrite Operating Memory of any commands selected in PIN\_DETECT\_OVERRIDE with their last read pin-detected values. The values in the Operating Memory are overwritten by the value retrieved from the User Store and Pin Detection. Any items in User Store that do not have matching locations in the Operating Memory are ignored.

To prevent storing mismatched register values to NVM, RESTORE\_USER\_ALL should not be used unless PHASE = FFh.

**7-15. (16h) RESTORE\_USER\_ALL Register Map**

7	6	5	4	3	2	1	0
W	W	W	W	W	W	W	W
RESTORE_USER_ALL							

LEGEND: R/W = Read/Write; R = Read only

## 7.6.9 (19h) CAPABILITY

CMD Address	19h
Write Transaction:	N/A
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	No
Updates:	N/A

This command provides a way for the host to determine the capabilities of this PMBus device. This command is read-only and has one data byte formatted as below.

 **7-16. (19h) CAPABILITY Register Map**

7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
PEC	SPEED		ALERT	FORMAT	AVSBUS	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-23. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	PEC	R	1b	1b: Packet Error Checking is supported.
6:5	SPEED	R	10b	10b: Maximum supported bus speed is 1 MHz.
4	ALERT	R	1b	1b: The device has an SMB_ALERT# pin and supports the SMBus Alert Response Protocol.
3	FORMAT	R	0b	0b: Numeric format is LINEAR or DIRECT.
2	AVSBUS	R	0b	0b: AVSBus is NOT supported.
1:0	Reserved	R	00b	Reserved and always set to 0.

Attempts to write (19h) CAPABILITY to any value will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification, section 10.9.3.

### 7.6.10 (1Bh) SMBALERT\_MASK

CMD Address	1Bh
Write Transaction:	Write Word
Read Transaction:	Block-Write/Block-Read Process Call
Format:	Write: Unsigned Binary (2 bytes)Read: Unsigned Binary (1 byte)
Phased:	No, Only PHASE = FFh is supported
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [SMBALERT\\_MASK](#) command can be used to prevent a warning or fault condition from asserting the SMBALERT# signal. Setting a MASK bit does not prevent the associated bit in the STATUS\_CMD from being set, but prevents the associated bit in the STATUS\_CMD from asserting SMB\_ALERT#. See Reference [3] for more information on the command format. The following register descriptions describe the individual mask bits available.

SMBALERT\_MASK Write Transaction = Write Word. CMD = 1Bh, Low =STATUS\_CMD, High=MASK

SMBALERT\_MASK Read Transaction = Block-Write/Block-Read Process Call. Write 1 byte block with STATUS\_CMD, read 1 byte block.



### 7.6.11 (1Bh) SMBALERT\_MASK\_VOUT

CMD Address	1Bh (with CMD byte = 7Ah)
Write Transaction:	Write Word
Read Transaction:	Block-Write/Block-Read Process Call
Format:	Unsigned Binary (1 byte)
Phased:	No, Only PHASE = FFh is supported
NVM Back-up:	EEPROM
Updates:	On-the-fly

SMBALERT\_MASK bits for the [STATUS\\_VOUT](#) command

**图 7-17. (1Bh) SMBALERT\_MASK\_VOUT Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	R	R
mVOUT_OVF	mVOUT_OVW	mVOUT_UVW	mVOUT_UVF	mVOUT_MINMAX	mTON_MAX	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-24. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	mVOUT_OVF	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
6	mVOUT_OVW	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
5	mVOUT_UVW	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
4	mVOUT_UVF	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
3	mVOUT_MINMAX	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
2	mTON_MAX	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
1:0	Not supported	R	00b	Not supported and always set to 00b.

## 7.6.12 (1Bh) SMBALERT\_MASK\_IOUT

CMD Address	1Bh (with CMD byte = 7Bh)
Write Transaction:	Write Word
Read Transaction:	Block-Write/Block-Read Process Call
Format:	Unsigned Binary (1 byte)
Phased:	No, Only PHASE = FFh is supported
NVM Back-up:	EEPROM
Updates:	On-the-fly

SMBALERT\_MASK bits for [STATUS\\_IOUT](#)

**图 7-18. (1Bh) SMBALERT\_MASK\_IOUT Register Map**

7	6	5	4	3	2	1	0
RW	R	RW	RW	R	R	R	R
mIOUT_OCF	0	mIOUT_OCW	mIOUT_UCF	0	0	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-25. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	mIOUT_OCF	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
6	Not supported	R	0b	Not supported
5	mIOUT_OCW	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
4	mIOUT_UCF	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
3	Not supported	R	0b	Not supported
2:0	Not supported	RW	0b	Not supported

### 7.6.13 (1Bh) SMBALERT\_MASK\_INPUT

CMD Address	1Bh (with CMD byte = 7Ch)
Write Transaction:	Write Word
Read Transaction:	Block-Write/Block-Read Process Call
Format:	Unsigned Binary (1 byte)
Phased:	No, Only PHASE = FFh is supported
NVM Back-up:	EEPROM
Updates:	On-the-fly

SMBALERT\_MASK bits for [STATUS\\_INPUT](#)

**图 7-19. (1Bh) SMBALERT\_MASK\_INPUT Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	R	RW	R	R	R
mVIN_OVF	mVIN_OVW	mVIN_UVW	0	mLOW_VIN	0	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-26. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	mVIN_OVF	RW	0b	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
6	mVIN_OVW	RW	0b	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
5	mVIN_UVW	RW	0b	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
4	Not supported	R	0b	Not supported
3	mLOW_VIN	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
2	Not supported	R	0b	Not supported
1	Not supported	R	0b	Not supported
0	Not supported	R	0b	Not supported

### 7.6.14 (1Bh) SMBALERT\_MASK\_TEMPERATURE

CMD Address	1Bh (with CMD byte = 7Dh)
Write Transaction:	Write Word
Read Transaction:	Block-Write/Block-Read Process Call
Format:	Unsigned Binary (1 byte)
Phased:	No, Only PHASE = FFh is supported
NVM Back-up:	EEPROM
Updates:	On-the-fly

SMBALERT\_MASK bits for [STATUS\\_TEMPERATURE](#)

**图 7-20. (1Bh) SMBALERT\_MASK\_TEMPERATURE Register Map**

7	6	5	4	3	2	1	0
RW	RW	R	R	R	R	R	R
mOTF	mOTW	0	0	0	0	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-27. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	mOTF	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
6	mOTW	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
5:0	Not supported	R	0d	Not supported and always set to 000000b.

### 7.6.15 (1Bh) SMBALERT\_MASK\_CML

CMD Address	1Bh (with CMD byte = 7Eh)
Write Transaction:	Write Word
Read Transaction:	Block-Write/Block-Read Process Call
Format:	Unsigned Binary (1 byte)
Phased:	No, Only PHASE = FFh is supported
NVM Back-up:	EEPROM
Updates:	On-the-fly

SMBALERT\_MASK bits for [STATUS\\_CML](#)

**图 7-21. (1Bh) SMBALERT\_MASK\_CML Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	R	RW	R
mIVC	mIVD	mPEC	mMEM	mPROC	0	mCOMM	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-28. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	mIVC	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
6	mIVD	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
5	mPEC	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
4	mMEM	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
3	mPROC	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
2	Not supported	R	0b	Not supported
1	mCOMM	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
0	Not supported	R	0b	Not supported

**7.6.16 (1Bh) SMBALERT\_MASK\_OTHER**

CMD Address	1Bh (with CMD byte = 7Fh)
Write Transaction:	Write Word
Read Transaction:	Block-Write/Block-Read Process Call
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

SMBALERT\_MASK bits for [STATUS\\_OTHER](#)**图 7-22. (1Bh) SMBALERT\_MASK\_OTHER Register Map**

7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
0	0	0	0	0	0	0	mFIRST_ TO_ALERT

LEGEND: R/W = Read/Write; R = Read only

**表 7-29. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:1	Not supported	R	0h	Not supported
0	mFIRST_ TO_ALERT	R	1b	The FIRST_TO_ALERT bit does not in itself generate SMBALERT assertion, hence this bit is hard-coded to 1b (source is masked).

### 7.6.17 (1Bh) SMBALERT\_MASK\_MFR

CMD Address	1Bh (with CMD byte = 80h)
Write Transaction:	Write Word
Read Transaction:	Block-Write/Block-Read Process Call
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

SMBALERT\_MASK bits for STATUS\_MFR

**图 7-23. (1Bh) SMBALERT\_MASK\_MFR Register Map**

7	6	5	4	3	2	1	0
RW	RW	R	R	RW	RW	RW	R
mPOR	mSELF	0	0	mRESET	mBCX	mSYNC	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-30. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	mPOR	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
6	mSELF	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition. Due to variations in AVIN UVLO, unmasking this bit can result in SMBALERT being asserted on power up.
5	Not supported	R	0b	Not supported
4	Not supported	R	0b	Not supported
3	mRESET	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
2	mBCX	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition.
1	mSYNC	RW	NVM	0b: SMBALERT may assert due to this condition. 1b: SMBALERT may NOT assert due to this condition. When the Master device of a multi-phase stack is programmed for Auto Detect SYNC, unmasking this bit can result in a momentary assertion of SMBALERT when the multi-phase stack is enabled.
0	Not supported	R	0b	Not supported

### 7.6.18 (20h) VOUT\_MODE

CMD Address	20h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	Conversion Disabled: on-the-fly, Conversion Enabled: Read Only

The data byte for the **VOUT\_MODE** command is one byte that consists of a one bit absolute/relative selection, two bit Mode, and a five bit Parameter as shown in [Figure 7-24](#). The two bit Mode is fixed to ULINEAR16 mode for output voltage related commands. The five bit Parameter provides more information about the selected mode, such as the ULINEAR16 Exponent that is being used.

**Figure 7-24. (20h) VOUT\_MODE Register Map**

7	6	5	4	3	2	1	0
RW	R	R	RW	RW	RW	RW	RW
REL	MODE		PARAMETER				

LEGEND: R/W = Read/Write; R = Read only

**Table 7-31. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	REL	RW	NVM	0b: Absolute Data Format 1b: Relative Data Format
6:5	MODE	R	00b	00b: Linear Format (ULINEAR16, SLINEAR16) Other: Unsupported/Invalid
4:0	PARAMETER	RW	NVM	MODE = 00b (Linear Format): Specifies the exponent "N" to use with output voltage related commands, in two's complement format. Supported exponent values in the linear mode range from -4 (62.5 mV/LSB) to -12 (0.244 mV/LSB). Refer to the following text for more information.

### Changing VOUT\_MODE

Changing **VOUT\_MODE** will force an update to the values of many VOUT related commands to conform to the updated **VOUT\_MODE** value including Relative versus Absolute mode and the linear Exponent value. When programming VOUT\_MODE in conjunction with other VOUT related commands, VOUT related commands will be interpreted with the current **VOUT\_MODE** value and converted if **VOUT\_MODE** is later changed.



### 7.6.19 (21h) VOUT\_COMMAND

CMD Address	21h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16, Absolute Only per <a href="#">VOUT_MODE</a>
Phased:	No
NVM Back-up:	EEPROM or Pin Detection
Updates:	on-the-fly

[VOUT\\_COMMAND](#) causes the device to set its output voltage to the commanded value with two data bytes. Output voltage changes due to [VOUT\\_COMMAND](#) occur at the rate specified by [VOUT\\_TRANSITION\\_RATE](#).

When PGD/RST\_B is configured as a RESET# pin in MISC\_OPTIONS, assertion of the PGD/RST\_B pin causes the output voltage to return to the VBOOT value, and causes the [VOUT\\_COMMAND](#) value to be updated accordingly.

**图 7-25. (21h) VOUT\_COMMAND Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_COMMAND (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_COMMAND (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-32. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_COMMAND	RW	NVM	Sets the output voltage target via the PMBus interface.

At power up, the reset value of [VOUT\\_COMMAND](#) is derived from either pin-detection on the VSEL pin, or from the NVM, depending on the VOUT\_COMMAND bit in PIN\_DETECT\_OVERRIDE.

When the VOUT\_COMMAND bit in PIN\_DETECT\_OVERRIDE = 0b, the default value of [VOUT\\_COMMAND](#) is restored from NVM at Power On Reset or RESTORE\_USER\_ALL.

When the VOUT\_COMMAND bit in PIN\_DETECT\_OVERRIDE = 1b, the default value of [VOUT\\_COMMAND](#) is derived from pin-detection on the VSEL pin, at Power-On Reset or RESTORE\_USER\_ALL.

This default value, whether derived from pin detection, or NVM becomes the “default” output voltage (also referred to as “VBOOT”), and is stored in RAM separately from the current value of [VOUT\\_COMMAND](#).

#### BOOT Voltage Behavior

The RESET\_FLT bit in MISC\_OPTIONS selects the VOUT\_COMMAND behavior following a fault-related shutdown. When RESET\_FLT = 0b, the device will retain the current value of [VOUT\\_COMMAND](#) during HICCUP after a fault. When RESET\_FLT = 1b, VOUT\_COMMAND will reset to the last detected VSEL voltage or the NVM STORED value for VOUT\_COMMAND as selected by the VOUT\_COMMAND bit in MISC\_OPTIONS.

#### Data Validity

Writes to [VOUT\\_COMMAND](#) for which the resulting value, including any offset from [VOUT\\_TRIM](#) is greater than the current [VOUT\\_MAX](#), or less than the current [VOUT\\_MIN](#), causes the reference DAC to move to the value

specified by [VOUT\\_MIN](#) or [VOUT\\_MAX](#) respectively, and causes the VOUT\_MAX\_MIN\_WARNING fault condition, setting the appropriate bits in [STATUS\\_WORD](#), [STATUS\\_VOUT](#) and notifying the host per the PMBus 1.3.1 Part II specification, section 10.2.

## 7.6.20 (22h) VOUT\_TRIM

CMD Address	22h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR16, Absolute Only per (20h) VOUT_MODE.
Phased:	No
NVM Back-up:	EEPROM
Updates:	on-the-fly

VOUT\_TRIM is used to apply a fixed offset voltage to the output voltage command value. Output voltage changes due to Programming VSEL occur at the rate specified by (27h) VOUT\_TRANSITION\_RATE.

**图 7-26. (22h) VOUT\_TRIM Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_TRIM (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_TRIM (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-33. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_TRIM	RW	See Below	Output voltage offset. SLINEAR16 (two's complement) format

### Limited NVM Back-up

Only 8 bits of NVM backup are provided for this command. While the Programming VSEL command follows the (20h) VOUT\_MODE exponent, NVM back-up is stored with an exponent -12 and stored values will be limited to -127 to +127 with an exponent -12 (-31mV to +31mV) irrespective of (20h) VOUT\_MODE.

### Data Validity

VOUT\_TRIM will accept values from -127 to +127 with the current (20h) VOUT\_MODE, but the NVM stored value will be limited as above. Values beyond this range will be NACKed and reported as invalid data in (7Eh) STATUS\_CML.

Referring to the data validity table in (21h) VOUT\_COMMAND (reproduced below), the output voltage value (including any offset from Programming VSEL, (21h) VOUT\_COMMAND, VOUT\_MARGIN, ...) may not exceed the values supported by the DAC hardware.

Programming a (21h) VOUT\_COMMAND + (22h) VOUT\_TRIM value greater than the maximum value supported by the DAC hardware but less than (24h) VOUT\_MAX will result in the regulated output voltage clamping at the maximum value supported by the DAC hardware without setting the VOUT\_MAX\_MIN bit in (7Ah) STATUS\_VOUT.

**表 7-34. VOUT\_COMMAND/VOUT\_MARGIN + VOUT\_TRIM data validity (Linear Format)**

VOUT_SCALE _LOOP	INTERNAL DIVIDER	VALID VOUT_COMMAND /MARGIN + VOUT_TRIM VALUES
1.0	None	0.000V to 0.700 V
0.5	1:1	0.000 V to 1.400 V

**表 7-34. VOUT\_COMMAND/VOUT\_MARGIN + VOUT\_TRIM data validity (Linear Format) (continued)**

VOUT_SCALE _LOOP	INTERNAL DIVIDER	VALID VOUT_COMMAND /MARGIN + VOUT_TRIM VALUES
0.25	1:3	0.000 V to 2.800 V
0.125	1:7	0.000 V to 6.000 V

The minimum and maximum valid data values for [Programming VSEL](#) follow the description in [\(21h\) VOUT\\_COMMAND](#). Attempts to write [Programming VSEL](#) to any value outside those specified as valid, will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits, and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

Writes to [Programming VSEL](#) for which the resulting output voltage is greater than the current [\(24h\) VOUT\\_MAX](#), or less than the current [\(2Bh\) VOUT\\_MIN](#), cause the reference DAC to move to the value specified by [\(2Bh\) VOUT\\_MIN](#) or [\(24h\) VOUT\\_MAX](#), respectively, and cause the VOUT\_MAX\_MIN\_WARNING fault condition, setting the appropriate bits in [\(79h\) STATUS\\_WORD](#), [\(7Ah\) STATUS\\_VOUT](#) and notifying the host per the PMBus 1.3.1 Part II specification, section 10.2.

## 7.6.21 (24h) VOUT\_MAX

CMD Address	24h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16, Absolute Only per <a href="#">VOUT_MODE</a>
Phased:	No
NVM Back-up:	EEPROM or Pin Detection
Updates:	On-the-fly

The [VOUT\\_MAX](#) command sets an upper limit on the output voltage the unit and can command regardless of any other commands or combinations. The intent of this command is to provide a safeguard against a user accidentally setting the output voltage to a possibly destructive level.

**图 7-27. (24h) VOUT\_MAX Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_MAX (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_MAX (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-35. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_MAX	RW	NVM	Maximum output voltage. ULINEAR16 absolute per the setting of VOUT_MODE. Refer to the following description for data validity.

While conversion is enabled, any output voltage change (including [VOUT\\_COMMAND](#), [VOUT\\_TRIM](#), margin operations) that causes the new target voltage to be greater than the current value of [VOUT\\_MAX](#) will cause the VOUT\_MAX\_MIN\_WARNING fault condition, unless VOUT is limited by reference DAC range of 0.75 V/ [VOUT\\_SCALE\\_LOOP](#). This result causes the TPS546B24A to:

- Set to the output voltage to current value of [VOUT\\_MAX](#), at the slew rate defined by [VOUT\\_TRANSITION\\_RATE](#).
- Set the NONE OF THE ABOVE bit in the [STATUS\\_BYTE](#).
- Set the VOUT bit in the [STATUS\\_WORD](#).
- Set the VOUT\_MIN\_MAX warning bit in [STATUS\\_VOUT](#).
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

Although the scenario is uncommon, note that the same response results if the user attempted to program [VOUT\\_MAX](#) less than the current output voltage target.

## 7.6.22 (25h) VOUT\_MARGIN\_HIGH

CMD Address	25h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16, per <a href="#">VOUT_MODE</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [VOUT\\_MARGIN\\_HIGH](#) command loads the unit with the voltage to which the output is to be changed when the [OPERATION](#) command is set to “Margin High”. Output voltage transitions during margin operation occur at the slew rate defined by [VOUT\\_TRANSITION\\_RATE](#).

When the MARGIN bits in the [OPERATION](#) command indicate “Margin High,” the output voltage is updated to the value of [VOUT\\_MARGIN\\_HIGH](#) + [VOUT\\_TRIM](#).

**图 7-28. (25h) VOUT\_MARGIN\_HIGH Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_MARGH (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_MARGH (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-36. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_MARGH	RW	NVM	Margin High output voltage. ULINEAR16 relative or absolute per the setting of <a href="#">VOUT_MODE</a>

The minimum and maximum valid data values for [VOUT\\_MARGIN\\_HIGH](#) follow the description in [VOUT\\_COMMAND](#). That is, the total combined output voltage, including [VOUT\\_MARGIN\\_HIGH](#) and [VOUT\\_TRIM](#), follow the values allowed by the current [VOUT\\_MAX](#) setting.

Attempts to write (25h) [VOUT\\_MARGIN\\_HIGH](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### 7.6.23 (26h) VOUT\_MARGIN\_LOW

CMD Address	26h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16, per <a href="#">VOUT_MODE</a>
Phased:	No
NVM Back-up:	EEPROM

The [VOUT\\_MARGIN\\_LOW](#) command loads the unit with the voltage to which the output is to be changed when the [OPERATION](#) command is set to “Margin Low”. Output voltage transitions during margin operation occur at the slew rate defined by [VOUT\\_TRANSITION\\_RATE](#).

When the MARGIN bits in the [OPERATION](#) command indicate “Margin Low,” the output voltage is updated to the value of [VOUT\\_MARGIN\\_LOW](#) + [VOUT\\_TRIM](#).

**图 7-29. (26h) VOUT\_MARGIN\_LOW Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_MARGIN_LOW (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_MARGIN_LOW (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-37. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_MARGL	RW	NVM	Margin Low output voltage. ULINEAR16 relative or absolute per the setting of <a href="#">VOUT_MODE</a>

The minimum and maximum valid data values for [VOUT\\_MARGIN\\_LOW](#) follow the description in [VOUT\\_COMMAND](#). Attempts to write (26h) [VOUT\\_MARGIN\\_LOW](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

## 7.6.24 (27h) VOUT\_TRANSITION\_RATE

CMD Address	27h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [VOUT\\_TRANSITION\\_RATE](#) sets the slew rate at which any output voltage changes during normal power conversion occur. This commanded rate of change does not apply when the unit is commanded to turn on or to turn off. The units are mV/μs.

**图 7-30. (27h) VOUT\_TRANSITION\_RATE Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOTR_EXP					VOTR_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOTR_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-38. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	VOTR_EXP	RW	11100b	Linear format two's complement exponent. Exponent = -4, LSB = 0.0625 mV/μs
10:0	VOTR_MAN	RW	NVM	Linear format two's complement mantissa

Per the TPS546B24A product specification, the following slew rates are supported (see the table below). Note that every binary value between the minimum and maximum values is writeable and readable, but that the actual output voltage slew rate is set to the nearest supported value.

VOUT\_TRANSITION RATE can be programmed from 0.067 mV/μs to 15.933 mV/μs.

Attempts to write [\(27h\) VOUT\\_TRANSITION\\_RATE](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.



## 7.6.25 (29h) VOUT\_SCALE\_LOOP

CMD Address	29h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	No
Updates:	Conversion Disable: on-the-fly. Conversion Enable: hardware update blocked. To update hardware after write while enabled, store to NVM with STORE_USER_ALL and RESTORE_USER_ALL or cycle AVIN below UVLO.
NVM Back-up:	EEPROM or Pin Detection

VOUT\_SCALE\_LOOP allows PMBus devices to map between the commanded voltage and the voltage at the control circuit input. In the TPS546B24A, VOUT\_SCALE\_LOOP also programs an internal precision resistor divider so no external divider is required.

**图 7-31. (29h) VOUT\_SCALE\_LOOP Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOSL_EXP					VOSL_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOSL_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-39. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	VOSL_EXP	RW	11001b	Linear format two's complement exponent
10:0	VOSL_MAN	RW	NVM	Linear format two's complement mantissa

## Data Validity

Every binary value between the minimum and maximum supported values is writeable and readable. However, not every combination is supported in hardware. Refer to [表 7-40](#):

**表 7-40. Accepted Values**

VOUT_SCALE_LOOP (DECODED)	INTERNAL DIVIDER SCALING FACTOR
Less than or equal to 0.125	0.125
$0.125 < \text{VOSL} \leq 0.25$	0.25
$0.25 < \text{VOSL} \leq 0.5$	0.5
Greater than 0.5	1.0

Attempts to write [\(29h\) VOUT\\_SCALE\\_LOOP](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

If a [\(29h\) VOUT\\_SCALE\\_LOOP](#) value other than a supported Internal Divider Scaling Factor is programmed into [\(29h\) VOUT\\_SCALE\\_LOOP](#), [\(21h\) VOUT\\_COMMAND](#) to VREF scale factors are calculated based on the actual [\(29h\) VOUT\\_SCALE\\_LOOP](#) value. [\(29h\) VOUT\\_SCALE\\_LOOP](#) values other than supported Internal Divider

Scaling Factors can produce a mismatch between (21h) [VOUT\\_COMMAND](#) and the actual commanded output voltage.

## 7.6.26 (2Bh) VOUT\_MIN

CMD Address	2Bh
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16, Absolute Only per <a href="#">VOUT_MODE</a>
Phased:	No
Updates:	on-the-fly
NVM Back-up:	EEPROM or Pin Detection

The [VOUT\\_MIN](#) command sets a lower limit on the output voltage the unit can command regardless of any other commands or combinations. The intent of this command is to provide a safeguard against a user accidentally setting the output voltage to a level which will render the load inoperable.

**图 7-32. (2Bh) VOUT\_MIN Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_MIN (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_MIN (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-41. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_MIN	RW	NVM	Minimum output voltage. ULINEAR16 absolute per the setting of VOUT_MODE.

During power conversion, any output voltage change (including [VOUT\\_COMMAND](#), [VOUT\\_TRIM](#), margin operations) that causes the new target voltage to be less than the current value of [VOUT\\_MIN](#) will cause the VOUT\_MAX\_MIN\_WARNING fault condition. These results cause the TPS546B24A to:

- Set to the output voltage to current value of [VOUT\\_MIN](#) at the slew rate defined by [VOUT\\_TRANSITION\\_RATE](#).
- Set the NONE OF THE ABOVE in the [STATUS\\_BYTE](#).
- Set the VOUT bit in the [STATUS\\_WORD](#).
- Set the VOUT\_MIN\_MAX warning bit in [STATUS\\_VOUT](#).
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

Although the scenario is uncommon, note that the same response results if the user attempted to program [VOUT\\_MAX](#) greater than the current output voltage target.

### Data Validity

The minimum and maximum valid data values for [VOUT\\_MIN](#) follow those of [VOUT\\_MAX](#). Attempts to write (2Bh) [VOUT\\_MIN](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

## 7.6.27 (33h) FREQUENCY\_SWITCH

CMD Address	33h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11, per <a href="#">CAPABILITY</a>
Phased:	No
Updates:	Conversion Disable: on-the-fly. Conversion Enable: hardware update blocked. To update hardware after write while enabled, store to NVM with STORE_USER_ALL and RESTORE_USER_ALL or cycle AVIN below UVLO.
NVM Back-up:	EEPROM or Pin Detection

FREQUENCY\_SWITCH sets the switching frequency of the active channel in kHz.

**图 7-33. (33h) FREQUENCY\_SWITCH Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
FSW_EXP					FSW_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
FSW_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-42. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	FSW_EXP	RW	NVM	Linear format two's complement exponent On reset, FSW_EXP is auto-generated based on the switching frequency stored in NVM.
10:0	FSW_MAN	RW	NVM	Linear format two's complement mantissa. Refer to <a href="#">表 7-43</a> .

**表 7-43. Supported Switching Frequency Settings**

FREQUENCY_SWITCH (Decoded)	Effective Switching Frequency (kHz)
Less than 250 kHz	225
$251 \leq \text{FSW} < 300$ kHz	275
$301 \leq \text{FSW} < 350$ kHz	325
$351 \leq \text{FSW} < 410$ kHz	375
$411 \leq \text{FSW} < 500$ kHz	450
$501 \leq \text{FSW} < 600$ kHz	550
$601 \leq \text{FSW} < 700$ kHz	650
$701 \leq \text{FSW} < 820$ kHz	750
$821 \leq \text{FSW} < 1000$ kHz	900
$1001 \leq \text{FSW} < 1200$ kHz	1100
$1201 \leq \text{FSW} < 1400$ kHz	1300
$1401 \leq \text{FSW} < 1650$ kHz	1500

FREQUENCY\_SWITCH values greater than 1100 kHz can require higher VDD5 current than can be provided by the internal AVIN to VDD5 linear regulator. Programming FREQUENCY\_SWITCH to a value greater than 1100

kHz without an external source to VDD5 can result in repeated start-up and shut-down attempt. FRQUENCY\_SWITCH values greater than 1100 kHz are not recommended for Stacked Multi-phase operation.

## 7.6.28 (35h) VIN\_ON

CMD Address	35h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11, per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

VIN\_ON command sets the value of the input voltage, in Volts, at which the unit should start power conversion.

**7-34. (35h) VIN\_ON Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VON_EXP					VON_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VON_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-44. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	VON_EXP	RW	11110b	Linear format two's complement exponent, -2
10:0	VON_MAN	RW	NVM	Linear format two's complement mantissa. Refer to the following text for more information.

Attempts to write (35h) VIN\_ON to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### Command Resolution and NVM Store/Restore Behavior

(35h) VIN\_ON and (36h) VIN\_OFF have limited hardware range and resolution as well as limited NVM allocation. While the command will accept any binary value within the valid range, values not exactly represented by the hardware resolution will be rounded down to the next lower supported threshold for implementation or upon restore from NVM during Power-On Reset or (16h) RESTORE\_USER\_ALL. (35h) VIN\_ON hardware supports all values from 2.50 V to 15.75 V in 0.25-V steps.

Note that the LOW\_VIN fault condition is masked until the sensed input voltage exceeds the VIN\_ON threshold for the first time following a power-on reset. Control/Enable pin toggles and EEPROM store/restore operations do not reset this masking.

## 7.6.29 (36h) VIN\_OFF

CMD Address	36h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11, per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

(36h) [VIN\\_OFF](#) command sets the value of the PVIN input voltage, in Volts, at which the unit should stop power conversion. If the Power Conversion Enable conditions as defined by (02h) [ON\\_OFF\\_CONFIG](#) are met and PVIN is less than (36h) [VIN\\_OFF](#), the output off due to low VIN bit in (7Ch) [STATUS\\_INPUT](#) is set.

**图 7-35. (36h) VIN\_OFF Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	R	RW	RW	RW
VOFF_EXP					VOFF_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOFF_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-45. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	VOFF_EXP	RW	11110b	Linear format two's complement exponent
10:0	VOFF_MAN	RW	NVM	Linear format two's complement mantissa. Refer to the following text.

Attempts to write (36h) [VIN\\_OFF](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### Command Resolution and NVM Store/Restore Behavior

(35h) [VIN\\_ON](#) and (36h) [VIN\\_OFF](#) have limited hardware range and resolution as well as limited NVM allocation. While the command will accept any binary value within the valid range, values not exactly represented by the hardware resolution will be rounded down to the next lower supported threshold for implementation or upon restoration from NVM during Power-On Reset or (16h) [RESTORE\\_USER\\_ALL](#). (36h) [VIN\\_OFF](#) hardware supports all values from 2.25 V to 15.75 V in 0.25-V steps.

While it is possible to set (36h) [VIN\\_OFF](#) equal to or greater than (35h) [VIN\\_ON](#), it is not advisable and can produce rapid enabling and disabling of conversion and undesirable operation.

### 7.6.30 (37h) INTERLEAVE

CMD Address	37h
Write Transaction:	Write Word (Single Phase Only)
Read Transaction:	Read Word
Format:	Four Hexadecimal values
Phased:	No, Read only in Multi-phase stack
Updates:	On-the-fly
NVM Back-up:	EEPROM or Pin Detection

INTERLEAVE sets the phase delay between the external SYNC (IN or OUT) and the internal PMW oscillator.

**图 7-36. (37h) INTERLEAVE Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	RW	RW	RW	RW
Not Used				GROUPID			
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
NUM_GROUP				ORDER			

LEGEND: R/W = Read/Write; R = Read only

**表 7-46. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:12	Not Used	R	0h	Not used, set to b'0000.
11:8	GROUPID	RW	NVM	Group ID Number. Set to 0h to Fh.
7:4	NUM_GROUP	RW	NVM	Number in Group, sets the number of phases positions and the phase shift for each value of ORDER. Set to value 1h to 4h.
3:0	ORDER	RW	NVM	Order within the group. Each value of ORDER adds a phase shift equal to $360^\circ / \text{NUM\_GROUP}$ . Set to value 0h to NUM_GROUP - 1.

**表 7-47. Supported INTERLEAVE Settings**

Number in Group	Order	Phase Position ( $^\circ$ )
1	0	0
2	0	0
2	1	180
3	0	0
3	1	120
3	2	240
4	0	0
4	1	90
4	2	180
4	3	270

The (37h) INTERLEAVE command is used to arrange multiple devices sharing a common SYNC signal in time. The phase delay added to each device is equal to  $360^\circ / \text{Number in Group} \times \text{Order}$ . To prevent misaligning the phases of a multi-phase stack, (37h) INTERLEAVE is read only when the TPS546B24A is configured as part of a



multi-phase stack. The Read/Write status of the (37h) **INTERLEAVE** command is set based on the state of the (ECh) **MFR\_SPECIFIC\_28 (STACK\_CONFIG)** command at power-on and is not updated if (ECh) **MFR\_SPECIFIC\_28 (STACK\_CONFIG)** is later changed. If (37h) **INTERLEAVE** will be used to program the phase position of a stand-alone device, the TPS546B24A must be configured as a stand-alone device at power-on to ensure write capability of the (37h) **INTERLEAVE** command.

### 7.6.31 (38h) IOUT\_CAL\_GAIN

CMD Address	38h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11, per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

(38h) [IOUT\\_CAL\\_GAIN](#) is used to trim the gain of the output current reported by the [READ\\_IOUT](#) command. The value is a unitless gain factor applied to the internally sensed current measurement. This unitless gain factor results in (38h) [IOUT\\_CAL\\_GAIN](#) having an inverse effect on (8Ch) [READ\\_IOUT](#) that the standard mΩ unit for PMBus. It defaults to a value of 1.

图 7-37. (38h) IOUT\_CAL\_GAIN Register Map

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
IOCG_EXP					IOCG_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
IOCG_MAN							

LEGEND: R/W = Read/Write; R = Read only

表 7-48. Register Field Descriptions

Bit	Field	Access	Reset	Description
15:11	IOCG_EXP	RW	11001b	Linear format, two's complement exponent
10:0	IOCG_MAN	RW	NVM	Linear format, two's complement mantissa

Changing (38h) [IOUT\\_CAL\\_GAIN](#) will adjust the overcurrent setting programmed by (46h) [IOUT\\_OC\\_FAULT\\_LIMIT](#) or (4Ah) [IOUT\\_OC\\_WARN\\_LIMIT](#) according to the new value of (38h) [IOUT\\_CAL\\_GAIN](#).

Attempts to write (38h) [IOUT\\_CAL\\_GAIN](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

#### Command Resolution and NVM Store/Restore Behavior

The (38h) [IOUT\\_CAL\\_GAIN](#) command is implemented using the TPS546B24A internal telemetry system. As a result, the value of this command can be programmed with very high resolution using the linear format. However, the TPS546B24A provides only limited NVM-backed options for this command. Following a power-cycle or NVM Store/Restore operation, the value will be rounded to the nearest 1/64 with a maximum supported value of 1.984 (1 63/64).

### 7.6.32 (39h) IOUT\_CAL\_OFFSET

CMD Address	39h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11, per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	EEPROM
Updates:	On-the-fly

IOUT\_CAL\_OFFSET is used to compensate for offset errors in the [READ\\_IOUT](#) command. Each [PHASE](#) in a stack can apply an independent IOUT\_CAL\_OFFSET value. The effective IOUT\_CAL\_OFFSET value for a stack is equal to the sum of the IOUT\_CAL\_OFFSET values from all devices in the stack.

**图 7-38. (39h) IOUT\_CAL\_OFFSET Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
IOCOS_EXP					IOCOS_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
IOCOS_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-49. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	IOCOS_EXP	RW	11100b	Linear format, two's complement exponent
10:0	IOCOS_MAN	RW	NVM	Linear format, two's complement mantissa

Attempts to write [\(39h\) IOUT\\_CAL\\_OFFSET](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

#### Command Resolution and NVM Store/Restore Behavior

The [\(39h\) IOUT\\_CAL\\_OFFSET](#) command is implemented using the TPS546B24A internal telemetry system. As a result, the value of this command can be programmed with very high resolution using the linear format. However, the TPS546B24A only provides limited NVM-backed options for this command. Following a power-cycle or NVM Store/Restore operation, the value will be restored to one of the supported values, according to the value present during the last NVM store operation. During operation, updates to this command with higher resolution, will be supported, and accepted as long as they fall between the minimum and maximum supported values given.

#### Phased Command Behavior

PHASE = 00h to 03h: Writes to [\(39h\) IOUT\\_CAL\\_OFFSET](#) modify the current sense offset for individual phases. Reads to [\(39h\) IOUT\\_CAL\\_OFFSET](#) return the configured current sense offset for individual phases.

PHASE = FFh: Writes to [\(39h\) IOUT\\_CAL\\_OFFSET](#) modify the total current sense offset for all individual phases. Individual phases will be assigned an IOUT\_CAL\_OFFSET value equal to the written value divided by the number of phases. Reads to [\(39h\) IOUT\\_CAL\\_OFFSET](#) return the configured current sense offset for [PHASE](#) = 00h times the number of phases.

### 7.6.33 (40h) VOUT\_OV\_FAULT\_LIMIT

CMD Address	40h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16 Relative or Absolute per <a href="#">VOUT_MODE</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [VOUT\\_OV\\_FAULT\\_LIMIT](#) command sets the value of the output voltage measured at the sense or output pins that causes an output overvoltage fault. [VOUT\\_OV\\_FAULT\\_LIMIT](#) sets an over-voltage threshold relative to the current [VOUT\\_COMMAND](#). Updates to [VOUT\\_COMMAND](#) do not update the value of [VOUT\\_OV\\_FAULT\\_LIMIT](#) when the absolute format is used. Note that even with [VOUT\\_MODE](#) configured in absolute format, the true overvoltage fault limit remains relative to the current [VOUT\\_COMMAND](#). [VOUT\\_OV\\_FAULT\\_LIMIT](#) is active as soon as the TPS546B24A completes its Power-On Reset, even if output conversion is disabled.

Following an overvoltage fault condition, the TPS546B24A responds according to [VOUT\\_OV\\_FAULT\\_RESPONSE](#).

**图 7-39. (40h) VOUT\_OV\_FAULT\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_OVF (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_OVF (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-50. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_OVF	RW	See Below.	Sets the overvoltage fault limit. Format is per <a href="#">VOUT_MODE</a> .

### Hardware Support and Value Mapping

The Hardware for [VOUT\\_OV\\_FAULT\\_LIMIT](#) is implemented as a fixed percentage of the current output voltage target. Depending on the [VOUT\\_MODE](#) setting, the value written to [VOUT\\_OV\\_FAULT\\_LIMIT](#) must be mapped to the hardware percentage.

Programmed values not exactly equal to one of the hardware relative values shall be rounded up to the next available relative value supported by hardware. The hardware supports values from 105% to 140% of [VOUT\\_COMMAND](#) in 2.5% steps. When output conversion is disabled, the hardware supports values from 110% to 140% of [VOUT\\_COMMAND](#) in 10% steps.

Attempts to write [VOUT\\_OV\\_FAULT\\_LIMIT](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### 7.6.34 (41h) VOUT\_OV\_FAULT\_RESPONSE

CMD Address	41h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [VOUT\\_OV\\_FAULT\\_RESPONSE](#) instructs the device on what action to take in response to an output overvoltage fault. Upon triggering the overvoltage fault, the controller TPS546B24A responds according to the data byte below, and the following actions are taken:

- Set the VOUT\_OV\_FAULT bit in the [STATUS\\_BYTE](#).
- Set the VOUT bit in the [STATUS\\_WORD](#).
- Set the VOUT\_OVF bit in the [STATUS\\_VOUT](#) register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**7-40. (41h) VOUT\_OV\_FAULT\_RESPONSE Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VO_OV_RESP		VO_OV_RETRY			VO_OV_DELAY		

LEGEND: R/W = Read/Write; R = Read only

**表 7-51. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:6	VO_OV_RE SP	RW	NVM	Output overvoltage response 00b: Ignore. Continue operating without interruption. 01b: Shutdown. Shutdown and retry according to VO_OV_RETRY. 10b: Shutdown. Shutdown and retry according to VO_OV_RETRY. 11b: Invalid/Unsupported
5:3	VO_OV_RE TRY	RW	NVM	0d: Do not attempt to restart (latch off). 1d-6d: After shutting down, wait one HICCUP period, and attempt to restart up to 1 - 6 times. After 1 - 6 failed restart attempts, do not attempt to restart (latch off). 7d: After shutting down, wait one HICCUP period, and attempt to restart indefinitely, until commanded OFF, or a successful start-up occurs.
2:0	VO_OV_DE LAY	RW	NVM	0d: VO_OV HICCUP period is equal to TON_RISE. 1d - 7d: VO_OV HICCUP period is equal to 1 - 7 times TON_RISE.

Attempts to write [VOUT\\_OV\\_FAULT\\_RESPONSE](#) to any value outside those specified as valid, will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

A Restart Attempt is successful and the restart limit counter is reset to 0 when no fault with a shut-down response is observed after one (61h) [TON\\_RISE](#) time after completing (61h) [TON\\_RISE](#) or after (62h) [TON\\_MAX\\_FAULT\\_LIMIT](#) if (62h) [TON\\_MAX\\_FAULT\\_LIMIT](#) is not set to 0 ms (Disabled).

If (41h) [VOUT\\_OV\\_FAULT\\_RESPONSE](#) is configured to ignore a VOUT\_OV\_FAULT, and a VOUT\_OV\_FAULT is present at the time of enabling the device, the device will not start up. To ensure the part will ignore any potential VOUT\_OV\_FAULT at start-up, it is recommended to set the (40h) [VOUT\\_OV\\_FAULT\\_LIMIT](#) greater than the maximum possible input voltage applied during start-up.

### 7.6.35 (42h) VOUT\_OV\_WARN\_LIMIT

CMD Address	42h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16 Relative or Absolute per <a href="#">VOUT_MODE</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [VOUT\\_OV\\_WARN\\_LIMIT](#) command sets the value of the output voltage at the sense or output pins that causes an output voltage high warning. This value is typically less than the output overvoltage threshold. The [OV\\_WARN\\_LIMIT](#) sets an overvoltage threshold relative to the current [VOUT\\_COMMAND](#). Updates to [VOUT\\_COMMAND](#) do not update the value of [VOUT\\_OV\\_FAULT\\_LIMIT](#) when the absolute format is used.

When the sensed output voltage exceeds the [VOUT\\_OV\\_WARN\\_LIMIT](#) threshold, the following actions are taken:

- Set the VOUT bit in the [STATUS\\_WORD](#).
- Set the VOUT\_OVW bit in the [STATUS\\_VOUT](#) register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**图 7-41. (42h) VOUT\_OV\_WARN\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_OVW (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_OVW (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-52. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_OVW	RW	NVM	Sets the overvoltage warning limit. Format is per <a href="#">VOUT_MODE</a> .

### Hardware Support and Value Mapping

The Hardware for [VOUT\\_OV\\_WARN\\_LIMIT](#) is implemented as a fixed percentage of the current output voltage target. Depending on the [VOUT\\_MODE](#) setting, the value written to [VOUT\\_OV\\_WARN\\_LIMIT](#) must be mapped to a hardware percentage.

Programmed values not exactly equal to one of the hardware relative values shall be rounded up to the next available relative value supported by hardware. The hardware supports values from 103% to 116% [VOUT\\_COMMAND](#) in 1% steps.

Attempts to write (42h) [VOUT\\_OV\\_WARN\\_LIMIT](#) to any value outside those specified as valid, will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### 7.6.36 (43h) VOUT\_UV\_WARN\_LIMIT

CMD Address	43h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16 Relative or Absolute per <a href="#">VOUT_MODE</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [VOUT\\_UV\\_WARN\\_LIMIT](#) command sets the value of the output voltage at the sense or output pins that causes an output voltage low warning. The [VOUT\\_UV\\_WARN\\_LIMIT](#) sets an undervoltage threshold relative to the current [VOUT\\_COMMAND](#). Updates to [VOUT\\_COMMAND](#) do not update [VOUT\\_UV\\_WARN\\_LIMIT](#) when the absolute format is used.

When the sensed output voltage exceeds the [VOUT\\_UV\\_WARN\\_LIMIT](#) threshold, the following actions are taken:

- Set the VOUT bit in the [STATUS\\_WORD](#).
- Set the VOUT\_UVW bit in the [STATUS\\_VOUT](#) register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**图 7-42. (43h) VOUT\_UV\_WARN\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_UVW (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_UVW (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-53. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_UVW	RW	NVM	Sets the undervoltage warning limit. Format is per <a href="#">VOUT_MODE</a> .

### Hardware Mapping and Supported Values

The Hardware for [VOUT\\_UV\\_WARN\\_LIMIT](#) is implemented as a fixed percentage relative to the current output voltage target. Depending on the [VOUT\\_MODE](#) setting, the value written to [VOUT\\_UV\\_WARN\\_LIMIT](#) must be mapped to the hardware percentage.

Programmed values not exactly equal to one of the hardware relative values is rounded down to the next available relative value supported by hardware. The hardware supports values from 84% to 97% [VOUT\\_COMMAND](#) in 1% steps.

Attempts to write (43h) [VOUT\\_UV\\_WARN\\_LIMIT](#) to any value outside those specified as valid, will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### 7.6.37 (44h) VOUT\_UV\_FAULT\_LIMIT

CMD Address	44h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	ULINEAR16 Absolute per <a href="#">VOUT_MODE</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [VOUT\\_UV\\_FAULT\\_LIMIT](#) command sets the value of the output voltage at the sense or output pins that causes an output voltage fault. The [VOUT\\_UV\\_FAULT\\_LIMIT](#) sets an undervoltage threshold relative to the current [VOUT\\_COMMAND](#). Updates to [VOUT\\_COMMAND](#) do not update [VOUT\\_UV\\_FAULT\\_LIMIT](#) when the absolute format is used.

When the undervoltage fault condition is triggered, the TPS546B24A responds according to [VOUT\\_UV\\_FAULT\\_RESPONSE](#).

**图 7-43. (44h) VOUT\_UV\_FAULT\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_UVF (High Byte)							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VOUT_UVF (Low Byte)							

LEGEND: R/W = Read/Write; R = Read only

**表 7-54. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	VOUT_UVW	RW	NVM	Sets the undervoltage fault limit. Format is per <a href="#">VOUT_MODE</a>

### Hardware Mapping and Supported Values

The Hardware for [VOUT\\_UV\\_FAULT\\_LIMIT](#) is implemented as a fixed percentage relative to the current output voltage target. Depending on the [VOUT\\_MODE](#) setting, the value written to [VOUT\\_UV\\_FAULT\\_LIMIT](#) must be mapped to the hardware percentage.

Programmed values not exactly equal to one of the hardware relative values are rounded down to the next available relative value supported by hardware. The hardware supports values from 60% to 95% of [VOUT\\_COMMAND](#) in 2.5% steps.

Attempts to write (44h) [VOUT\\_UV\\_FAULT\\_LIMIT](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.



### 7.6.38 (45h) VOUT\_UV\_FAULT\_RESPONSE

CMD Address	45h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

- The [VOUT\\_UV\\_FAULT\\_RESPONSE](#) instructs the device on what action to take in response to an output undervoltage fault.

The [VOUT\\_UV\\_FAULT\\_RESPONSE](#) instructs the device on what action to take in response to an output undervoltage fault. Upon triggering the overvoltage fault, the TPS546B24A responds according to the data byte below, and the following actions are taken:

- Set the NONE OF THE ABOVE bit in the [STATUS\\_BYTE](#).
- Set the VOUT bit in the [STATUS\\_WORD](#).
- Set the VOUT\_UVF bit in the [STATUS\\_VOUT](#) register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**表 7-44. (45h) VOUT\_UV\_FAULT\_RESPONSE Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VO_UV_RESP		VO_UV_RETRY			VO_UV_DLY		

LEGEND: R/W = Read/Write; R = Read only

**表 7-55. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:6	VO_UV_RESP	RW	NVM	Output undervoltage response 00b: Ignore. Continue operating without interruption. 01b: Shutdown after Delay, as set by VO_UV_DELY 10b: Shutdown Immediately Other: Invalid/Unsupported
5:3	VO_UV_RETRY	RW	NVM	Output undervoltage retry 0d: Do not attempt to restart (latch off). 1d-6d: After shutting down, wait one HICCUP period, and attempt to restart upto 1 - 6 times. After 1 - 6 failed restart attempts, do not attempt to restart (latch off). 7d: After shutting down, wait one HICCUP period, and attempt to restart indefinitely, until commanded OFF, or a successful start-up occurs.
2:0	VO_UV_DLY	RW	NVM	Output undervoltage delay time for respond after delay and HICCUP 0d: Shutdown delay of three PWM_CLK, HICCUP equal to TON_RISE 1d: Shutdown delay of three PWM_CLK, HICCUP equal to TON_RISE 2d - 4d: Shutdown delay of five PWM_CLK, HICCUP equal to 2 - 4 times TON_RISE 5d - 7d: Shutdown delay of nine PWM_CLK, HICCUP equal to 5 - 7 times TON_RISE

Attempts to write [\(45h\) VOUT\\_UV\\_FAULT\\_RESPONSE](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### 7.6.39 (46h) IOUT\_OC\_FAULT\_LIMIT

CMD Address	46h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	EEPROM or Pin Detection
Updates:	On-the-fly

The [IOUT\\_OC\\_FAULT\\_LIMIT](#) command sets the value of the output current that causes the overcurrent detector to indicate an overcurrent fault condition. While each TPS546B24A device in a multi-phase stack has its own IOUT\_OC\_FAULT\_LIMIT and comparator, the effective current limit of the multi-phase stack is equal to the lowest IOUT\_OC\_FAULT\_LIMIT setting times the number of phases in the stack.

When the overcurrent fault is triggered, the TPS546B24A responds according to [IOUT\\_OC\\_FAULT\\_RESPONSE](#).

**图 7-45. (46h) IOUT\_OC\_FAULT\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
IO_OCF_EXP					IO_OCF_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
IO_OCF_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-56. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	IO_OCF_EXP	RW	11110b	Linear format two's complement exponent
10:0	IO_OCF_MAN	RW	NVM	Linear format two's complement mantissa Multi-phase Stack Current Limit up to 62 A x Number of Phases (PHASE = FFh) Per Phase OCL: up to 31 A (PHASE != FFh)

Attempts to write (46h) [IOUT\\_OC\\_FAULT\\_LIMIT](#) to any value outside those specified as valid, will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

#### Command Resolution and NVM Store/Restore Behavior

The Per-PHASE (PHASE != FFh) [IOUT\\_OC\\_FAULT\\_LIMIT](#) is implemented in analog hardware. The analog hardware supports current limits from 4 A to 31 A in 1-A steps. Programmed values not exactly equal to hardware supported values will be rounded up to the next available supported value. Values less than 8 A per device can be written to IOUT\_OC\_FAULT\_LIMIT, but values less than 4 A per device will be implemented as 4 A in hardware. The TPS546B24A provides only limited NVM-backed options for this command. Following a power-cycle or NVM Store/Restore operation, the value will be rounded to the nearest NVM supported value. The NVM supports values up to 31 A in 0.25-A steps.

#### Phased Command Behavior

Write when PHASE = FFh: Set IOUT\_OC\_FAULT\_LIMIT for each phase to the written value divided by the number of phases.

Read when PHASE = FFh: Report the IOUT\_OC\_FAULT\_LIMIT value of PHASE = 00h (Master) times the number of phases.

Write when PHASE != FFh: Set IOUT\_OC\_FAULT\_LIMIT for the current phase to the written value.

Read when PHASE != FFh: Report the IOUT\_OC\_FAULT\_LIMIT value of the current phase.

## 7.6.40 (47h) IOUT\_OC\_FAULT\_RESPONSE

CMD Address	47h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The **IOUT\_OC\_FAULT\_RESPONSE** instructs the device on what action to take in response to an overcurrent fault. Upon triggering the overcurrent fault, the TPS546B24A responds according to the data byte below, and the following actions are taken:

- Set the IOUT\_OC bit in the **STATUS\_BYTE**.
- Set the IOUT bit in the **STATUS\_WORD**.
- Set the IOUT\_OCF bit in the **STATUS\_IOUT** register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**图 7-46. (47h) IOUT\_OC\_FAULT\_RESPONSE Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	R	R	R
IO_OC_RESP		IO_OC_RETRY			IO_OC_DELAY		

LEGEND: R/W = Read/Write; R = Read only

**表 7-57. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:6	IO_OC_RESP	RW	NVM	Output overcurrent response 00b: Ignore. Continue operating without interruption. 01b: Invalid 10b: Shutdown after Delay, as set by IO_OC_DELAY 11b: Shutdown Immediately
5:3	IO_OC_RETRY	RW	NVM	Output overcurrent retry 0d: Do not attempt to restart (latch off). 1d-6d: After shutting down, wait one HICCUP period, and attempt to restart upto 1 - 6 times. After 1 - 6 failed restart attempts, do not attempt to restart (latch off). 7d: After shutting down, wait one HICCUP period, and attempt to restart indefinitely, until commanded OFF, or a successful start-up occurs.
2:0	IO_OC_DELAY	RW	NVM	Output overcurrent delay time for respond after delay and HICCUP 0d: Shutdown delay of three PWM_CLK, HICCUP equal to TON_RISE 1d: Shutdown delay of three PWM_CLK, HICCUP equal to TON_RISE 2d - 4d: Shutdown delay of five PWM_CLK, HICCUP equal to 2 - 4 times TON_RISE 5d - 7d: Shutdown delay of nine PWM_CLK, HICCUP equal to 5 - 7 times TON_RISE

Attempts to write **(47h) IOUT\_OC\_FAULT\_RESPONSE** to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

## 7.6.41 (4Ah) IOUT\_OC\_WARN\_LIMIT

CMD Address	4Ah
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	EEPROM or Pin Detection
Updates:	On-the-fly

The [IOUT\\_OC\\_WARN\\_LIMIT](#) command sets the value of the output current, in amperes, that causes the overcurrent detector to indicate an overcurrent warning condition. The units are amperes.

IOUT\_OC\_WARN\_LIMIT is a phased command. Each phase will report an output current overcurrent warning independently.

In response to an overcurrent warning condition, the TPS546B24A takes the following action:

- Set the NONE OF THE ABOVE bit in the [STATUS\\_BYTE](#).
- Set the IOUT bit in the [STATUS\\_WORD](#).
- Set the IOUT\_OCW bit in the [STATUS\\_IOUT](#) register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**7-47. (4Ah) IOUT\_OC\_WARN\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
IOOCW_EXP					IOOCW_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
IOOCW_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-58. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	IOOCW_EXP	RW	11110b	Linear format two's complement exponent
10:0	IOOCW_MAN	RW	NVM	Linear format two's complement mantissa Supported values up to 31 A times the number of phases.

Attempts to write [\(4Ah\) IOUT\\_OC\\_WARN\\_LIMIT](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### Command Resolution and NVM Store/Restore Behavior

The Per-PHASE (PHASE != FFh) [IOUT\\_OC\\_WARN\\_LIMIT](#) is implemented in analog hardware. The analog hardware supports current limits from 4 A to 31 A in 1-A steps. Programmed values not exactly equal to hardware supported values will be rounded up to the next available supported value. Values less than 8 A per device can be written to IOUT\_OC\_FAULT\_LIMIT, but values less than 4 A per device will be implemented as 4 A in hardware. The TPS546B24A provides only limited NVM-backed options for this command. Following a power-cycle or NVM Store/Restore operation, the value will be rounded to the nearest NVM supported value. The NVM supports values up to 31 A in 0.25-A steps.

### 7.6.42 (4Fh) OT\_FAULT\_LIMIT

CMD Address	4Fh
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [OT\\_FAULT\\_LIMIT](#) command sets the value of the temperature limit, in degrees Celsius, that causes an overtemperature fault condition.

The converter response to an overtemperature event is described in [OT\\_FAULT\\_RESPONSE](#).

**图 7-48. (4Fh) OT\_FAULT\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
OTF_EXP					OTF_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
OTF_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-59. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	OTF_EXP	RW	00000b	Linear format two's complement exponent
10:0	OTF_MAN	RW	NVM	Linear format two's complement mantissa. Refer to the following text.

Attempts to write [\(4Fh\) OT\\_FAULT\\_LIMIT](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

#### Command Resolution and NVM Store/Restore Behavior

The [\(4Fh\) OT\\_FAULT\\_LIMIT](#) command is implemented using the TPS546B24A internal telemetry system. As a result, the value of this command can be programmed with very high resolution using the linear format. However, the TPS546B24A provides only limited NVM-backed options for this command. Following a power-cycle or NVM Store/Restore operation, the value will be restored to the nearest NVM supported value. The NVM supports values from 0°C to 160°C in 1°C steps. Programming a value of 255°C will disable Programmable Overtemperature Fault Limit without disabling the on-die Bandgap thermal shutdown.

### 7.6.43 (50h) OT\_FAULT\_RESPONSE

CMD Address	50h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [OT\\_FAULT\\_RESPONSE](#) command instructs the device on what action to take in response to an Overtemperature Fault. Upon triggering the overtemperature fault, the converter responds per the data byte below, and the following actions are taken:

- Set the TEMP bit in the [STATUS\\_BYTE](#).
- Set the OTF bit in the [STATUS\\_TEMPERATURE](#) register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

Note: the OT Fault hysteresis is set by the [\(51h\) OT\\_WARN\\_LIMIT](#). When [\(8Dh\) READ\\_TEMPERATURE\\_1](#) falls below [\(51h\) OT\\_WARN\\_LIMIT](#), the overtemperature fault condition will be released and restart will be allowed if selected by [\(50h\) OT\\_FAULT\\_RESPONSE](#). If [\(51h\) OT\\_WARN\\_LIMIT](#) is programmed higher than [\(4Fh\) OT\\_FAULT\\_LIMIT](#), a default hysteresis of 20°C will be used instead.

**图 7-49. (50h) OT\_FAULT\_RESPONSE Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
OTF_RESP		OT_RETRY			OT_DELAY		

LEGEND: R/W = Read/Write; R = Read only

**表 7-60. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:6	OTF_RESP	RW	NVM	Overtemperature fault response 00b: Ignore. Continue operating without interruption. 01b: Delayed Shutdown Continue Operating for 10ms x OT_DELAY. If OT_FAULT is still present, shut down and restart according to OT_RETRY. 10b: Immediate Shutdown. Shut down and restart according to OT_RETRY. 11b: Shutdown until Temperature is below OT_WARN_LIMIT, then restart according to OT_RETRY*.
5:3	OT_RETRY	RW	NVM	Overtemperature retry. 0d: Do not attempt to restart (latch off). 1d-6d: After shutting down, wait one HICCUP period, and attempt to restart up to 1 - 6 times. After 1 - 6 failed restart attempts, do not attempt to restart (latch off). Restart attempts that occur while temperature is above OT_WARN_LIMIT will not be observable but will be counted. 7d: After shutting down, wait one HICCUP period, and attempt to restart indefinitely, until commanded OFF or a successful start-up occurs.
2:0	OT_DELAY	RW	NVM	Overtemperature delay time for respond after delay and HICCUP 0d: Shutdown delay of 0 ms, HICCUP equal to TON_RISE, HICCUP delay equal to TON_RISE 1d - 7d: Shutdown delay of 10 - 70 ms, HICCUP equal to 1 - 7 times TON_RISE

Attempts to write (50h) OT\_FAULT\_RESPONSE to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

\*When (50h) OT\_FAULT\_RESPONSE OTF\_RESP (Bits 7:6) are set to 11b - shut down until temperature is below (51h) OT\_WARN\_LIMIT, issuing a (03h) CLEAR\_FAULTS command while the temperature is between (4Fh) OT\_FAULT\_LIMIT and (51h) OT\_WARN\_LIMIT can result in the TPS546B24A remaining in the OT\_FAULT state until the temperature rises above (4Fh) OT\_FAULT\_LIMIT or disabled and enabled according to (02h) ON\_OFF\_CONFIG.

If (50h) OT\_FAULT\_RESPONSE is configured to ignore a OT\_FAULT, and a OT\_FAULT is present at the time of enabling the device, the device will not start up. To ensure the part will ignore any potential OT\_FAULT at start-up, it is recommended to set the (4Fh) OT\_FAULT\_LIMIT greater than the maximum possible temperature during start-up.



#### 7.6.44 (51h) OT\_WARN\_LIMIT

CMD Address	51h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [OT\\_WARN\\_LIMIT](#) command sets the temperature, in degrees Celsius, of the unit at which it should indicate an Overtemperature Warning alarm. The units are degrees C.

Upon triggering the overtemperature fault, the converter responds per the data byte below, and the following actions are taken:

- Set the TEMP bit in the [STATUS\\_BYTE](#).
- Set the OTW bit in the [STATUS\\_TEMPERATURE](#) register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**7-50. (51h) OT\_WARN\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
OTW_EXP					OTW_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
OTW_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-61. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	OTW_EXP	RW	00000b	Linear format two's complement exponent
10:0	OTW_MAN	RW	NVM	Linear format two's complement mantissa. Refer to the following text.

Attempts to write (51h) [OT\\_WARN\\_LIMIT](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

#### Command Resolution and NVM Store/Restore Behavior

The (51h) [OT\\_WARN\\_LIMIT](#) command is implemented using the TPS546B24A internal telemetry system. As a result the value of this command can be programmed with very high resolution using the linear format. However, the TPS546B24A provides only limited NVM-backed options for this command. Following a power-cycle or NVM Store/Restore operation, the value will be restored to the nearest NVM supported value. The NVM supports values from 0°C to 160°C in 1°C steps. Programming OT\_WARN\_LIMIT to a value of 255°C will disable the OT\_WARN\_LIMIT function.

OT\_WARN\_LIMIT is used to provide hysteresis to OT\_FAULT\_LIMIT faults. If OT\_WARN\_LIMIT is programmed greater than OT\_FAULT\_LIMIT, including disabling OT\_WARN\_LIMIT with a value of 255°C, a default hysteresis of 20°C will be used instead.

### 7.6.45 (55h) VIN\_OV\_FAULT\_LIMIT

CMD Address	55h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The (55h) [VIN\\_OV\\_FAULT\\_LIMIT](#) command sets the PVIN voltage, in volts, when a VIN\_OV\_FAULT is declared. The response to a detected VIN\_OV\_FAULT is determined by the settings of (56h) [VIN\\_OV\\_FAULT\\_RESPONSE](#). (55h) [VIN\\_OV\\_FAULT\\_LIMIT](#) is typically used to stop switching in the event of excessive input voltage, which can result in over-stress damage to the power FETs due to ringing on the SW node.

**图 7-51. (55h) VIN\_OV\_FAULT\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VINOVF_EXP					VINOVF_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VINOVF_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-62. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	VINOVF_EXP	RW	11110b	Linear format two's complement exponent
10:0	VINOVF_MAN	RW	NVM	Linear format two's complement mantissa

Attempts to write (55h) [VIN\\_OV\\_FAULT\\_LIMIT](#) beyond the supported range will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3. (55h) [VIN\\_OV\\_FAULT\\_LIMIT](#) supports values from 5 V to 22 V in 0.25-V steps. Following a Power Cycle or STORE/RESTORE, (55h) [VIN\\_OV\\_FAULT\\_LIMIT](#) will be restored to the nearest supported value.

## 7.6.46 (56h) VIN\_OV\_FAULT\_RESPONSE

CMD Address	56h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The VIN\_OV\_FAULT\_RESPONSE command instructs the device on what action to take in response to a PVIN Overvoltage Fault. Upon triggering the PVIN overvoltage fault, the converter responds per the data byte below, and the following actions are taken:

- Set the NONE OF THE ABOVE bit in the [STATUS\\_BYTE](#) register.
- Set the INPUT bit in the upper byte of the STATUS\_WORD register.
- Set the VIN\_OV bit in the STATUS\_INPUT register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**图 7-52. (56h) VIN\_OV\_FAULT\_RESPONSE Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VINOVF_RESP		VINOVF_RETRY			VIN_OVF_DLY		

LEGEND: R/W = Read/Write; R = Read only

**表 7-63. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:6	VIN_OVF_RESP	RW	NVM	PVIN Overvoltage fault response 00b: Ignore. Continue operating without interruption. 01b: Delayed Shutdown Continue Operating for a number of switching cycles defined by VIN_OVF_DLY, then if fault persists, shut down and restart according to VIN_OV_RETRY. 10b: Immediate Shutdown. Shut down and restart according to VIN_OV_RETRY. 11b: Invalid / Not Supported
5:3	VIN_OVF_RETRY	RW	NVM	PVIN Overvoltage retry 0d: Do not attempt to restart (latch off). 1d-6d: After shutting down, wait one HICCUP period, and attempt to restart up to 1 - 6 times. After 1 - 6 failed restart attempts, do not attempt to restart (latch off). Restart attempts that occur while PVIN voltage is above VIN_OV_FAULT_LIMIT will not be observable but will be counted 7d: After shutting down, wait one HICCUP period, and attempt to restart indefinitely, until commanded OFF, or a successful start-up occurs.
2:0	VIN_OVF_DLY	RW	NVM	PVIN Overvoltage delay time for respond after delay and HICCUP 0d: Shutdown delay of three PWM_CLK, HICCUP equal to TON_RISE 1d: Shutdown delay of three PWM_CLK, HICCUP equal to TON_RISE 2d - 4d: Shutdown delay of five PWM_CLK, HICCUP equal to 2 - 4 times TON_RISE 5d - 7d: Shutdown delay of nine PWM_CLK, HICCUP equal to 5 - 7 times TON_RISE

If (56h) VIN\_OV\_FAULT\_RESPONSE is configured to ignore a VIN\_OV\_FAULT, and a VIN\_OV\_FAULT is present at the time of enabling the device, the device will not start up. To ensure the part will ignore any potential

VIN\_OV\_FAULT at start-up, it is recommended to set the (55h) VIN\_OV\_FAULT\_LIMIT greater than the maximum possible input voltage applied during start-up.

Attempts to write (56h) VIN\_OV\_FAULT\_RESPONSE to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### 7.6.47 (58h) VIN\_UV\_WARN\_LIMIT

CMD Address	58h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	EEPROM
Updates:	On-the-fly

The (58h) [VIN\\_UV\\_WARN\\_LIMIT](#) command sets the value of the PVIN pin voltage, in volts, that causes the input voltage detector to indicate an input undervoltage warning.

The (58h) [VIN\\_UV\\_WARN\\_LIMIT](#) is a phase command, each phase within a stack will independently detect and report input undervoltage warnings.

In response to an input undervoltage warning condition, the TPS546B24A takes the following action:

- Set the NONE OF THE ABOVE bit in the [STATUS\\_BYTE](#).
- Set the INPUT bit in the [STATUS\\_WORD](#).
- Set the VIN\_UVW bit in the [STATUS\\_INPUT](#) register.
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**图 7-53. (58h) VIN\_UV\_WARN\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
VINUVW_EXP					VINUVW_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
VINUVW_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-64. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	VINUVW_EXP	RW	11110b	Linear format two's complement exponent
10:0	VINUVW_MAN	RW	NVM	Linear format two's complement mantissa

The default (58h) [VIN\\_UV\\_WARN\\_LIMIT](#) is 2.5 V. The programmable range for (58h) [VIN\\_UV\\_WARN\\_LIMIT](#) is 5 V - 22 V. If (58h) [VIN\\_UV\\_WARN\\_LIMIT](#) is programmed above 5 V, (58h) [VIN\\_UV\\_WARN\\_LIMIT](#) cannot be reprogrammed below 5 V.

Attempts to write (58h) [VIN\\_UV\\_WARN\\_LIMIT](#) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

## 7.6.48 (60h) TON\_DELAY

CMD Address	60h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [TON\\_DELAY](#) command sets the time, in milliseconds, from when a start condition is received (as programmed by the [ON\\_OFF\\_CONFIG](#) command) until the output voltage starts to rise.

**图 7-54. (60h) TON\_DELAY Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
TONDLY_EXP					TONDLY_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
TONDLY_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-65. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	TONDLY_EXP	RW	11111b	Linear format two's complement exponent.
10:0	TONDLY_MAN	RW	NVM	Linear format two's complement mantissa. Note, a minimum turn-on delay of approximately 100 $\mu$ s is observed even when TON_DELAY during which the device initializes itself at every power-on.

Attempts to write [\(60h\) TON\\_DELAY](#) beyond the supported range will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3. TON\_DELAY supports values from 0ms to 127.5 ms in 0.5-ms steps. Following a Power Cycle or STORE/RESTORE, TON\_DELAY will be restored to the nearest supported value.

Refer to the [Start-Up and Shutdown](#) behavior section for handling of corner cases with respect to interrupted [TON\\_DELAY](#), [TON\\_RISE](#), [TOFF\\_FALL](#), and [TOFF\\_DELAY](#) times.

## 7.6.49 (61h) TON\_RISE

CMD Address	61h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM or Pin Detection
Updates:	On-the-fly

The [TON\\_RISE](#) command sets the time, in milliseconds, from when the output starts to rise until the voltage has entered the regulation band. This effectively sets the slew rate of the reference DAC during the soft-start period. Note that the rise time is equal to [TON\\_RISE](#) regardless of the value of the target output voltage or [VOUT\\_SCALE\\_LOOP](#).

Due to hardware limitations in the resolution of the reference DAC slew-rate control, longer TON\_RISE times with higher VOUT\_COMMAND voltages can result in some quantization error in the programmed TON\_RISE times with several TON\_RISE times producing the same VOUT slope and TON\_RISE time even with different TON\_RISE settings or different TON\_RISE times for the same TON\_RISE setting and different VOUT\_COMMAND voltages.

**图 7-55. (61h) TON\_RISE Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
TONR_EXP					TONR_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
TONR_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-66. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	TONR_EXP	RW	11110b	Linear format two's complement exponent
10:0	TONR_MAN	RW	NVM	Linear format two's complement mantissa

Attempts to write [\(61h\) TON\\_RISE](#) beyond the supported range will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3. TON\_RISE will support the range from 0ms to 31.75 ms in 0.25-ms steps. Values less than 0.5 ms are supported as 0.5 ms.

### 7.6.50 (62h) TON\_MAX\_FAULT\_LIMIT

CMD Address	62h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [TON\\_MAX\\_FAULT\\_LIMIT](#) command sets an upper limit, in milliseconds, on how long the unit can attempt to power up the output without reaching the target voltage.

The TON\_MAX time is defined as the maximum allowable amount of time from the end of [TON\\_DELAY](#), until the output voltage reaches 85% of the programmed output voltage, as sensed by the READ\_VOUT telemetry at VOSNS - GOSNS.

Note that for the TPS546B24A, the undervoltage fault limit is enabled at the end of TON\_RISE. As a consequence, unless [VOUT\\_UV\\_FAULT\\_RESPONSE](#) is set to ignore, in the case of a “real” TON\_MAX fault (for example, output voltage did not rise quickly enough), UV faults / associated response will always precede TON\_MAX.

The converter response to a TON\_MAX fault event is described in [TON\\_MAX\\_FAULT\\_RESPONSE](#).

**图 7-56. (62h) TON\_MAX\_FAULT\_LIMIT Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
TONMAXF_EXP					TONMAXF_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
TONMAXF_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-67. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	TONMAXF_EXP	RW	11111b	Linear format two's complement exponent
10:0	TONMAXF_MAN	RW	NVM	Linear format two's complement mantissa

Attempts to write [\(62h\) TON\\_MAX\\_FAULT\\_LIMIT](#) beyond its supported range will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3. TON\_MAX\_FAULT\_LIMIT supports values from 0 ms to 127 ms in 0.5-ms steps.

TON\_MAX\_FAULT\_LIMIT compares the last VOUT telemetry value recorded prior to the TON\_MAX\_FAULT\_LIMIT timer expiring to 87.5% of VOUT\_COMMAND to determine a TON\_MAX\_FAULT. Due to delay in VOUT telemetry, a TON\_MAX\_FAULT can be declared if VOUT was less than 87.5% of VOUT\_COMMAND up to 2ms prior to TON\_MAX\_FAULT\_LIMIT.

\*Note: programming TON\_MAX\_FAULT to 0ms disables the TON\_MAX functionality.



## 7.6.51 (63h) TON\_MAX\_FAULT\_RESPONSE

CMD Address	63h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [TON\\_MAX\\_FAULT\\_RESPONSE](#) instructs the device on what action to take in response to TON\_MAX fault. Upon triggering the input TON\_MAX fault, the converter responds per the byte below and the following actions are taken:

- Set the NONE OF THE ABOVE bit in the [STATUS\\_BYTE](#).
- Set the VOUT bit in the [STATUS\\_WORD](#).
- Set the TON\_MAX bit in [STATUS\\_VOUT](#).
- Notify the host per PMBus 1.3.1 Part II specification, section 10.2.

**图 7-57. (63h) TON\_MAX\_FAULT\_RESPONSE Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
TONMAX_RESP		TONMAX_RETRY			TONMAX_DELAY		

LEGEND: R/W = Read/Write; R = Read only

**表 7-68. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:6	TONMAX_RESP	RW	NVM	TON_MAX Fault Response 00b: Ignore. Continue operating without interruption. 01b: Continue Operating for the delay time specified by TONMAX_DELAY, if the fault is still present, shutdown and restart according to TONMAX_RETRY. 10b: Shutdown Immediately and restart according to TONMAX_RETRY. Other: Invalid/Unsupported
5:3	TONMAX_RETRY	RW	NVM	TON_MAX Fault Retry 0d: Do not attempt to restart (latch off). 1d-6d: After shutting down, wait one HICCUP period, and attempt to restart up to 1 - 6 times. 7d: After shutting down, wait one HICCUP period, and attempt to restart indefinitely, until commanded OFF, or a successful start-up occurs.
2:0	TONMAX_DELAY	RW	NVM	TON_MAX delay time for respond after delay and HICCUP 0d: Shutdown delay of 0 ms, HICCUP equal to TON_RISE 1d - 7d: Shutdown delay of 1 - 7 ms, HICCUP equal to 1 - 7 times TON_RISE

Attempts to write [\(63h\) TON\\_MAX\\_FAULT\\_RESPONSE](#) to any value outside those specified as valid, will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

## 7.6.52 (64h) TOFF\_DELAY

CMD Address	64h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [TOFF\\_DELAY](#) command sets the time, in milliseconds, from when a stop condition is received (as programmed by the [ON\\_OFF\\_CONFIG](#) command) until the unit stops transferring energy to the output.

**图 7-58. (64h) TOFF\_DELAY Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
TOFFDLY_EXP					TOFFDLY_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
TOFFDLY_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-69. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	TOFFDLY_EXP	RW	11111b	Linear format two's complement exponent
10:0	TOFFDLY_MAN	RW	NVM	Linear format two's complement mantissa

Attempts to write [\(64h\) TOFF\\_DELAY](#) beyond the supported range will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3. TOFF\_DELAY supports values from 0 ms to 127.5 ms in 0.25-ms steps. An internal delay of up to 50  $\mu$ s will be added to TOFF\_DELAY, even if TOFF\_DELAY is equal to 0 ms.

### 7.6.53 (65h) TOFF\_FALL

CMD Address	65h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly

The [TOFF\\_FALL](#) command sets the time, in milliseconds, from the end of the turnoff delay time until the voltage is commanded to zero. Note that this command can only be used with a device whose output can sink enough current to cause the output voltage to decrease at a controlled rate. This effectively sets the slew rate of the reference DAC during the soft-off period. Note that the fall time is equal to [TOFF\\_FALL](#) regardless of the value of the target output voltage or [VOUT\\_SCALE\\_LOOP](#) for the purposes of slew rate selection based on the target output voltage.

Due to hardware limitations in the resolution of the reference DAC slew-rate control, longer [TOFF\\_FALL](#) times with higher (21h) [VOUT\\_COMMAND](#) voltages can result in some quantization error in the programmed [TOFF\\_FALL](#) times with several [TOFF\\_FALL](#) times producing the same VOUT slope and [TOFF\\_FALL](#) time even with different [TOFF\\_FALL](#) settings, or different [TOFF\\_FALL](#) times for the same [TOFF\\_FALL](#) setting and different (21h) [VOUT\\_COMMAND](#) voltages.

**图 7-59. (65h) TOFF\_FALL Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
TOFFF_EXP					TOFFF_MAN		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
TOFFF_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-70. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	TOFFF_EXP	RW	11110b	Linear format two's complement exponent. Exponent = -2, LSB = 0.25 ms
10:0	TOFFF_MAN	RW	NVM	Linear format two's complement mantissa

Attempts to write (65h) [TOFF\\_FALL](#) beyond the supported range will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3. (65h) [TOFF\\_FALL](#) supports values from 0.5 ms to 31.75 ms in 0.25-ms steps. Values less than 0.5 ms will be implemented as 0.5 ms.

## 7.6.54 (78h) STATUS\_BYTE

CMD Address	78h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	Yes
NVM Back-up:	No
Updates:	On-the-fly

The **STATUS\_BYTE** command returns one byte of information with a summary of the most critical faults, such as overvoltage, overcurrent, overtemperature, and so forth. The supported **STATUS\_BYTE** message content is described in the following table. The **STATUS\_BYTE** is equal the low byte of **STATUS\_WORD**. The conditions in the **STATUS\_BYTE** are summary information only. They are asserted to inform the host as to which other STATUS registers should be checked in the event of a fault. Setting and clearing of these bits must be done in the individual status registers. For example, Clearing VOUT\_OVF in **STATUS\_VOUT** also clears VOUT\_OV in **STATUS\_BYTE**.

**图 7-60. (78h) STATUS\_BYTE Register Map**

7	6	5	4	3	2	1	0
RW	R	R	R	R	R	R	R
BUSY	OFF	VOUT_OV	IOUT_OC	VIN_UV	TEMP	CML	NONE OF THE ABOVE

LEGEND: R/W = Read/Write; R = Read only

**表 7-71. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	BUSY	RW	0b	0b: A fault was NOT declared because the device was busy and unable to respond. 1b: A fault was declared because the device was busy and unable to respond.
6	OFF	R	0b	LIVE (unlatched) status bit 0b: The unit is enabled and converting power. 1b: The unit is NOT converting power for any reason including simply not being enabled.
5	VOUT_OV	R	0b	0b: An output overvoltage fault has NOT occurred. 1b: An output overvoltage fault has occurred.
4	IOUT_OC	R	0b	0b: An output overcurrent fault has NOT occurred. 1b: An output overcurrent fault has occurred.
3	VIN_UV	R	0b	0b: An input undervoltage fault has NOT occurred. 1b: An input undervoltage fault has occurred.
2	TEMP	R	0b	0b: A temperature fault/warning has NOT occurred. 1b: A temperature fault/warning has occurred, the host should check STATUS_TEMPERATURE for more information.
1	CML	R	0b	0b: A communication, memory, logic fault has NOT occurred. 1b: A communication, memory, logic fault has occurred, the host should check STATUS_CML for more information.
0	NONE OF THE ABOVE	R	0b	0b: A fault other than those listed above has NOT occurred. 1b: A fault other than those listed above has occurred. The host should check the STATUS_WORD for more information.

Writing 80h to STATUS\_BYTE will clear the BUSY bit, if set.

### 7.6.55 (79h) STATUS\_WORD

CMD Address	79h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	Unsigned Binary (2 bytes)
Phased:	Yes
NVM Back-up:	No
Updates:	On-the-fly

The **STATUS\_WORD** command returns two bytes of information with a summary of the most critical faults, such as overvoltage, overcurrent, overtemperature, and so forth. The low byte of the **STATUS\_WORD** is the same register as the **STATUS\_BYTE**. The supported **STATUS\_WORD** message content is described in the following table. The conditions in the **STATUS\_BYTE** are summary information only.

**图 7-61. (79h) STATUS\_WORD Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
VOUT	IOUT	INPUT	MFR	PGOOD	0	OTHER	0
7	6	5	4	3	2	1	0
RW	R	R	R	R	R	R	R
STATUS_BYTE							

LEGEND: R/W = Read/Write; R = Read only

**表 7-72. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15	VOUT	R	0b	0b: An output voltage related fault has NOT occurred. 1b: An output voltage fault has occurred. The host should check STATUS_VOUT for more information
14	IOUT	R	0b	0b: An output current related fault has NOT occurred. 1b: An output current fault has occurred. The host should check STATUS_IOUT for more information
13	INPUT	R	0b	0b: An input related fault has NOT occurred. 1b: An input fault has occurred. The host should check STATUS_INPUT for more information
12	MFR	R	0b	0b: A Manufacturer-defined fault has NOT occurred. 1b: A Manufacturer-defined fault has occurred. The host should check STATUS_MFR_SPECIFIC for more information.
11	PGOOD	R	0b	LIVE (unlatched) status bit. Should follow always the value of the PGOOD/RESET_B pin is asserted. 0b: The output voltage is within the regulation window. PGOOD pin is de-asserted. 1b: The output voltage is NOT within the regulation window. PGOOD pin is asserted.
10	Not Supported	R	0b	Not supported and always set to 0b
9	OTHER	R	0b	0b: An OTHER fault has not occurred. 1b: An OTHER fault has occurred, the host should check STATUS_OTHER for more information.

表 7-72. Register Field Descriptions (continued)

Bit	Field	Access	Reset	Description
8	Not Supported	R	0b	Not supported and always set to 0b.
7:0	STATUS_BYTE	RW	00h	Always equal to the STATUS_BYTE value.

All bits which can trigger SMBALERT have a corresponding bit in [SMBALERT\\_MASK](#).

Writing 0080h to STATUS\_WORD will clear the BUSY bit, if set. Writing 0180h to STATUS\_WORD will clear both the BUSY bit and UNKNOWN bit, if set.

## 7.6.56 (7Ah) STATUS\_VOUT

CMD Address	7Ah
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	No
Updates:	On-the-fly

The [STATUS\\_VOUT](#) command returns one data byte with contents as follows. All supported bits can be cleared either by [CLEAR\\_FAULTS](#), or individually by writing 1b to the (7Ah) [STATUS\\_VOUT](#) register in their position, per the PMBus 1.3.1 Part II specification section 10.2.4.

**图 7-62. (7Ah) STATUS\_VOUT Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	R	R
VOUT_OVF	VOUT_OVW	VOUT_UVW	VOUT_UVF	VOUT_MIN_MAX	TON_MAX	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-73. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	VOUT_OVF	RW	0b	0b: Latched flag indicating VOUT OV fault has NOT occurred. 1b: Latched flag indicating a VOUT OV fault has occurred. Note: the mask bits for VOUT_OVF will mask fixed, tracking, and pre-biased OVP. These can be individually controlled in SMBALERT_MASK_EXTENDED.
6	VOUT_OVW	RW	0b	0b: Latched flag indicating VOUT OV warn has NOT occurred. 1b: Latched flag indicating a VOUT OV warn has occurred. Note: the mask bits for VOUT_OVF will mask fixed and tracking Overvoltage Protection.
5	VOUT_UVW	RW	0b	0b: Latched flag indicating VOUT UV warn has NOT occurred. 1b: Latched flag indicating a VOUT UV warn has occurred.
4	VOUT_UVF	RW	0b	0b: Latched flag indicating VOUT UV fault has NOT occurred. 1b: Latched flag indicating a VOUT UV fault has occurred.
3	VOUT_MIN_MAX	RW	0b	0b: Latched flag indicating a VOUT_MIN_MAX has NOT occurred. 1b: Latched flag indicating a VOUT_MIN_MAX has occurred.
2	TON_MAX	RW	0b	0b: Latched flag indicating a TON_MAX has NOT occurred. 1b: Latched flag indicating a TON_MAX has occurred.
1:0	Not supported	R	00b	Not supported and always set to 00b.

All bits which can trigger SMBALERT have a corresponding bit in [SMBALERT\\_MASK](#).



## 7.6.57 (7Bh) STATUS\_IOUT

CMD Address	7Bh
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	Yes
NVM Back-up:	No
Updates:	On-the-fly

The [STATUS\\_IOUT](#) command returns one data byte with contents as follows. All supported bits can be cleared either by [CLEAR\\_FAULTS](#), or individually by writing 1b to the (7Bh) [STATUS\\_IOUT](#) register in their position, per the PMBus 1.3.1 Part II specification section 10.2.4.

**图 7-63. (7Bh) STATUS\_IOUT Register Map**

7	6	5	4	3	2	1	0
RW	R	RW	RW	R	R	R	R
IOUT_OCF	0	IOUT_OCW	IOUT_UCF	0	0	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-74. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	IOUT_OCF	RW	0b	0b: Latched flag indicating IOUT OC fault has NOT occurred. 1b: Latched flag indicating IOUT OC fault has occurred.
6	Not Supported	R	0b	Not supported and always set to 0b.
5	IOUT_OCW	RW	0b	0b: Latched flag indicating IOUT OC warn has NOT occurred. 1b: Latched flag indicating IOUT OC warn has occurred.
4	IOUT_UCF	RW	0b	0b: Latched flag indicating IOUT UC fault has NOT occurred. 1b: Latched flag indicating IOUT UC fault has occurred.
3:0	Not Supported	R	0000b	Not supported and always set to 0000b.

All bits which can trigger SMBALERT have a corresponding bit in [SMBALERT\\_MASK](#).

## 7.6.58 (7Ch) STATUS\_INPUT

CMD Address	7Ch
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	Yes
NVM Back-up:	No
Updates:	On-the-fly

The [STATUS\\_INPUT](#) command returns one data byte with contents as follows. All supported bits can be cleared either by [CLEAR\\_FAULTS](#), or individually by writing 1b to the (7Ch) [STATUS\\_INPUT](#) register in their position, per the PMBus 1.3.1 Part II specification section 10.2.4.

**图 7-64. (7Ch) STATUS\_INPUT Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	R	RW	R	R	R
VIN_OVF	VIN_OVW	VIN_UVW	0	LOW_VIN	0	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-75. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	VIN_OVF	RW	0b	0b: Latched flag indicating PVIN OV fault has NOT occurred. 1b: Latched flag indicating PVIN OV fault has occurred.
6	VIN_OVW	RW	0b	0b: Latched flag indicating PVIN OV warning has NOT occurred. 1b: Latched flag indicating PVIN OV warning has occurred.
5	VIN_UVW	RW	0b	0b: Latched flag indicating PVIN UV warn occurred. 1b: Latched flag indicating PVIN UV warn has occurred.
4	Not Supported	R	0b	Not supported and always set to 0b.
3	LOW_VIN	RW	0b	LIVE (unlatched) status bit. Showing the value of PVIN relative to VIN_ON and VIN_OFF. 0b: PVIN is ON. 1b: PVIN is OFF.
2:0	Not Supported	R	000b	Not supported and always set to 000b.

All bits which may trigger SMBALERT have a corresponding bit in [SMBALERT\\_MASK](#).

### LOW\_VIN vs VIN\_UVW

The LOW\_VIN bit is an information only (will not assert SMBALERT) flag which indicates that the device is not converting power because its PVIN voltage is less than [VIN\\_ON](#) or the VDD5 voltage is less than its UVLO to enable conversion. LOW\_VIN asserts initially at reset but does not assert SMBALERT.

The VIN\_UVW bit is a latched status bit, may assert SMBALERT if it is triggered to alert the host of an input voltage issue. VIN\_UVW IS masked until the first time the sensed input voltage exceeds the [VIN\\_ON](#) threshold.

## 7.6.59 (7Dh) STATUS\_TEMPERATURE

CMD Address	7Dh
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	Yes
NVM Back-up:	No
Updates:	On-the-fly

The [STATUS\\_TEMPERATURE](#) command returns one data byte with contents as follows. All supported bits can be cleared either by [CLEAR\\_FAULTS](#), or individually by writing 1b to the (7Dh) [STATUS\\_TEMPERATURE](#) register in their position, per the PMBus 1.3.1 Part II specification section 10.2.4.

**图 7-65. (7Dh) STATUS\_TEMPERATURE Register Map**

7	6	5	4	3	2	1	0
RW	RW	R	R	R	R	R	R
OTF	OTW	0	0	0	0	0	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-76. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	OTF	RW	0b	0b: Latched flag indicating OT fault has NOT occurred. 1b: Latched flag indicating OT fault has occurred.
6	OTW	RW	0b	0b: Latched flag indicating OT warn has NOT occurred. 1b: Latched flag indicating OT warn has occurred
5:0	Not supported	R	0d	Not supported and always set to 000000b.

All bits which can trigger SMBALERT have a corresponding bit in [SMBALERT\\_MASK](#).

## 7.6.60 (7Eh) STATUS\_CML

CMD Address	7Eh
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	Yes
NVM Back-up:	No
Updates:	On-the-fly

The [STATUS\\_CML](#) command returns one data byte with contents relating to communications, logic, and memory as follows. All supported bits can be cleared either by [CLEAR\\_FAULTS](#), or individually by writing 1b to the (7Eh) [STATUS\\_CML](#) register in their position, per the PMBus 1.3.1 Part II specification section 10.2.4.

**图 7-66. (7Eh) STATUS\_CML Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	R	RW	R
IVC	IVD	PEC	MEM	PROC_FLT	0	COMM	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-77. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	IVC	RW	0b	0b: Latched flag indicating invalid or unsupported command was NOT received. 1b: Latched flag indicating an invalid or unsupported command was received.
6	IVD	RW	0b	0b: Latched flag indicating invalid or unsupported data was NOT received. 1b: Latched flag indicating an invalid or unsupported data was received.
5	PEC	RW	0b	0b: Latched flag indicating NO packet error check has failed. 1b: Latched flag indicating a packet error check has failed.
4	MEM	RW	0b	0b: Latched flag indicating NO memory error was detected. 1b: Latched flag indicating a memory error was detected.
3	PROC_FLT	RW	0b	0b: Latched flag indicating NO logic core error was detected. 1b: Latched flag indicating a logic core error was detected.
2	Not supported	R	0b	Not supported and always set to 0b.
1	COMM	RW	0b	0b: Latched flag indicating NO communication error detected. 1b: Latched flag indicating communication error detected.
0	Not supported	R	0b	Not supported and always set to 0b.

All bits which can trigger SMBALERT have a corresponding bit in [SMBALERT\\_MASK](#).

Slaves will report a Back-Channel communications issue as a CML fault on their phase.

The corresponding bit [STATUS\\_BYTE](#) is an OR'ing of the supported bits in this command. When a fault condition in this command occurs, the corresponding bit in [STATUS\\_BYTE](#) is updated. Likewise, if this byte is individually cleared (for example, by a write of 1 to a latched condition), it should clear the corresponding bit in [STATUS\\_BYTE](#).

## 7.6.61 (7Fh) STATUS\_OTHER

CMD Address	7Fh
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	No
Updates:	On-the-fly

The **STATUS\_OTHER** command returns one data byte with information not specified in the other STATUS bytes.

**7-67. (7Fh) STATUS\_OTHER Register Map**

7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	RW
0	0	0	0	0	0	0	FIRST_ TO_ALERT

LEGEND: R/W = Read/Write; R = Read only

**表 7-78. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:1	Reserved	R	0h	Reserved
0	FIRST_TO_ALERT	RW	0b	0b: Latched flag indicating that this device was NOT the first to assert SMBALERT. This can mean either that the SMBALERT signal is not asserted (or has since been cleared), or that it is asserted, but this device was not the first on the bus to assert it. 1b: Latched flag indicating that this device was the first to assert SMBALERT.

The corresponding bit **STATUS\_BYTE** is an OR'ing of the supported bits in this command. When a fault condition in this command occurs, the corresponding bit in **STATUS\_BYTE** is updated. Likewise, if this byte is individually cleared (for example, by a write of 1 to a latched condition), it should clear the corresponding bit in **STATUS\_BYTE**.

## 7.6.62 (80h) STATUS\_MFR\_SPECIFIC

CMD Address	80h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	Yes
NVM Back-up:	No
Updates:	On-the-fly

The **STATUS\_MFR\_SPECIFIC** command returns one data byte with contents regard of communications, logic, and memory as follows. All supported bits may be cleared either by **CLEAR\_FAULTS**, or individually by writing 1b to the (80h) **STATUS\_MFR\_SPECIFIC** register in their position, per the PMBus 1.3.1 Part II specification section 10.2.4.

**图 7-68. (80h) STATUS\_MFR\_SPECIFIC Register Map**

7	6	5	4	3	2	1	0
RW	R	R	R	RW	RW	RW	R
POR	SELF	0	0	RESET	BCX	SYNC	0

LEGEND: R/W = Read/Write; R = Read only

**表 7-79. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	POR	RW	0b	0: No Power-On Reset Fault has been detected. 1: A Power-On Reset Fault has been detected. This bit should be set if: Power-On Self-Check of Internal Trim values, USER_STORE NVM check-sum, or Pin Detection reports an invalid result.
6	SELF	R	0b	LIVE (unlatched) status bit. Showing the status of the Power-On Self-Check. 0b: Power On Self-Check is complete. All expected BCX slaves have responded. 1b: Power-On Self-Check is in progress. One or more BCX slaves have not responded.
5:4	Not supported	R	00b	Not supported and always set to 00b.
3	RESET	RW	0b:	0b: A RESET_ VOUT event has NOT occurred. 1b: A RESET_ VOUT event has occurred.
2	BCX	RW	0b	0b: A BCX fault event has NOT occurred. 1b: A BCX fault event has occurred.
1	SYNC	RW	0b	0b: No SYNC fault has been detected. 1b: A SYNC fault has been detected.
0	Not supported	R	0b	Not supported and always set to 0b.

Per the PMBus Spec writing a 1 to any bit in a STATUS register shall clear that bit if it is set. All bits which may trigger SMBALERT have a corresponding bit in **SMBALERT\_MASK**.

### 7.6.63 (88h) READ\_VIN

CMD Address	88h
Write Transaction:	N/A
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	No
Update Rate:	1ms
Supported Range:	0 - 24 V

The [READ\\_VIN](#) command returns the output current in amperes.

**图 7-69. (88h) READ\_VIN Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
READ_VIN_EXP					READ_VIN_MAN		
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
READ_VIN_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-80. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	READ_VIN_EXP	RW	Input voltage	Linear format two's complement exponent
10:0	READ_VIN_MAN	RW	Input voltage	Linear format two's complement mantissa

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, the TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).
- Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

#### PHASE Behavior

When [PHASE](#) = FFh, [READ\\_VIN](#) returns the PVIN voltage of the master device.

When [PHASE](#) != FFh, [READ\\_VIN](#) returns the PVIN voltage of the device assigned to the current [PHASE](#).

## 7.6.64 (8Bh) READ\_VOUT

CMD Address	8Bh
Write Transaction:	N/A
Read Transaction:	Read Word
Format:	ULINEAR16 per <a href="#">VOUT_MODE</a> .
Phased:	Yes
NVM Back-up:	No
Update Rate:	1 ms
Supported Range	0 V to 6.0 V

The [READ\\_VOUT](#) command returns the actual, measured output voltage.

**图 7-70. (8Bh) READ\_VOUT Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
READ_VOUT							
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
READ_VOUT							

LEGEND: R/W = Read/Write; R = Read only

**表 7-81. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	READ_VOUT	RW	Current Status	Output voltage reading, per <a href="#">VOUT_MODE</a>

READ\_VOUT will report the voltage at the VOSNS pin with respect to AGND when a device is configured as a slave (GOSNS = BP1V5). In this configuration, VOUT\_SCALE\_LOOP is ignored and VOSNS must be externally scaled to maintain a voltage between 0 V and 0.75 V for proper reporting of the VOSNS voltage.

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, the TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).
- Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.



## 7.6.65 (8Ch) READ\_IOUT

CMD Address	8Ch
Write Transaction:	N/A
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	No
Update Rate:	1 ms
Supported Range:	-15 A to 90 A per Phase

The [READ\\_IOUT](#) command returns the output current in amperes.

**图 7-71. (8Ch) READ\_IOUT Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
READ_IOUT_EXP					READ_IOUT_MAN		
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
READ_IOUT_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-82. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	READ_IOUT_EXP	RW	Current Status	Linear format two's complement exponent
10:0	READ_IOUT_MAN	RW	Current Status	Linear format two's complement mantissa

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, the TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).
- Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### PHASE Behavior

When [PHASE](#) = FFh, [READ\\_IOUT](#) returns the total current for the stack of devices supporting a single output.

When [PHASE](#) != FFh, [READ\\_IOUT](#) returns the measured current of the device assigned to the current [PHASE](#).

## 7.6.66 (8Dh) READ\_TEMPERATURE\_1

CMD Address	8Dh
Write Transaction:	N/A
Read Transaction:	Read Word
Format:	SLINEAR11 per <a href="#">CAPABILITY</a>
Phased:	Yes
NVM Back-up:	No
Update Rate:	300 $\mu$ s
Supported Range:	-40°C to 175°C

The [READ\\_TEMPERATURE\\_1](#) command returns the maximum power stage temperature in degrees Celsius.

**图 7-72. (8Dh) READ\_TEMPERATURE\_1 Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
READ_T1_EXP					READ_T1_MAN		
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
READ_T1_MAN							

LEGEND: R/W = Read/Write; R = Read only

**表 7-83. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:11	READ_T1_EXP	RW	Current Status	Linear format two's complement exponent. LSB = 1°C
10:0	READ_T1_MAN	RW	Current Status	Linear format two's complement mantissa

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, the TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).
- Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

### PHASE Behavior

When [PHASE](#) = FFh, [READ\\_TEMPERATURE\\_1](#) returns the temperature of the hottest of device in the stack of devices supporting a single output.

When [PHASE](#) ! = FFh, [READ\\_TEMPERATURE\\_1](#) returns the measured temperature of the device assigned to the current [PHASE](#).

## 7.6.67 (98h) PMBUS\_REVISION

CMD Address	98h
Write Transaction:	N/A
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 byte)
Phased:	No
Max Transaction Time:	0.25 ms

The [PMBUS\\_REVISION](#) command reads the revision of the PMBus to which the device is compliant.

**图 7-73. (98h) PMBUS\_REVISION Register Map**

7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
PART_I				PART_II			

LEGEND: R/W = Read/Write; R = Read only

**表 7-84. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:4	PART_I	R	0011b	0011b: Compliant to PMBus Rev 1.3, Part 1
3:0	PART_II	R	0011b	0011b: Compliant to PMBus Rev 1.3, Part 2

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, the TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).
- Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

**7.6.68 (99h) MFR\_ID**

CMD Address	99h
Write Transaction:	Write Block
Read Transaction:	Read Block
Format:	Unsigned Binary (3 bytes)
Phased:	No
NVM Back-up:	EEPROM

The **MFR\_ID** command loads the unit with 3 bytes that contains the manufacturer's ID. This is typically done once at the time of manufacture.

**图 7-74. (99h) MFR\_ID Register Map**

23	22	21	20	19	18	17	16
RW	RW	RW	RW	RW	RW	RW	RW
MFR_ID							
15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
MFR_ID							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
MFR_ID							

LEGEND: R/W = Read/Write; R = Read only

**表 7-85. Register Field Descriptions**

Bit	Field	Access	Reset	Description
23:0	MFR_ID	RW	NVM	3 bytes of arbitrarily writable user-store NVM for manufacturer ID information.

## 7.6.69 (9Ah) MFR\_MODEL

CMD Address	9Ah
Write Transaction:	Write Block
Read Transaction:	Read Block
Format:	Unsigned Binary (3 bytes)
Phased:	No
NVM Back-up:	EEPROM

The [MFR\\_MODEL](#) command loads the unit with 3 bytes that contains the manufacturer's ID. This is typically done once at the time of manufacture.

**图 7-75. (9Ah) MFR\_MODEL Register Map**

23	22	21	20	19	18	17	16
RW	RW	RW	RW	RW	RW	RW	RW
MFR_MODEL							
15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
MFR_MODEL							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
MFR_MODEL							

LEGEND: R/W = Read/Write; R = Read only

**表 7-86. Register Field Descriptions**

Bit	Field	Access	Reset	Description
23:0	MFR_MODEL	RW	NVM	3 bytes of arbitrarily writable user-store NVM for manufacturer model information

### 7.6.70 (9Bh) MFR\_REVISION

CMD Address	9Bh
Write Transaction:	Write Block
Read Transaction:	Read Block
Format:	Unsigned Binary (3 bytes)
Phased:	No
NVM Back-up:	EEPROM

The **MFR\_REVISION** command loads the unit with 3 bytes that contains the power supply manufacturer's revision number. This is typically done once at the time of manufacture.

**图 7-76. (9Bh) MFR\_REVISION Register Map**

23	22	21	20	19	18	17	16
RW	RW	RW	RW	RW	RW	RW	RW
MFR_REV							
15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
MFR_REV							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
MFR_REV							

LEGEND: R/W = Read/Write; R = Read only

**表 7-87. Register Field Descriptions**

Bit	Field	Access	Reset	Description
23:0	MFR_REV	RW	NVM	3 bytes of arbitrarily writable user-store NVM for manufacturer revision information

## 7.6.71 (9Eh) MFR\_SERIAL

CMD Address	9Eh
Write Transaction:	Write Block
Read Transaction:	Read Block
Format:	Unsigned Binary (3 bytes)
Phased:	No
NVM Back-up:	EEPROM

The [MFR\\_SERIAL](#) command loads the unit with 3 bytes that contains the power supply manufacturer's serial number. This is typically done once at the time of manufacture.

**图 7-77. (9Eh) MFR\_SERIAL Register Map**

23	22	21	20	19	18	17	16
RW	RW	RW	RW	RW	RW	RW	RW
MFR_SERIAL							
15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
MFR_SERIAL							
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
MFR_SERIAL							

LEGEND: R/W = Read/Write; R = Read only

**表 7-88. Register Field Descriptions**

Bit	Field	Access	Reset	Description
23:00	MFR_SERIAL	RW	NVM	Arbitrary 3-byte Serial Number assigned by manufacturer

Note: Because the value for [MFR\\_SERIAL](#) is included in the NVM memory store used to calculate the [NVM\\_CHECKSUM](#), assigning a unique [MFR\\_SERIAL](#) value will also result in a unique [NVM\\_CHECKSUM](#) value.

## 7.6.72 (ADh) IC\_DEVICE\_ID

CMD Address	ADh
Write Transaction:	N/A
Read Transaction:	Read Block
Format:	Unsigned Binary (6 bytes)
Phased:	No

The [IC\\_DEVICE\\_ID](#) command is used to either set or read the type or part number of an IC embedded within a PMBus that is used for the PMBus interface.

**图 7-78. (ADh) IC\_DEVICE\_ID Register Map**

47	46	45	44	43	42	41	40
R	R	R	R	R	R	R	R
IC_DEVICE_ID[47:40]							
39	38	37	36	35	34	33	32
R	R	R	R	R	R	R	R
IC_DEVICE_ID[39:32]							
31	30	29	28	27	26	25	24
R	R	R	R	R	R	R	R
IC_DEVICE_ID[31:24]							
23	22	21	20	19	18	17	16
R	R	R	R	R	R	R	R
IC_DEVICE_ID[23:16]							
15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
IC_DEVICE_ID[15:8]							
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
IC_DEVICE_ID[7:0]							

LEGEND: R/W = Read/Write; R = Read only

**表 7-89. Register Field Descriptions**

Bit	Field	Access	Reset	Description
47:0	IC_DEVICE_ID	R	See text.	See the table below.

**表 7-90. IC\_DEVICE\_ID Values**

Byte Number (Bit Indices)	Byte 0 (7:0)	Byte 1 (15:8)	Byte 2 (23:16)	Byte 3 (31:24)	Byte 4 (39:32)	Byte 5 (47:40)
TPS546B24A	54h	49h	54h	6Dh	24h	41h

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).
- Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.



### 7.6.73 (AEh) IC\_DEVICE\_REV

CMD Address	AEh
Write Transaction:	N/A
Read Transaction:	Read Block
Format:	Unsigned Binary (2 bytes)
Phased:	No

The [IC\\_DEVICE\\_REV](#) command is used to either set or read the revision of the IC.

**Figure 7-79. (AEh) IC\_DEVICE\_REV Register Field Descriptions**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
MAJOR_REV				MINOR_REV			
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
SUB_MINOR_REV							

LEGEND: R/W = Read/Write; R = Read only

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, the TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).

Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

**7.6.74 (B1h) USER\_DATA\_01 (COMPENSATION\_CONFIG)**

CMD Address	B1h
Write Transaction:	Write Block
Read Transaction:	Read Block
Format:	Unsigned Binary (5 bytes)
Phased:	No
NVM Back-up:	EEPROM or Pin Detection
Updates:	Conversion Disable: on-the-fly. Conversion Enable: hardware update blocked. To update hardware after write while enabled, store to NVM with (15h) STORE_USER_ALL and (16h) RESTORE_USER_ALL or cycle AVIN below UVLO.

Configure the control loop compensation.

**图 7-80. (B1h) USER\_DATA\_01 (COMPENSATION\_CONFIG) Register Map**

39	38	37	36	35	34	33	32
RW	RW	RW	RW	RW	RW	RW	RW
SEL_CZI[1:0]		SEL_CPI[4:0]				SEL_CZI_MUL	
31	30	29	28	27	26	25	24
R	RW	RW	RW	RW	RW	RW	RW
SEL_RVI[5:0]						SEL_CZI[3:2]	
23	22	21	20	19	18	17	16
RW	RW	RW	RW	RW	RW	RW	RW
SEL_CZV[1:0]		SEL_CPV[4:0]				0	
15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
SEL_RVV[5:0]						SEL_CZV[3:2]	
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
0	0	SEL_GMV[1:0]		0	0	SEL_GMI[1:0]	

LEGEND: R/W = Read/Write; R = Read only

**表 7-91. Register Field Descriptions**

Bit	Field	Access	Reset	Description
25:24,39:38	SEL_CZI[3:0]	RW	NVM	Selects the value of current loop integrating capacitor. $CZI = 6.66\text{pF} \times CZI\_MUL \times 2^{SEL\_GMI[1:0]} \times SEL\_CZI[3:0]$
37:33	SEL_CPI[4:0]	RW	NVM	Selects the value of current loop filter capacitor. $CPI = 3.2\text{pF} \times SEL\_CPI[4:0]$
32	SEL_CZI_MUL	RW	NVM	Selects the value of current loop integrating capacitor multiplier. 0b: CZI_MUL = 1 1b: CZI_MUL = 2
31:26	SEL_RVI[5:0]	RW	NVM	Selects the value of current loop mid-band gain resistor. $RVI = 5\text{k}\Omega \times SEL\_RVI[5:0]$
9:8, 23:22	SEL_CZV[3:0]	RW	NVM	Selects the value of voltage loop integrating capacitor. $CZV = 125\text{pF} \times 2^{SEL\_GMV[1:0]} \times SEL\_CZV[3:0]$
21:17	SEL_CPV[4:0]	RW	NVM	Selects the value of voltage loop filter capacitor. $CPV = 6.25\text{pF} \times SEL\_CPV[4:0]$

**表 7-91. Register Field Descriptions (continued)**

Bit	Field	Access	Reset	Description
16	Reserved	RW	NVM	Reserved, set to 0b
15:10	SEL_RVV[5:0]	RW	NVM	Selects the value of voltage loop mid-band gain resistor. $RVV = 5k\Omega \times SEL\_RVV[5:0]$
7:6	Reserved	RW	NVM	Reserved, set to 00b
5:4	SEL_GMV[1:0]	RW	NVM	Selects the value of voltage error transconductance. $GMV = 25\mu S \times 2^{SEL\_GMV[1:0]}$
3:2	Reserved	RW	NVM	Reserved, set to 00b
1:0	SEL_GMI[1:0]	RW	NVM	Selects the value of current error transconductance. $GMI = 25\mu S \times 2^{SEL\_GMI[1:0]}$

(B1h) [USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#) can be written to while output conversion is enabled, but updating those values to hardware will be blocked. To update the value used by the control loop:

- Disable conversion, then write to (B1h) [USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#).
- Write to (B1h) [USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#) while conversion is enabled, store PMBus values to NVM using (15h) [STORE\\_USER\\_ALL](#), clear the (B1h) [USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#) bit in (EEh) [MFR\\_SPECIFIC\\_30 \(PIN\\_DETECT\\_OVERRIDE\)](#), then cycle AVIN or use the (16h) [RESTORE\\_USER\\_ALL](#) command.

Due to the complexity of translating the 5-byte HEX value of (B1h) [USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#) into analog compensation values, users are recommended to use the tools available on the [TPS546B24A product folder](#) such as the [TPS546x24A Compensation and Pin-Strap Resistor Calculator](#) design tool.

### 7.6.75 (B5h) USER\_DATA\_05 (POWER\_STAGE\_CONFIG)

CMD Address	B5h
Write Transaction:	Write Block (per PMBus Spec, even though 1 data byte)
Read Transaction:	Read Block (per PMBus Spec, even though 1 data byte)
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-the-fly
Max Transaction Time:	1.0 ms
Max Action Delay:	1.0 ms (not time critical)

POWER\_STAGE\_CONFIG allows the user to adjust the VDD5 regulator voltage.

**图 7-81. (B5h) USER\_DATA\_05 (POWER\_STAGE\_CONFIG) Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	R	R	R	R
SEL_VDD5				Reserved			

LEGEND: R/W = Read/Write; R = Read only

**表 7-92. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:4	SEL_VDD5	RW	NVM	3h: VDD5 = 3.9 V (Not Recommended for Production) 4h: VDD5 = 4.1 V 5h: VDD5 = 4.3 V 6h: VDD5 = 4.5 V 7h: VDD5 = 4.7 V 8h: VDD5 = 4.9 V 9h: VDD5 = 5.1 V Ah: VDD5 = 5.3 V Other: Invalid
3:0	Reserved	R	0000b	Reserved. Set to 0000b.

Setting 30h is not recommended for production use unless an external VDD5 voltage is provided because the 3.9-V LDO setting can result in a VDD5 voltage less than the VDD5 undervoltage lockout required to enable conversion and can result in the TPS546B24A device being unable to enable conversion without an external VDD5 voltage.

### 7.6.76 (D0h) MFR\_SPECIFIC\_00 (TELEMETRY\_CONFIG)

CMD Address	D0h
Write Transaction:	Write Block
Read Transaction:	Read Block
Format:	Unsigned Binary (6 bytes)
Phased:	No
NVM Back-up:	EEPROM
Updates:	On-The-Fly

Configure the priority and averaging for each channel of the internal telemetry system.

The internal telemetry system shares a single ADC across each measurement. The priority setting allows the user to adjust the relative rate of measurement of each telemetry value. The ADC will first measure each value with a priority A value. With each pass through all priority A measurements, one priority B measurement will be taken. With each pass through all priority B measurements, one priority C measurement will be taken.

Example: If output voltage has priority A and output current has priority B, and temperature has priority C, the telemetry sequence will be VOUT IOUT VOUT TEMPERATURE VOUT IOUT VOUT TEMPERATURE.

**7-82. (D0h) MFR\_SPECIFIC\_00 (TELEMETRY\_CONFIG) Register Map**

47	46	45	44	43	42	41	40
RW	RW	RW	RW	RW	RW	RW	RW
Reserved priority		Reserved			Reserved averaging		
39	38	37	36	35	34	33	32
RW	RW	RW	RW	RW	RW	RW	RW
Reserved priority		Reserved			Reserved averaging		
31	30	29	28	27	26	25	24
R	RW	RW	RW	RW	RW	RW	RW
RD_VI_PRI		Reserved			RD_VI_AVG		
23	22	21	20	19	18	17	16
RW	RW	RW	RW	RW	RW	RW	RW
RD_TMP_PRI		Reserved			RD_TMP_AVG		
15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
RD_IO_PRI		Reserved			RD_IO_AVG		
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
RD_VO_PRI		Reserved			RD_VO_AVG		

LEGEND: R/W = Read/Write; R = Read only

**表 7-93. Register Field Descriptions**

Bit	Field	Access	Reset	Description
47:40	Not used	R	00h	Reserved. Set values to 00h.
39:32	Not used	RW	NVM	Reserved. Set values to 03h.

**表 7-93. Register Field Descriptions (continued)**

Bit	Field	Access	Reset	Description
31:30	RD_VI_PRI	RW	NVM	00b: Assign priority A to input voltage telemetry. 01b: Assign priority B to input voltage telemetry. 10b: Assign priority C to input voltage telemetry. 11b: Disable input voltage telemetry.
31:24	RD_VI_AVG	RW	NVM	0d - 5d: READ_VIN Rolling average of 2 <sup>N</sup> samples 6d-7d: Invalid
23:22	RD_TMP_P RI	RW	NVM	00b: Assign priority A to temperature telemetry. 01b: Assign priority B to temperature telemetry. 10b: Assign priority C to temperature telemetry. 11b: Invalid
21:19	Reserved	RW	NVM	Reserved. Set to 000b.
18:16	RD_TMP_A VG	RW	NVM	0d - 5d: READ_TEMPERATURE_1 Rolling average of 2 <sup>N</sup> samples 6d-7d: Invalid
15:14	RD_IO_PRI	RW	NVM	00b: Assign priority A to output current telemetry. 01b: Assign priority B to output current telemetry. 10b: Assign priority C to output current telemetry. 11b: Disable output current telemetry.
13:11	Reserved	RW	NVM	Reserved. Set to 000b.
10:8	RD_IO_AVG	RW	NVM	0d - 5d: READ_IOUT Rolling average of 2 <sup>N</sup> samples 6d-7d: Invalid
7:6	RD_VO_PRI	RW	NVM	00b: Assign priority A to output voltage telemetry. 01b: Assign priority B to output voltage telemetry. 10b: Assign priority C to output voltage telemetry. 11b: Disable output voltage telemetry.
5:3	Reserved	RW	NVM	Reserved. Set to 000b.
2:0	RD_VO_AV G	RW	NVM	0d - 5d: READ_VOUT Rolling average of 2 <sup>N</sup> samples 6d-7d: Invalid

Disabling any telemetry value will force the associated READ PMBus command to report 0000h.

Because temperature telemetry is used for Overtemperature Protection, temperature telemetry cannot be disabled.

## 7.6.77 (DAh) MFR\_SPECIFIC\_10 (READ\_ALL)

CMD Address	DAh
Write Transaction:	NA
Read Transaction:	Read Block
Format:	Unsigned Binary (14 bytes)
Phased:	No
NVM Back-up:	No

READ\_ALL provides for a 14-byte BLOCK read of [STATUS\\_WORD](#) and telemetry values to improve bus utilization for polling by combining multiple READ functions into a single command, eliminating the need for multiple address and command code bytes.

**7-83. (DAh) MFR\_SPECIFIC\_10 (READ\_ALL) Register Map**

111	110	109	108	107	106	105	104
R	R	R	R	R	R	R	R
Not Supported = 00h							
103	102	101	100	99	98	97	96
R	R	R	R	R	R	R	R
Not Supported = 00h							
95	94	93	92	91	90	89	88
R	R	R	R	R	R	R	R
Not Supported = 00h							
87	86	85	84	83	82	81	80
R	R	R	R	R	R	R	R
Not Supported = 00h							
79	78	77	76	75	74	73	72
R	R	R	R	R	R	R	R
READ_VIN (MSB)							
71	70	69	68	67	66	65	64
R	R	R	R	R	R	R	R
READ_VIN (LSB)							
63	62	61	60	59	58	57	56
R	R	R	R	R	R	R	R
READ_TEMPERATURE1 (MSB)							
55	54	53	52	51	50	49	48
R	R	R	R	R	R	R	R
READ_TEMPERATURE1 (LSB)							
47	46	45	44	43	42	41	40
R	R	R	R	R	R	R	R
READ_IOUT (MSB)							
39	38	37	36	35	34	33	32
R	R	R	R	R	R	R	R
READ_IOUT (LSB)							
31	30	29	28	27	26	25	24

R	R	R	R	R	R	R	R
READ_VOUT (MSB)							
23	22	21	20	19	18	17	16
R	R	R	R	R	R	R	R
READ_VOUT (LSB)							
15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
STATUS_WORD (High Byte)							
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
STATUS_BYTE							

LEGEND: R/W = Read/Write; R = Read only

**表 7-94. Register Field Descriptions**

Bit	Field	Access	Reset	Description
111:96	READ_DUTY_CYCLE	R	0000h	Not supported = 0000h
95:80	READ_IIN	R	0000h	Not supported = 0000h
79:64	READ_VIN	R	0000h	READ_VIN (Linear Format)
63:48	READ_TEMPERATURE1	R	0000h	READ_TEMPERATURE1 (Linear Format)
47:32	READ_IOUT	R	0000h	READ_IOUT (Linear Format)
31:16	READ_VOUT	R	0000h	READ_VOUT (ULinear16 Format, Per VOUT_MODE)
15:0	STATUS_WORD	R	0000h	STATUS_WORD

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, the TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).

Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.



## 7.6.78 (DBh) MFR\_SPECIFIC\_11 (STATUS\_ALL)

CMD Address	DBh
Write Transaction:	NA
Read Transaction:	Read Block
Format:	Unsigned Binary (7 bytes)
Phased:	No
NVM Back-up:	No

STATUS\_ALL provides for a 7-byte block of STATUS command codes. This can reduce bus utilization to read multiple faults.

**图 7-84. (DBh) MFR\_SPECIFIC\_11 (STATUS\_ALL) Register Map**

55	54	53	52	51	50	49	48
R	R	R	R	R	R	R	R
STATUS_MFR							
47	46	45	44	43	42	41	40
R	R	R	R	R	R	R	R
STATUS_OTHER							
39	38	37	36	35	34	33	32
R	R	R	R	R	R	R	R
STATUS_CML							
31	30	29	28	27	26	25	24
R	R	R	R	R	R	R	R
STATUS_TEMPERATURE							
23	22	21	20	19	18	17	16
R	R	R	R	R	R	R	R
STATUS_INPUT							
15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
STATUS_IOUT							
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
STATUS_VOUT							

LEGEND: R/W = Read/Write; R = Read only

**表 7-95. Register Field Descriptions**

Bit	Field	Access	Reset	Description
55:48	STATUS_MFR	R	Current Status	STATUS_MFR
47:40	STATUS_OTHER	R	Current Status	STATUS_OTHER
39:32	STATUS_CML	R	Current Status	STATUS_CML

**表 7-95. Register Field Descriptions (continued)**

Bit	Field	Access	Reset	Description
31:24	STATUS_ TEMPERAT URE	R	Current Status	STATUS_ TEMPERATURE
23:16	STATUS_ INPUT	R	Current Status	STATUS_ INPUT
15:8	STATUS_ IOUT	R	Current Status	STATUS_ IOUT
7:0	STATUS_ VOUT	R	Current Status	STATUS_ VOUT

Attempts to write read-only commands cause the CML: invalid command (IVC) fault condition, the TPS546B24A responds as follows:

- Set the CML bit in [STATUS\\_BYTE](#).
- Set the CML\_IVC (bit 7) bit in [STATUS\\_CML](#).
- Notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

Writes to STATUS\_ALL do not clear asserted status bits.

## 7.6.79 (DCh) MFR\_SPECIFIC\_12 (STATUS\_PHASE)

CMD Address	DCh
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	Unsigned Binary (2 bytes)
Phased:	Yes
Updates:	On-the-fly
NVM Back-up:	No

When **PHASE** = FFh, reads to this command return a data word detailing which phases have experienced fault conditions. When **PHASE** != FFh, reads to this command return a data word with a 1 in the bit 0 position if the active phase is reporting any status bit. Bits corresponding to unused (unassigned or disabled) phase numbers are always equal to 0b.

**图 7-85. (DCh) MFR\_SPECIFIC\_12 (STATUS\_PHASE)**

15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
R	R	R	R	RW	RW	RW	RW	RW	RW	RW	RW	RW	RW	RW	RW
0	0	0	0	0	0	0	0	0	0	0	0	PH3	PH2	PH1	PH0

LEGEND: R/W = Read/Write; R = Read only

**表 7-96. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:4	Reserved	R	0b	Reserved
3	PH3	RW	0b	0b: The TPS546B24A assigned to <b>PHASE</b> = 3d has NOT experienced a fault. 1b: The TPS546B24A assigned to <b>PHASE</b> = 3d has experienced a fault. Set <b>PHASE</b> = 3d, and read STATUS_WORD or STATUS_ALL for more information.
2	PH2	RW	0b	0b: The TPS546B24A assigned to <b>PHASE</b> = 2d has NOT experienced a fault. 1b: The TPS546B24A assigned to <b>PHASE</b> = 2d has experienced a fault. Set <b>PHASE</b> = 2d, and read STATUS_WORD or STATUS_ALL for more information.
1	PH1	RW	0b	0b: The TPS546B24A assigned to <b>PHASE</b> = 1d has NOT experienced a fault. 1b: The TPS546B24A assigned to <b>PHASE</b> = 1d has experienced a fault. Set <b>PHASE</b> = 1d, and read STATUS_WORD or STATUS_ALL for more information.
0	PH0	RW	0b	0b: The TPS546B24A assigned to <b>PHASE</b> = 0d has NOT experienced a fault. 1b: The TPS546B24A assigned to <b>PHASE</b> = 0d has experienced a fault. Set <b>PHASE</b> = 0d, and read STATUS_WORD or STATUS_ALL for more information.

**7.6.80 (E3h) MFR\_SPECIFIC\_19 (PGOOD\_CONFIG)**

CMD Address	E3h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format	Unsigned Word
Phased:	No
NVM Backup:	EEPROM or Pin Detect
Updates:	Conversion Disable: see below. Conversion Enable: Read-Only

**7-86. (E3h) MFR\_SPECIFIC\_19 (PGOOD\_CONFIG) Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
PGOOD_OFF_DELAY[3:0]				PGOOD_ON_DELAY[3:0]			
7	6	5	4	3	2	1	0
R	R	R	R	RW	RW	RW	RW
pgmOVF	pgmOVW	pgmUVW	pgmUVF	pgmOCW	pgmOCF	pgmINOVW	pgmINOVF

LEGEND: R/W = Read/Write; R = Read only

**表 7-97. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:12	PGOOD_OF F_DELAY[3: 0]	RW	NVM	Sets Delay from the detection of an unmasked Fault or Warning event to the assertion of PGOOD low. 0d: Delay PGOOD high-low 1 PWM CLK 1d-15d: Delay PGOOD high-low $2^N+1$ PWM CLKs
11:8	PGOOD_O N_DELAY[3: 0]	RW	NVM	Sets Delay from the detection of no unmasked Fault or Warning events to the release of PGOOD low. 0d: Delay PGOOD low-high to 1 PWM CLK 1d-15d: Delay PGOOD low-high $2^N+1$ PWM CLKs
7	pgmOVF	RW	NVM	0b: Output Overvoltage Fault can assert PGOOD low. 1b: Output Overvoltage Fault cannot assert PGOOD low.
6	pgmOVW	RW	NVM	0b: Output Overvoltage Warning can assert PGOOD low. 1b: Output Overvoltage Warning cannot assert PGOOD low.
5	pgmUVF	RW	NVM	0b: Output Undervoltage Fault can assert PGOOD low. 1b: Output Undervoltage Fault cannot assert PGOOD low.
4	pgmUVW	RW	NVM	0b: Output Undervoltage Warning can assert PGOOD low. 1b: Output Undervoltage Warning cannot assert PGOOD low.
3	pgmOCW	RW	NVM	0b: Output Overcurrent Warning can assert PGOOD low. 1b: Output Overcurrent Warning cannot assert PGOOD low.
2	pgmOCF	RW	NVM	0b: Output Overcurrent Fault can assert PGOOD low. 1b: Output Overcurrent Fault cannot assert PGOOD low.
1	pgmINOVW	RW	NVM	0b: Input Overvoltage Warning can assert PGOOD low. 1b: Input Overvoltage Warning cannot assert PGOOD low.
0	pgmINOVF	RW	NVM	0b: Input Overvoltage Fault can assert PGOOD low. 1b: Input Overvoltage Fault cannot assert PGOOD low.

Power Good indicates the status of the converter. (E3h) MFR\_SPECIFIC\_19 (PGOOD\_CONFIG) provides control of the delays asserting and releasing Power Good. Power Good is always low while conversion is

disabled, during (60h) [TON\\_DELAY](#), (61h) [TON\\_RISE](#), (65h) [TOFF\\_FALL](#), and during a fault shut-down or hiccup delay. PGOOD\_OFF\_DELAY is bypassed during (65h) [TOFF\\_FALL](#) and during a fault shut-down or hiccup. Power Good will still be asserted on an unmasked fault event unless that fault's RESPONSE command is configured to Continue Operating without Interruption.

PGOOD\_OFF\_DELAY and PGOOD\_ON\_DELAY are sensed and timed independently from each other. If PGOOD\_ON\_DELAY is less than PGOOD\_OFF\_DELAY and an unmasked fault or warning event lasts less than PGOOD\_OFF\_DELAY - PGOOD\_ON\_DELAY, Power Good will not be asserted low during the fault or warning events.

**7.6.81 (E4h) MFR\_SPECIFIC\_20 (SYNC\_CONFIG)**

CMD Address	E4h
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary
Phased:	No
NVM Back-up:	EEPROM or Pin Detect
Updates:	On-the-fly

**图 7-87. (E4h) MFR\_SPECIFIC\_20 (SYNC\_CONFIG) Register Map**

7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
SYNC_DIR		SYNC_EDGE	10000b				

LEGEND: R/W = Read/Write; R = Read only

**表 7-98. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7:6	SYNC_DIR	RW	NVM	00b: SYNC disabled 01b: Enable SYNC OUT. 10b: Enable SYNC IN. 11b: Enable Auto Detect SYNC
5	SYNC_EDGE	RW	NVM	0b: Synchronize to falling edge of SYNC. 1b: Synchronize to rising edge of SYNC.
4:0	Not supported	RW	10000b	Not supported. Set to 10000b.

Attempts to write (E4h) MFR\_SPECIFIC\_E4 (SYNC\_CONFIG) to any value outside those specified as valid will be considered invalid/unsupported data and cause the TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

When SYNC\_DIR = 11b - Enable Auto Detect, the TPS546B24A will select SYNC\_IN or SYNC\_OUT based on the state of the SYNC pin when the Enable Condition, as defined by ON\_OFF\_CONFIG is met. If the SYNC\_PIN is >2 V or switching faster than 75% of FRQUENCY\_SWITCH, SYNC\_IN shall be enabled. If the SYNC\_PIN is less than 0.8 V and not switching, SYNC\_OUT will be selected.

Slave devices in a multi-phase stack will always be configured for SYNC\_IN and will declare a SYNC\_FAULT in (80h) STATUS\_MFR\_SPECIFIC if enabled before a SYNC signal is present, or if SYNC is lost before being disabled. To prevent such false SYNC\_FAULTs from occurring, it is recommended that multi-phase stacks configure select SYNC\_OUT in (E4h) MFR\_SPECIFIC\_20 (SYNC\_CONFIG) if not using an external synchronization signal.

Changing SYNC\_DIR from SYNC\_IN to SYNC\_OUT while enabled and operating at the lower limit of the SYNC\_IN function (70% of nominal switching frequency) will result in the switching frequency remaining at the lower limit of SYNC\_IN until the output is disabled and enabled.

Changing SYNC\_DIR from SYNC\_IN to SYNC\_OUT on a multi-phase stack while conversion is enabled but prevented due to a SYNC\_FAULT will result in the internal oscillator operating at 70% of its nominal frequency. Since this is out-side of the ensured SYNC\_IN range of the slave device, this could result in unsynchronized operation.

## 7.6.82 (ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG)

CMD Address	ECh
Write Transaction:	Write Word
Read Transaction:	Read Word
Format	Unsigned Word
Phased:	No
NVM Backup:	EEPROM or Pin Detect
Updates:	Conversion Disable: see below. Conversion Enable: Read-Only

**7-88. (ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
Reserved 0000h							
7	6	5	4	3	2	1	0
R	R	R	R	RW	RW	RW	RW
BCX_START				BCX_STOP			

LEGEND: R/W = Read/Write; R = Read only

**表 7-99. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:8	Not supported	R	0000h	Reserved. Equal 0000h.
7:4	BCX_START	R	0000b	BCX_Address for Stack Master. Equal to 0000b.
3:0	BCX_STOP	RW	NVM	0000b: Stand Alone, Single-phase 0001b: One-Slave, 2-phase 0010b: Two Slaves, 3-phase 0011b: Three Slaves, 4-phase Other: Not supported / Invalid

Attempts to write (ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) to any value outside those specified as valid, will be considered invalid/unsupported data and cause TPS546B24A to respond by flagging the appropriate status bits and notifying the host according to the PMBus 1.3.1 Part II specification section 10.9.3.

(ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) controls the operation of the BCX\_CLK and BCX\_DAT pins. If the TPS546B24A powers up with (ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) equal to 0000h (Stand Alone) the BCX\_CLK and BCX\_DAT functionality is disabled. Changing (ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) to a Multi-phase configuration will not enable BCX communication until the next power-up. To program slave devices connected to a Master device that was powered up with (ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) = 0000h, program (EEh) MFR\_SPECIFIC\_30 (PIN\_DETECT\_OVERRIDE) to default (ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) to NVM by setting bit 12 = 0b, (15h) STORE\_USER\_ALL and cycle AVIN power below its UVLO prior to programing other commands in order to enable BCX communication and allow the Master device to relay commands to the slave devices.

(ECh) MFR\_SPECIFIC\_28 (STACK\_CONFIG) can be changed from 0001h to 0003h to 0000h - 0003h live without requiring an AVIN power cycle since the BCX\_CLK and BCX\_DAT function is enabled at power up.

**7.6.83 (EDh) MFR\_SPECIFIC\_29 (MISC\_OPTIONS)**

CMD Address	EDh
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	Unsigned Binary (2 bytes)
Phased:	No
NVM Backup:	EEPROM
Updates:	on-the-fly

MFR\_SPECIFIC\_29 is used to configure miscellaneous settings.

**7-89. (EDh) MFR\_SPECIFIC\_29 (MISC\_OPTIONS) Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
PEC	RESET_CNT	RESET_FLT	RESET#	Reserved	Reserved	Reserved	Reserved
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
Reserved	Reserved	Reserved	Reserved	PULLUP#	FLT_CNT	ADC_RES	

LEGEND: R/W = Read/Write; R = Read only

**表 7-100. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15	PEC	RW	NVM	0b: PEC Optional. Transactions received without PEC byte will be processed. 1b: PEC Required. Transactions received without PEC byte will be rejected as COMS_FAIL in (7Eh) STATUS_CML.
14	RESET_CNT	RW	NVM	0b: VOUT_COMMAND will be unchanged following a shutdown. 1b: VOUT_COMMAND will be changed to VBOOT on a Control or OPERATION shutdown.
13	RESET_FLT	RW	NVM	0b: VOUT_COMMAND will be unchanged following a Fault Restart. 1b: VOUT_COMMAND will be changed to VBOOT on Restart from a Fault when Fault Retry is set to Retry after Fault.
12	RESET#	RW	NVM	Sets the function of the PGD/RESET_B pin. 0b: PGD/RESET_B functions as PGOOD and internal pullup is disabled. 1b: PGD/RESET_B functions as RESET# and internal pullup is set by bit 3 PULLUP#.
11:3	Reserved	RW	NVM	Reserved. Must be 00000000b
3	PULLUP#	RW	NVM	Sets the pullup of the PGD/RESET_B pin when RESET# = 1b. 0b: Internal pullup of PGD/RESET_B pin enabled when RESET# = 1b. 1b: Internal pullup of PGD/RESET_B pin disabled when RESET# = 1b.
2	FLT_CNT	RW	NVM	0b: Fault Counter counts down one cycle on PWM cycle without fault 1b: Fault Counter resets counter to 0 on PWM cycle without fault
1:0	ADC_RES	RW	NVM	ADC Resolution Control 00b: Set ADC Resolution to 12-bit 01b: Set ADC Resolution to 10-bit 10b: Set ADC Resolution to 8-bit 11b: Set ADC Resolution to 6-bit



### 7.6.84 (EEh) MFR\_SPECIFIC\_30 (PIN\_DETECT\_OVERRIDE)

CMD Address	EEh
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	Unsigned Binary (1 byte)
Phased:	No
NVM Backup:	EEPROM
Updates:	on-the-fly (pin detection occurs on POR only).

PMBUS specified that NVM (Default or User) stored values will overwrite Pin Programmed Values. Setting a “1” in each bit of this register will prevent DEFAULT or USER STORE values from overwriting the Pin-Programmed Value associated that bit.

**7-90. (EEh) MFR\_SPECIFIC\_30 (PIN\_DETECT\_OVERRIDE) Register Map**

15	14	13	12	11	10	9	8
RW	RW	RW	RW	RW	RW	RW	RW
Reserved			STACK_CONFIG	SYNC_CONFIG	Reserved	COMP_CONFIG	ADDRESS
7	6	5	4	3	2	1	0
RW	RW	RW	RW	RW	RW	RW	RW
Reserved		INTERLEAVE	Reserved	TON_RISE	IOUT_OC	FREQ	VOUT

LEGEND: R/W = Read/Write; R = Read only

**表 7-101. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:13	Reserved	RW	NVM	Not used and set to 000b.
12	STACK_CONFIG	RW	NVM	0b: At power-up or RESTORE, STACK_CONFIG will be reset to NVM value. 1b: At power-up or RESTORE, STACK_CONFIG will be reset to pin-detected value.
11	SYNC_CONFIG	RW	NVM	0b: At power-up or RESTORE, SYNC_CONFIG will be reset to NVM value. 1b: At power-up or RESTORE, SYNC_CONFIG will be reset to pin-detected value.
10	Reserved	RW	NVM	Not used and set to 0b or 1b.
9	COMP_CONFIG	RW	NVM	0b: At power-up or RESTORE, COMPENSATION_CONFIG will be reset to NVM value. 1b: At power-up or RESTORE, COMPENSATION_CONFIG will be reset to pin-detected value.
8	ADDRESS	RW	NVM	0b: At power-up or RESTORE, SLAVE_ADDRESS will be reset to NVM value. 1b: At power-up or RESTORE, SLAVE_ADDRESS will be reset to pin-detected value.
7:6	Reserved	RW	NVM	Not used and set to 00b.
5	INTERLEAVE	RW	NVM	0b: At power-up or RESTORE, INTERLEAVE will be reset to NVM value. 1b: At power-up or RESTORE, INTERLEAVE will be reset to pin-detected value.
4	Reserved	RW	NVM	Not used and set to 0b or 1b.
3	TON_RISE	RW	NVM	0b: At power-up or RESTORE, TON_RISE will be reset to NVM value. 1b: At power-up or RESTORE, TON_RISE will be reset to pin-detected value.

**表 7-101. Register Field Descriptions (continued)**

Bit	Field	Access	Reset	Description
2	IOUT_OC	RW	NVM	0b: At power-up or RESTORE, IOUT_OC_FAULT_LIMIT and IOUT_OC_WARN_LIMIT will be reset to NVM value. 1b: At power-up or RESTORE, IOUT_OC_FAULT_LIMIT and IOUT_OC_WARN_LIMIT will be reset to pin-detected value.
1	FREQ	RW	NVM	0b: At power-up or RESTORE, FREQUENCY_SWITCH will be reset to NVM value. 1b: At power-up or RESTORE, FREQUENCY_SWITCH will be reset to pin-detected value.
0	VOUT	RW	NVM	0b: At power-up or RESTORE, VOUT_COMMAND, VOUT_SCALE_LOOP, VOUT_MAX, and VOUT_MIN will be reset to NVM value. 1b: At power-up or RESTORE, VOUT_COMMAND, VOUT_SCALE_LOOP, VOUT_MAX, and VOUT_MIN will be reset to pin-detected value.

PIN\_DETECT\_OVERRIDE allows the user to force Pin Detected values to override the User Store NVM value for various PMBus commands during Power On Reset and RESTORE\_USER\_ALL.

### 7.6.85 (EFh) MFR\_SPECIFIC\_31 (SLAVE\_ADDRESS)

CMD Address	EFh
Write Transaction:	Write Byte
Read Transaction:	Read Byte
Format:	Unsigned Binary (1 bytes)
Phased:	No
NVM Backup:	EEPROM or Pin Detect
Updates:	on-the-fly

The (EFh) MFR\_SPECIFIC\_31 (SLAVE\_ADDRESS) command can be used to program or read-back the slave address of digital communication. Note, when (EFh) MFR\_SPECIFIC\_31 (SLAVE\_ADDRESS) is updated, the TPS546B24A updates its slave address and the TPS546B24A will stop responding to its prior address and start responding to its new address immediately. Attempts to write to or read from its prior address will be NACKed.

**图 7-91. (EFh) MFR\_SPECIFIC\_31 (SLAVE\_ADDRESS) Register Map**

7	6	5	4	3	2	1	0
R	RW	RW	RW	RW	RW	RW	RW
0	ADDR_PMBUS						

LEGEND: R/W = Read/Write; R = Read only

**表 7-102. Register Field Descriptions**

Bit	Field	Access	Reset	Description
7	Not support	R	0b	Not support. Set to b'0.
6:0	ADDR_PMBUS	RW	NVM/ Pinstap	PMBus Slave address

There are a number of slave address values which are reserved in the SMBus specification. The following reserved addresses are invalid and can not be programmed:

- 0x0C
- 0x28
- 0x37
- 0x61

**7.6.86 (F0h) MFR\_SPECIFIC\_32 (NVM\_CHECKSUM)**

CMD Address	F0h
Write Transaction:	NA
Read Transaction:	Read Word
Format:	Unsigned Binary (2 bytes)
Phased:	No
NVM Back-up:	EEPROM
Updates:	At boot-up, and following NVM Store/Restore operations.

NVM\_CHECKSUM reports the CRC-16 (polynomial 0x8005) checksum for the current NVM settings.

**图 7-92. (F0h) MFR\_SPECIFIC\_32 (NVM\_CHECKSUM) Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
NVM_CHECKSUM							
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
NVM_CHECKSUM							

LEGEND: R/W = Read/Write; R = Read only

**表 7-103. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	NVM_CHECKSUM	R	Per NVM Settings	CRC16 for EEPROM settings.

### 7.6.87 (F1h) MFR\_SPECIFIC\_33 (SIMULATE\_FAULT)

CMD Address	F1h
Write Transaction:	Write Word
Read Transaction:	Read Word
Format:	Unsigned Binary (2 bytes)
Phased:	Yes
NVM Back-up:	No

SIMULATE\_FAULT will allow the user to simulate fault and warning conditions by triggering the output of the detection circuit for that controls it. Multiple faults and or can be simulated at once.

**图 7-93. (F1h) MFR\_SPECIFIC\_F1 (SIMULATE\_FAULT) Register Map**

15	14	13	12	11	10	9	8
W/R	W/R	W/R	W/R	W/R	W/R	W/R	W/R
FAULT_PERSIST	SIM_TEMP_OTF	Reserved	SIM_IOUT_OC_F	SIM_VIN_OFF	SIM_VIN_OVF	SIM_VOUT_UVF	SIM_VOUT_OVF
7	6	5	4	3	2	1	0
W/R	W/R	W/R	W/R	W/R	W/R	W/R	W/R
WARN_PERSIST	Reserved	Reserved	SIM_IOUT_OC_W	SIM_VIN_UVW	Reserved	SIM_VOUT_UVW	SIM_VOUT_OVW

LEGEND: R/W = Read/Write; R = Read only

**表 7-104. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15	FAULT_PERSIST	W/R	0b	0b: Simulated faults are automatically removed after one fault response. 1b: Simulated faults persist until SIMULATE_FAULTS is written again.
14	SIM_TEMP_OTF	W/R	0b	0b: No change, 1b: Simulate overtemperature fault
13	Reserved	W/R	0b	0b: No change, 1b: Not used
12	SIM_IOUT_OCF	W/R	0b	0b: No change, 1b: Simulate output current overcurrent fault.
11	SIM_VIN_OFF*	W/R	0b	0b: No change, 1b: Simulate PVIN undervoltage lockout.
10	SIM_VIN_OVF	W/R	0b	0b: No change, 1b: Simulate PVIN overvoltage fault.
9	SIM_VOUT_UVF	W/R	0b	0b: No change, 1b: Simulate VOUT undervoltage fault.
8	SIM_VOUT_OVF*	W/R	0b	0b: No change, 1b: Simulate VOUT overvoltage fault.
7	WARN_PERSIST	W/R	Default Settings	0b: Simulated warnings are automatically removed after one Fault response. 1b: Simulated warnings persist until SIMULATE_FAULTS is written again.
6	Reserved	W/R	Default Settings	0b: No change, 1b: Not used
5	Reserved	W/R	Default Settings	0b: No change, 1b: Not used

**表 7-104. Register Field Descriptions (continued)**

Bit	Field	Access	Reset	Description
4	SIM_IOUT_ OCW	W/R	Default Settings	0b: No change, 1b: Simulate output current overcurrent warning.
3	SIM_VIN_U VW	W/R	Default Settings	0b: No change, 1b: Simulate PVIN undervoltage warning.
2	Reserved	W/R	Default Settings	0b: No change, 1b: Not used
1	SIM_VOUT_ UVW	W/R	Default Settings	0b: No change, 1b: Simulate VOUT undervoltage warning.
0	SIM_VOUT_ OVW	W/R	Default Settings	0b: No change, 1b: Simulate VOUT overvoltage warning.

\*Only SIM\_VIN\_OFF and SIM\_VOUT\_OVF are allowed to trigger their analog comparator while conversion is disabled. All other faults, including SIM\_TEMP\_OTF and SIM\_VIN\_OVF will only simulate while conversion is enabled in order to allow these faults to simulate repeated shut-down and restart responses when FAULT\_PERSIST is selected.

### 7.6.88 (FCh) MFR\_SPECIFIC\_44 (FUSION\_ID0)

CMD Address	FCh
Write Transaction:	Write Word (writes accepted but otherwise ignored)
Read Transaction:	Read Word
Format:	Unsigned Binary (2 bytes)
Phased:	No
NVM Back-up:	No

FUSION\_ID0 provides a platform level Identification code to be used by Texas Instruments Digital Power Designer for identifying a TI device.

Writes to this command will be accepted, but ignored otherwise (the readback value of this command does not change following a write attempt). This command is writeable for some TI devices, so to maintain cross-compatibility, the TPS546B24A accepts write transactions to this command as well. No [STATUS\\_CML](#) bits are set as a result of the receipt of a write attempt to this command.

**图 7-94. (FCh) MFR\_SPECIFIC\_44 (FUSION\_ID0) Register Map**

15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
FUSION_ID0							
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
FUSION_ID0							

LEGEND: R/W = Read/Write; R = Read only

**表 7-105. Register Field Descriptions**

Bit	Field	Access	Reset	Description
15:0	FUSION_ID0	R	02D0h	Hard Coded to 02D0h

**7.6.89 (FDh) MFR\_SPECIFIC\_45 (FUSION\_ID1)**

CMD Address	FDh
Write Transaction:	Block Write (writes accepted but otherwise ignored)
Read Transaction:	Block Read
Format:	Unsigned Binary (6 bytes)
Phased:	No
NVM Back-up:	No

FUSION\_ID1 provides a platform level Identification code to be used by Texas Instruments Digital Power Designer for identifying a TI device.

Writes to this command will be accepted, but ignored otherwise (the readback value of this command does not change following a write attempt). This command is writeable for some TI devices, so to maintain cross-compatibility, the TPS546B24A accepts write transactions to this command as well. No [STATUS\\_CML](#) bits are set as a result of the receipt of a write attempt to this command.

**图 7-95. (FDh) MFR\_SPECIFIC\_45 (FUSION\_ID1) Register Map**

47	46	45	44	43	42	41	40
R	R	R	R	R	R	R	R
FUSION_ID1							
39	38	37	36	35	34	33	32
R	R	R	R	R	R	R	R
FUSION_ID1							
31	30	29	28	27	26	25	24
FUSION_ID1							
23	22	21	20	19	18	17	16
R	R	R	R	R	R	R	R
FUSION_ID1							
15	14	13	12	11	10	9	8
R	R	R	R	R	R	R	R
FUSION_ID1							
7	6	5	4	3	2	1	0
R	R	R	R	R	R	R	R
FUSION_ID1							

LEGEND: R/W = Read/Write; R = Read only

**表 7-106. Register Field Descriptions**

Bit	Field	Access	Reset	Description
47:40	FUSION_ID1	R	4Bh	Hard coded to 4Bh
39:32	FUSION_ID1	R	43h	Hard coded to 43h
31:24	FUSION_ID1	R	4Fh	Hard coded to 4Fh
23:16	FUSION_ID1	R	4Ch	Hard coded to 4Ch



**表 7-106. Register Field Descriptions (continued)**

Bit	Field	Access	Reset	Description
15:8	FUSION_ ID1	R	49h	Hard coded to 49h
7:0	FUSION_ ID1	R	54h	Hard coded to 54h

## 8 Application and Implementation

### Note

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

### 8.1 Application Information

The TPS546B24A is a highly integrated, synchronous step-down DC/DC converter. This device is used to convert a higher DC-input voltage to a lower DC-output voltage, with a maximum output current of for a single device. Use the following design procedures to select key component values for single phase. The appropriate behavioral options can be set through PMBus.

### 8.2 Typical Application

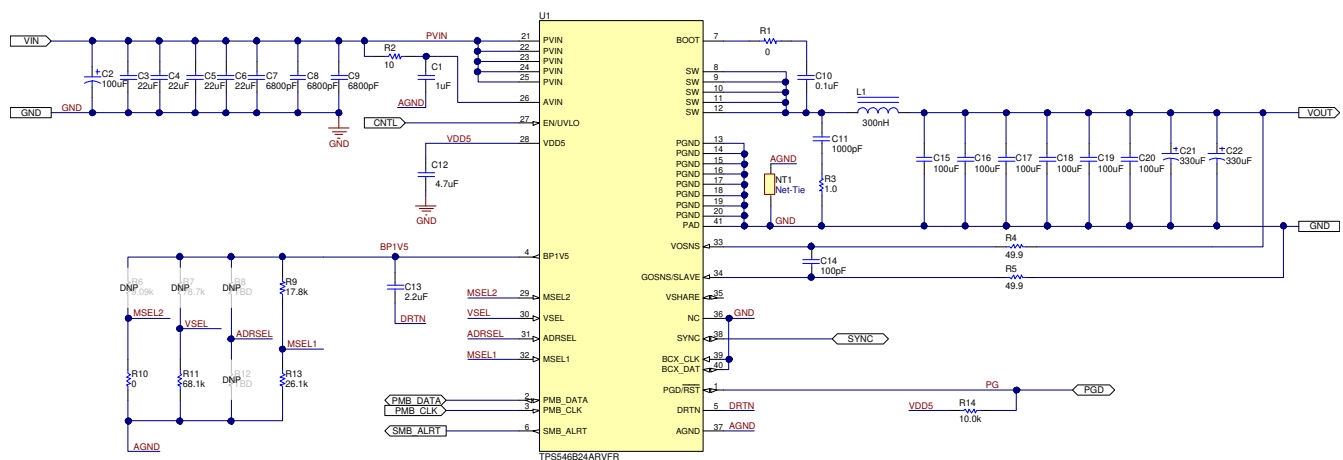


図 8-1. TPS546B24A Application

## 8.2.1 Design Requirements

For this design example, use the input parameters listed in 表 8-1.

**表 8-1. Design Parameters**

DESIGN PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{IN}$	Input voltage		5	12	18	V
$V_{IN(ripple)}$	Input ripple voltage	$V_{IN} = 12\text{ V}$ , $I_{OUT} = 20\text{ A}$		0.3		V
$V_{OUT}$	Output voltage			1.2		V
$\Delta V_{O(\Delta V)}$	Line regulation	$5\text{ V} \leq V_{IN} \leq 18\text{ V}$			0.5%	
$\Delta V_{O(\Delta I)}$	Load regulation	$0\text{ V} \leq I_{OUT} \leq 20\text{ A}$			0.5%	
$V_{PP}$	Output ripple voltage	$I_{OUT} = 20\text{ A}$		20		mV
$\Delta V_{OUT}$	$V_{OUT}$ deviation during load transient	$\Delta I_{OUT} = 10\text{ A}$ , $V_{IN} = 12\text{ V}$		50		mV
$I_{OUT}$	Output current	$5\text{ V} \leq V_{IN} \leq 18\text{ V}$	0		20	A
$I_{OCP}$	Output overcurrent protection threshold			26		A
$F_{SW}$	Switching frequency	$V_{IN} = 12\text{ V}$		650		kHz
$\eta_{Full\ load}$	Full load efficiency	$V_{IN} = 12\text{ V}$ , $I_{OUT} = 20\text{ A}$		88%		
$t_{SS}$	Soft-start time ( $T_{ON\_RISE}$ )			5		ms

## 8.2.2 Detailed Design Procedure

The TPS546B24A provides four pins to program critical PMBus register values without requiring PMBus communication. Please refer to 表 7-7 for the pin-strapping options. Some equations include a variable N, which is the number of devices stacked together. In this stand-alone device example, the value of N is equal to 1.

The [TPS546x24A Compensation and Pin-Strap Resistor Calculator](#) can also be used to aid in design calculations and pin-strap resistor selection.

### 8.2.2.1 Custom Design With WEBENCH® Tools

[Click here](#) to create a custom design using the TPS546B24A device with the WEBENCH® Power Designer.

1. Start by entering the input voltage ( $V_{IN}$ ), output voltage ( $V_{OUT}$ ), and output current ( $I_{OUT}$ ) requirements.
2. Optimize the design for key parameters such as efficiency, footprint, and cost using the optimizer dial.
3. Compare the generated design with other possible solutions from Texas Instruments.

The WEBENCH Power Designer provides a customized schematic along with a list of materials with real-time pricing and component availability.

In most cases, these actions are available:

- Run electrical simulations to see important waveforms and circuit performance
- Run thermal simulations to understand board thermal performance
- Export customized schematic and layout into popular CAD formats
- Print PDF reports for the design, and share the design with colleagues

Get more information about WEBENCH tools at [www.ti.com/WEBENCH](http://www.ti.com/WEBENCH).

### 8.2.2.2 Switching Frequency

The MSEL1 pin programs [USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#) and [FREQUENCY\\_SWITCH](#). The resistor divider ratio for MSEL1 selects the nominal switching frequency. In the design procedure for MSEL1, switching frequency is configured first, compensation will be chosen after output capacitance is determined.

There is a tradeoff between higher and lower switching frequencies for buck converters. Higher switching frequencies may produce smaller solution size using lower valued inductors and smaller output capacitors compared to a power supply that switches at a lower frequency. However, the higher switching frequency causes extra switching losses, which decrease efficiency and impact thermal performance.

In this design, a moderate switching frequency of 650 kHz achieves both a small solution size and a high-efficiency operation. Use the MSEL1 pin program table to select the frequency option. See 表 7-8 for resistor divider code selection. Resistor divider code 8 or 9 is needed to set the switching frequency to 325 kHz.

### 8.2.2.3 Inductor Selection

Use 式 9 to calculate the value of the output inductor (L). The coefficient, KIND, represents the amount of inductor-ripple current relative to the maximum output current. The output capacitor filters the inductor-ripple current. Therefore, selecting a high inductor-ripple current impacts the selection of the output capacitor because the output capacitor must have a ripple-current rating equal to or greater than the inductor-ripple current. Generally, the KIND coefficient should be kept between 0.2 and 0.3 for balanced performance. Additionally the product of KIND and  $I_{OUT(Max)}$  should be kept above 1 A to prevent the inductance from being too large. Using this target ripple current, the required inductor size can be calculated as shown in 式 9.

$$L = \frac{V_{OUT}}{V_{IN(Max)} \times f_{SW(Min)}} \times \frac{(V_{IN(Max)} - V_{OUT})}{\frac{I_{OUT(Max)}}{N} \times KIND} = \frac{1.2 \text{ V}}{18 \text{ V} \times 650 \text{ kHz}} \times \frac{(18 \text{ V} - 1.2 \text{ V})}{\frac{20 \text{ A}}{1} \times 0.3} = 287 \text{ nH} \quad (9)$$

Selecting a value of 0.3 for the KIND coefficient, the target inductance, L, is 287 nH. An inductance of 300 nH is selected. Use 式 10, 式 11, and 式 12 to calculate the inductor-ripple current ( $I_{RIPPLE}$ ), RMS current ( $I_{L(rms)}$ ), and peak current ( $I_{L(peak)}$ ), respectively. Use these values to select an inductor with approximately the target inductance value, and current ratings that allow normal operation with some margin.

$$I_{RIPPLE} = \frac{V_{OUT}}{V_{IN(Max)} \times f_{SW(Min)}} \times \frac{V_{IN(Max)} - V_{OUT}}{L1} = \frac{1.2 \text{ V} \times (18 \text{ V} - 1.2 \text{ V})}{18 \text{ V} \times 650 \text{ kHz} \times 300 \text{ nH}} = 5.74 \text{ A} \quad (10)$$

$$I_{L(rms)} = \sqrt{\left(\frac{I_{OUT(Max)}}{N}\right)^2 + \frac{1}{12}(I_{RIPPLE})^2} = \sqrt{\left(\frac{20 \text{ A}}{1}\right)^2 + \frac{1}{12}(5.74 \text{ A})^2} = 20 \text{ A} \quad (11)$$

$$I_{L(peak)} = \frac{I_{OUT(Max)}}{N} + \frac{1}{2}(I_{RIPPLE}) = \frac{20 \text{ A}}{1} + \frac{1}{2} \times (5.74 \text{ A}) = 22.9 \text{ A} \quad (12)$$

Considering the required inductance, RMS current and peak current, the 300-nH inductor, SLC1175-301ME, from Coilcraft was selected for this application.

### 8.2.2.4 Output Capacitor Selection

Consider the following when selecting the value of the output capacitor:

- The output-voltage deviation during load transient
- The output-voltage ripple

#### 8.2.2.4.1 Output Voltage Deviation During Load Transient

The desired response to a load transient is the first criterion for output capacitor selection. The output capacitor must supply the load with the required current when not immediately provided by the regulator. When the output capacitor supplies load current, the impedance of the capacitor affects the magnitude of the voltage deviation during the transient.

To meet the requirements for control-loop stability, the device requires the addition of compensation components in the design of the error amplifier. While these compensation components provide for a stable control loop, they often also reduce the speed with which the regulator can respond to load transients. The delay in the regulator response to load changes can be two or more clock cycles before the control loop reacts to the change. During that time, the difference (delta) between the old and the new load current must be supplied (or absorbed) by the output capacitance. The output capacitor impedance must be designed to supply or absorb the delta current

while maintaining the output voltage within acceptable limits. 式 13 and 式 14 show the relationship between the transient response overshoot ( $V_{OVER}$ ), the transient response undershoot ( $V_{UNDER}$ ), and the required output capacitance ( $C_{OUT}$ ).

$$V_{OVER} < \frac{(I_{TRAN})^2 \times L}{V_{OUT} \times C_{OUT}} \quad (13)$$

$$V_{UNDER} < \frac{(I_{TRAN})^2 \times L}{(V_{IN} - V_{OUT}) \times C_{OUT}} \quad (14)$$

If

- $V_{IN(min)} > 2 \times V_{OUT}$ , use overshoot to calculate minimum output capacitance.
- $V_{IN(min)} < 2 \times V_{OUT}$ , use undershoot to calculate minimum output capacitance.

In this case, the minimum designed input voltage,  $V_{IN(min)}$ , is greater than  $2 \times V_{OUT}$ , so  $V_{OVER}$  dictates the minimum output capacitance. Therefore, using 式 15, the minimum output capacitance required to meet the transient requirement is 500  $\mu F$ .

$$C_{OUT(Min)} = \frac{(I_{TRAN})^2 \times L}{V_{OUT} \times V_{OVER}} = \frac{(10 \text{ A})^2 \times 300 \text{ nH}}{1.2 \text{ V} \times 50 \text{ mV}} = 500 \mu F \quad (15)$$

The bandwidth of the voltage loop should also be considered when calculating the minimum output capacitance. The voltage loop can typically be compensated to have a bandwidth of 1/10th the  $f_{SW}$ . 式 16 calculates the minimum output capacitance to be 490  $\mu F$ .

$$C_{OUT(Min)} = \frac{1}{2\pi \times \frac{f_{SW}}{10} \times \frac{V_{TRAN}}{I_{TRAN}}} = \frac{1}{2\pi \times \frac{650 \text{ kHz}}{10} \times \frac{50 \text{ mV}}{10 \text{ A}}} = 490 \mu F \quad (16)$$

#### 8.2.2.4.2 Output Voltage Ripple

The output-voltage ripple is the second criterion for output capacitor selection. Use 式 17 to calculate the minimum output capacitance required to meet the output-voltage ripple specification.

$$C_{OUT(Min)} = \frac{I_{RIPPLE}}{8 \times f_{SW} \times V_{OUT(RIPPLE)}} = \frac{5.74 \text{ A}}{8 \times 650 \text{ kHz} \times 20 \text{ mV}} = 55 \mu F \quad (17)$$

In this case, the target maximum output-voltage ripple is 20 mV. Under this requirement, the minimum output capacitance for ripple is 55  $\mu F$ . This capacitance value is smaller than the output capacitance required for the transient response, so select the output capacitance value based on the transient requirement. Considering the variation and derating of capacitance, in this design, two 330- $\mu F$  low-ESR tantalum polymer bulk capacitors and six 100- $\mu F$  ceramic capacitors were selected to meet the transient specification with sufficient margin. Therefore the selected nominal  $C_{OUT}$  is equal to 1260  $\mu F$ .

With the output capacitance value selected the ESR must be considered. This is an important consideration in this example because it uses mixed output capacitor types. First use 式 18 to calculate the maximum allowable impedance for the output capacitor bank at the switching frequency to meet the output voltage ripple specification. 式 18 indicates the output capacitor bank impedance should be less than 3.5 m $\Omega$ . The impedance of the ceramic capacitors is calculated with 式 19 and the impedance of the bulk capacitor is calculated with 式 20. The result from 式 20 shows the impedance of the bulk capacitor at the switching frequency is dominated by its ESR. 式 21 calculates the total output impedance of the output capacitor bank at the switching frequency to be m $\Omega$  which meets the 3.5 m $\Omega$  requirement.

$$Z_{\text{COUT(Max)}\_f_{\text{SW}}} = \frac{V_{\text{OUT(RIPPLE)}}}{I_{\text{RIPPLE}}} = \frac{20 \text{ mV}}{5.74 \text{ A}} = 3.5 \text{ m}\Omega \quad (18)$$

$$Z_{\text{CER\_}f_{\text{SW}}} = \frac{1}{2\pi \times f_{\text{SW}} \times C_{\text{CER}}} = \frac{1}{2\pi \times 650 \text{ kHz} \times (6 \times 100 \text{ }\mu\text{F})} = 0.4 \text{ m}\Omega \quad (19)$$

$$Z_{\text{BULK\_}f_{\text{SW}}} = \sqrt{\text{ESR}_{\text{BULK}}^2 + \left( \frac{1}{2\pi \times f_{\text{SW}} \times C_{\text{BULK}}} \right)^2} = \sqrt{\left( \frac{6 \text{ m}\Omega}{2} \right)^2 + \left( \frac{1}{2\pi \times 650 \text{ kHz} \times (2 \times 330 \text{ }\mu\text{F})} \right)^2} = 3.0 \text{ m}\Omega \quad (20)$$

$$Z_{\text{COUT\_}f_{\text{SW}}} = \frac{Z_{\text{CER\_}f_{\text{SW}}} \times Z_{\text{BULK\_}f_{\text{SW}}}}{Z_{\text{CER\_}f_{\text{SW}}} + Z_{\text{BULK\_}f_{\text{SW}}}} = \frac{0.4 \text{ m}\Omega \times 3.0 \text{ m}\Omega}{0.4 \text{ m}\Omega + 3.0 \text{ m}\Omega} = 0.35 \text{ m}\Omega \quad (21)$$

### 8.2.2.5 Input Capacitor Selection

The power-stage input-decoupling capacitance (effective capacitance at the PVIN and PGND pins) must be sufficient to supply the high switching currents demanded when the high-side MOSFET switches on, while providing minimal input-voltage ripple as a result. This effective capacitance includes any DC-bias effects. The voltage rating of the input capacitor must be greater than the maximum input voltage with derating. The capacitor must also have a ripple-current rating greater than the maximum input-current ripple to the device during full load. Use 式 22 to estimate the input RMS current.

$$I_{\text{IN(rms)}} = \frac{I_{\text{OUT(Max)}}}{N} \times \sqrt{\frac{V_{\text{OUT}}}{V_{\text{IN(Min)}}} \times \frac{(V_{\text{IN(Min)}} - V_{\text{OUT}})}{V_{\text{IN(Min)}}}} = \frac{20 \text{ A}}{1} \times \sqrt{\frac{1.2 \text{ V}}{5 \text{ V}} \times \frac{(5 \text{ V} - 1.2 \text{ V})}{5 \text{ V}}} = 8.54 \text{ A} \quad (22)$$

The minimum input capacitance and ESR values for a given input voltage-ripple specification,  $V_{\text{IN(ripple)}}$ , are shown in 式 23 and 式 24. The input ripple is composed of a capacitive portion ( $V_{\text{RIPPLE(cap)}}$ ) and a resistive portion ( $V_{\text{RIPPLE(esr)}}$ ).

$$C_{\text{IN(Min)}} = \frac{\frac{I_{\text{OUT(Max)}}}{N} \times V_{\text{OUT}}}{V_{\text{RIPPLE(cap)}} \times V_{\text{IN(Max)}} \times f_{\text{SW}}} = \frac{\frac{20 \text{ A}}{1} \times 1.2 \text{ V}}{0.1 \text{ V} \times 18 \text{ V} \times 650 \text{ kHz}} = 20.5 \text{ }\mu\text{F} \quad (23)$$

$$\text{ESR}_{\text{CIN(Max)}} = \frac{V_{\text{RIPPLE(ESR)}}}{\frac{I_{\text{OUT(Max)}}}{N} + \frac{1}{2} I_{\text{RIPPLE}}} = \frac{0.2 \text{ V}}{\frac{20 \text{ A}}{1} + \frac{1}{2} \times 5.74 \text{ A}} = 8.7 \text{ m}\Omega \quad (24)$$

The value of a ceramic capacitor varies significantly over temperature and the amount of DC bias applied to the capacitor. The capacitance variations because of temperature can be minimized by selecting a dielectric material that is stable over temperature. X5R and X7R ceramic dielectrics are usually selected for power-regulator capacitors because these components have a high capacitance-to-volume ratio and are fairly stable over temperature. The input capacitor must also be selected with consideration of the DC bias. For this example design, a ceramic capacitor with at least a 25-V voltage rating is required to support the maximum input voltage. For this design, allow 0.1-V input ripple for  $V_{\text{RIPPLE(cap)}}$  and 0.2-V input ripple for  $V_{\text{RIPPLE(esr)}}$ . Using 式 23 and 式 24, the minimum input capacitance for this design is 20.5  $\mu\text{F}$ , and the maximum ESR is 8.7 m $\Omega$ . For this design example, four 22- $\mu\text{F}$ , 25-V ceramic capacitors, three 6800-pF, 25-V ceramic capacitors, and one additional 100- $\mu\text{F}$ , 25-V low-ESR electrolytic capacitors in parallel were selected for the power stage with sufficient margin. For all designs a minimum input capacitance of 10  $\mu\text{F}$  is required and a maximum input ripple of 500 mV is recommended.

To minimize the high frequency ringing, the high frequency 6800-pF PVIN bypass capacitors must be placed close to power stage.

#### 8.2.2.6 AVIN, BP1V5, VDD5 Bypass Capacitor

The BP1V5 pin requires a minimum capacitance of 1 µF connected to DRTN. The VDD5 pin should have approximately 4.7 µF of capacitance connected to PGND. The AVIN pin should have approximately 1 µF of capacitance connected to AGND. To filter switching noise on the AVIN pin, a small value resistor of typically 10-Ω is recommended to be placed between PVIN and AVIN. If using split rail inputs and if the AVIN pin is connected to the VDD5 pin, a small value resistor is recommended to be placed between AVIN and VDD5.

#### 8.2.2.7 Bootstrap Capacitor Selection

A ceramic capacitor with a value of 0.1 µF must be connected between the BOOT and SW pins for proper operation. TI recommends using a ceramic capacitor with X5R or better grade dielectric with a voltage rating of 25 V or higher. Lower voltage rating capacitors may be used as long as the capacitance is greater than 0.08 µF after AC and DC bias derating.

#### 8.2.2.8 R-C Snubber

An R-C snubber must be placed between the switching node and PGND to reduce voltage spikes on the switching node. The power rating of the resistor must be larger than the power dissipation on the resistor with sufficient margin. To balance efficiency and voltage spike amplitude, a 1-nF capacitor and a 1-Ω resistor were selected for this design. In this example, an 0805 resistor was selected, which is rated for 0.125 W.

#### 8.2.2.9 Output Voltage Setting (VSEL Pin)

The output voltage can be set using the VSEL pin. The resistor divider ratio for VSEL programs the [VOUT\\_COMMAND](#) range, [VOUT\\_SCALE\\_LOOP](#) divider, [VOUT\\_MIN](#), and [VOUT\\_MAX](#) levels according to [表 7-12](#). Select the resistor divider code for the range of VOUT desired. For this 1.2-V output example, resistor divider code 4 or a single resistor to AGND.

With the resistor divider code selected for the range of VOUT, select the resistor to AGND code with the VOUT\_COMMAND Offset and VOUT\_COMMAND step from [表 7-13](#). To calculate the resistor to AGND code subtract the VOUT\_COMMAND offset from the target output voltage and divide by the VOUT\_COMMAND step. For this example, a single resistor to AGND was used and the result is code 14. A 68.1-kΩ resistor to AGND at VSEL programs the desired setting.

$$\text{Code} = \frac{V_{\text{OUT}} - V_{\text{OUT\_COMMAND}}_{(\text{Offset})}}{V_{\text{OUT\_COMMAND}}_{(\text{STEP})}} = \frac{1.2 - 0.5}{0.05} = 14 \quad (25)$$

#### 8.2.2.10 Compensation Selection (MSEL1 Pin)

The resistor to AGND for MSEL1 selects the [\(B1h\) USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#) values to program the following voltage loop and current loop gains. For options other than the EEPROM code (MSEL1 shorted to AGND or MSEL1 to AGND resistor code 0), the current and voltage loop zero and pole frequencies are scaled with the programmed switching frequency.

Based on [Current Error Integrator](#), calculate the mid-band current loop gain with [式 26](#).

$$I_{\text{LOOP\_MB}} = G_{\text{MI}} \times R_{\text{VI}} = \frac{V_{\text{ramp}}}{V_{\text{PVIN}}} \times \frac{1.7}{\text{CSA}} \times L \times \pi \times \frac{f_{\text{SW}}}{4} = \frac{1.7 \times \pi}{4 \times 5.5 \times 12.31 \times 10^{-3}} \times L \times f_{\text{SW}} = 19.72 \times L \times f_{\text{SW}} = 19.7 \times 300\text{nH} \times 650\text{kHz} = 3.9 \quad (26)$$

Find the smaller value closest to 3.9 in [表 7-9](#) and this is 3.7. An Iloop of 5 is chosen to reduce pulse-width jitter.

To calculate the target voltage loop gain, first use [式 27](#) through [式 29](#) to calculate the output impedance. Use [式 30](#) to calculate the target voltage loop gain.



$$Z_{CER\_f_{BW}} = \frac{1}{2\pi \times \frac{f_{SW}}{10} \times C_{CER}} = \frac{1}{2\pi \times \frac{650 \text{ kHz}}{10} \times (6 \times 100 \text{ } \mu\text{F})} = 4.1 \text{ m}\Omega \quad (27)$$

$$Z_{BULK\_f_{BW}} = \sqrt{ESR_{BULK}^2 + \left( \frac{1}{2\pi \times \frac{f_{SW}}{10} \times C_{BULK}} \right)^2} = \sqrt{\left( \frac{6 \text{ m}\Omega}{2} \right)^2 + \left( \frac{1}{2\pi \times \frac{650 \text{ kHz}}{10} \times (2 \times 330 \text{ } \mu\text{F})} \right)^2} = 8.7 \text{ m}\Omega \quad (28)$$

$$Z_{COUT\_f_{BW}} = \frac{Z_{CER\_f_{BW}} \times Z_{BULK\_f_{BW}}}{Z_{CER\_f_{BW}} + Z_{BULK\_f_{BW}}} = \frac{4.1 \text{ m}\Omega \times 8.7 \text{ m}\Omega}{4.1 \text{ m}\Omega + 8.7 \text{ m}\Omega} = 2.8 \text{ m}\Omega \quad (29)$$

$$V_{LOOP\_MB} = GMV \times RVV = \frac{1}{V_{OUT\_SCALE\_LOOP}} \times \frac{CSA}{N \times Z_{COUT\_f_{BW}}} = \frac{1}{0.5} \times \frac{12.31 \frac{\text{mV}}{\text{A}}}{1 \times 2.8 \text{ m}\Omega} = 8.8 \quad (30)$$

Find the smaller value closest to 8.8 in [表 7-9](#) for voltage loop gain and this is 8. This setting gives a stable design but through bench evaluation the voltage loop gain was reduced to 4 to improve the gain and phase margin. The calculated current and voltage loop gain correspond to compensation setting 9. To use this compensation setting resistor to AGND code 9 is needed. With this compensation code the even resistor divider code should be used to set the switching frequency. Divider code 8 sets the fsw to 650 kHz. Resistor to AGND code and resistor divider code 8 9 is selected using an MSEL1 resistor divider of  $R_{TOP} = 17.8 \text{ k}\Omega$  and  $R_{BOT} = 26.1 \text{ k}\Omega$ .

The procedure given is meant to give a stable design. Further optimization of the compensation is often possible through testing the design on the bench. Increasing the voltage loop gain will increase the loop bandwidth to improve the transient response but it is important verify there is still sufficient gain and phase margin. The maximum voltage loop bandwidth possible is limited by these stability margins. Decreasing the current loop gain can help to minimize pulse-width jitter but this typically comes with a tradeoff of decreased phase margin. Lastly, the pole and zero locations can also be adjusted through PMBus. For example, it can be beneficial to use the CPV capacitor in the voltage loop to add a pole at the same frequency of the ESR zero when using high ESR output capacitors.

When using a larger inductance, the current loop gain that can be selected through pin strapping can be much lower than the calculated target value. If this happens, the voltage loop gain must also be scaled back by about the same amount to keep sufficient phase margin. For higher voltage loop bandwidth, the inductance can be decreased to reduce the current loop gain needed or higher current loop gain can be programmed through the PMBus command [USER\\_DATA\\_01 \(COMPENSATION\\_CONFIG\)](#).

#### 8.2.2.11 Soft Start, Overcurrent Protection, and Stacking Configuration (MSEL2 Pin)

Soft-start time, overcurrent protection thresholds, and stacking configuration can be configured using the MSEL2 pin. The TPS546B24A device support several soft-start times from 0 to 31.75 ms in 250- $\mu\text{s}$  steps (7 bits) selected by the [TON\\_RISE](#) command. Eight times are selectable using the MSEL2 pin. The TPS546B24A device support several low-side overcurrent warn and fault thresholds from TBD to TBD A selected by the [IOUT\\_OC\\_WARN\\_LIMIT](#) and [IOUT\\_OC\\_FAULT\\_LIMIT](#) commands. Four thresholds are selectable using the MSEL2 pin. The response to an OC fault can be changed through PMBus. Lastly, the number of devices stacked is set using the MSEL2 pin.

The resistor divider code for MSEL2 selects the soft-start values. The resistor to AGND will determine the number of devices sharing common output and the overcurrent thresholds. Use [表 7-11](#) and [表 7-10](#) to select the resistor to AGND code and resistor divider code needed for the desired configuration.

In this single phase design, resistor divider code 3 is selected for 5-ms soft start and resistor to AGND code 0 is selected for the highest current limit thresholds and stand alone configuration.



### 8.2.2.12 Enable and UVLO

The [ON\\_OFF\\_CONFIG](#) command is used to select the turnon behavior of the converter. For this example, the EN/UVLO pin or CONTROL pin was used to enable or disable the converter, regardless of the state of [OPERATION](#), as long as the input voltage is present and above the UVLO threshold. The EN/UVLO pin is pulled low internally if it is floating.

A resistor divider can be added the EN/UVLO pin to program an additional UVLO. Additionally 0.1 μF can be placed on this pin to filter noise or short glitches. Use [式 31](#) and [式 32](#) to calculate the resistor values to target a 4.75-V turnon and a 4.25-V turnoff. Standard resistor values of 30.1 kΩ and 8.66 kΩ are selected for this example. Use [式 33](#) and [式 34](#) to calculate the thresholds based on selected resistor values.

$$R_{ENTOP} = \frac{V_{ON} \times V_{ENFALL} - V_{OFF} \times V_{ENRISE}}{N \times I_{ENHYS} \times V_{ENRISE}} = \frac{4.75 \text{ V} \times 0.98 \text{ V} - 4.25 \text{ V} \times 1.05 \text{ V}}{1 \times 5.5 \mu\text{A} \times 1.05 \text{ V}} = 33.3 \text{ k}\Omega \quad (31)$$

$$R_{ENBOT} = \frac{R_{ENTOP} \times V_{ENFALL}}{V_{OFF} - V_{ENFALL} + N \times I_{ENHYS} \times R_{ENTOP}} = \frac{30.1 \text{ k}\Omega \times 0.98 \text{ V}}{4.25 \text{ V} - 0.98 \text{ V} + 1 \times 5.5 \mu\text{A} \times 30.1 \text{ k}\Omega} = 8.59 \text{ k}\Omega \quad (32)$$

$$V_{ON} = \frac{V_{ENRISE} \times (R_{ENBOT} + R_{ENTOP})}{R_{ENBOT}} = \frac{1.05 \text{ V} \times (8.66 \text{ k}\Omega + 30.1 \text{ k}\Omega)}{8.66 \text{ k}\Omega} = 4.7 \text{ V} \quad (33)$$

$$V_{OFF} = \frac{V_{ENFALL} \times (R_{ENBOT} + R_{ENTOP})}{R_{ENBOT}} - N \times I_{ENHYS} \times R_{ENTOP} = \frac{0.98 \text{ V} \times (8.66 \text{ k}\Omega + 30.1 \text{ k}\Omega)}{8.66 \text{ k}\Omega} - 1 \times 5.5 \mu\text{A} \times 30.1 \text{ k}\Omega = 4.22 \text{ V} \quad (34)$$

### 8.2.2.13 ADRSEL

In this example, the ADRSEL pin is left floating. This sets the PMBus slave address to the EEPROM value, 0x24h (36d) by default, and the SYNC pin to auto detect with 0 degrees phase shift. Use [表 7-14](#) and [表 7-15](#) to select the resistor to AGND code and resistor divider code needed for the desired configuration.

If through pin-strapping, the desired address is not possible with the SYNC pin set to auto detect and synchronization is not needed in the application, the SYNC pin should be configured for SYNC\_OUT. The device will still regulate normally with the SYNC pin configured for SYNC\_IN, however, if there is not clock input to the SYNC pin, the device will declare a SYNC fault in the [STATUS\\_MFR\\_SPECIFIC](#) command.

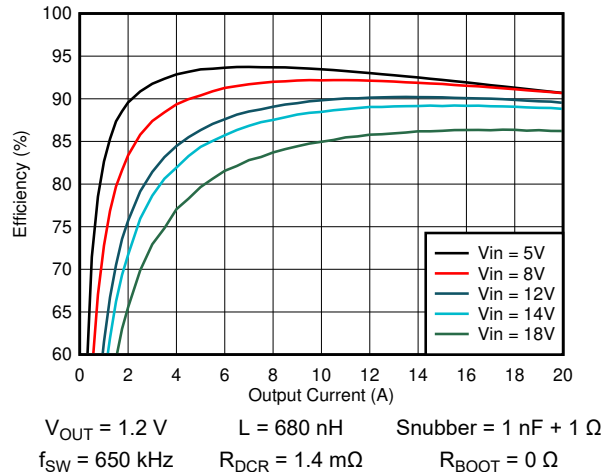
### 8.2.2.14 Pin-Strapping Resistor Selection

The following tables provide the resistor to AGND values, in ohms, in the highlighted top rows and the top resistor (pin to BP1V5) values, in ohms, in the unhighlighted cells. Select the column associated with the desired *resistor to AGND* code and the row with the desired *resistor divide* code in [表 7-17](#) and [表 7-18](#).

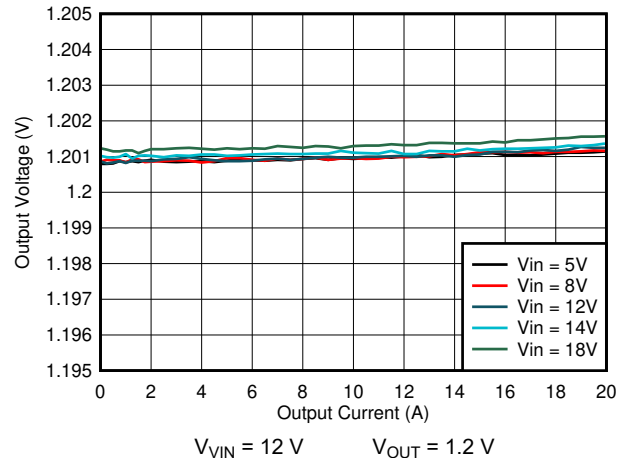
### 8.2.2.15 BCX\_CLK and BCX\_DAT

For a stand-alone device, the BCX\_CLK and BCX\_DAT pins are not used. As shown in [表 7-5](#), TI recommends ground them to the thermal pad.

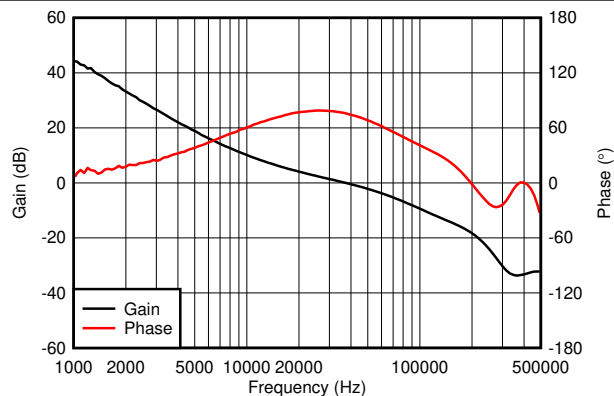
## 8.2.3 Application Curves



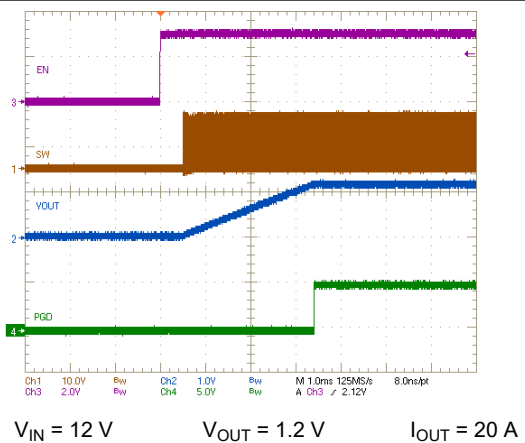
**8-2. Efficiency vs Output Current**



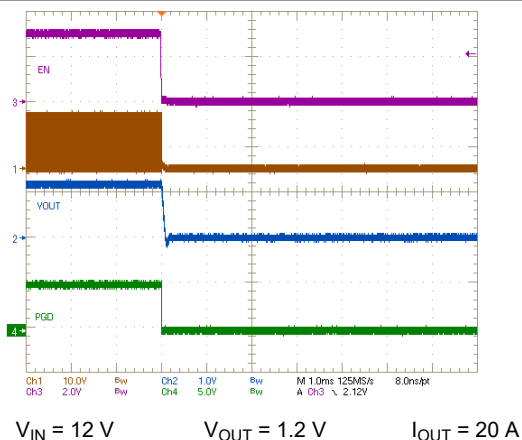
**8-3. Load Regulation**



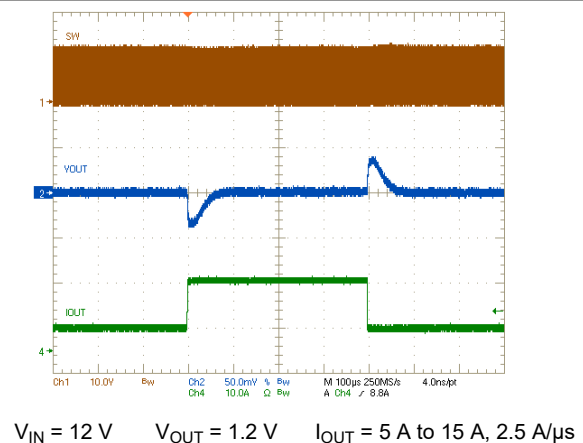
**8-4. Total-Loop Bode Plot**



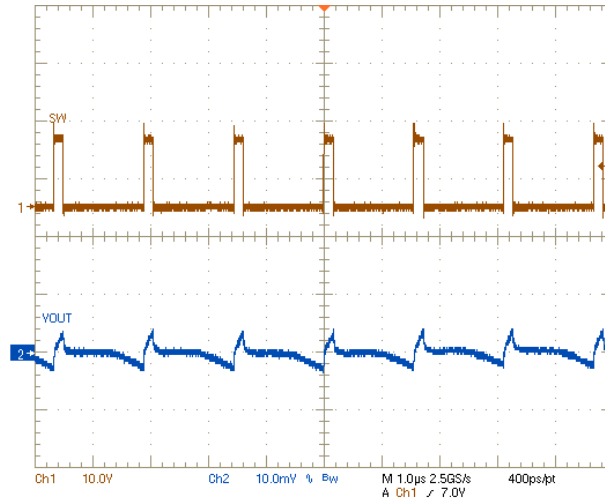
**8-5. Start-Up from EN/UVLO**



**8-6. Shutdown from CNTL**



**8-7. Load Transient Response**



$V_{IN} = 12\text{ V}$

$V_{OUT} = 1.2\text{ V}$

$I_{OUT} = 20\text{ A}$

**8-8.  $V_{OUT}$  Steady-State Ripple**

## 9 Power Supply Recommendations

The TPS546B24A devices are designed to operate from split input voltage supplies. AVIN is designed to operate from 2.95 V to 18 V. AVIN must be powered to enable POR, PMBus communication, or output conversion. For AVIN voltages less than 4 V, VDD5 must be supplied with an input voltage greater than 4 V to enable switching. PVIN is designed to operate from 2.95 V to 16 V. PVIN must be powered to enable switching, but not for POR or PMBus communication. The TPS546B24A can be operated from a single 4-V or higher supply voltage by connecting AVIN to PVIN. TI recommends a 10-Ω resistor between AVIN and PVIN to reduce switching noise on AVIN. See the recommendations in [Layout](#).

## 10 Layout

### 10.1 Layout Guidelines

Layout is critical for good power-supply design. [Figure 10-1](#) shows the recommended PCB-layout configuration. A list of PCB layout considerations using these devices is listed as follows:

- As with any switching regulator, several power or signal paths exist that conduct fast switching voltages or currents. Minimize the loop area formed by these paths and their bypass connections.
- Bypass the PVIN pins to PGND with a low-impedance path. Place the input bypass capacitors of the power-stage as close as physically possible to the PVIN and PGND pins. Additionally, a high-frequency bypass capacitor in a 0402 package on the PVIN pins can help reduce switching spikes. This capacitor can be placed on the other side of the PCB directly underneath the device to keep a minimum loop.
- The VDD5 bypass capacitor carries a large switching current for the gate driver. Bypassing the VDD5 pin to PGND at the thermal pad with a low-impedance path is very critical to the stable operation of the TPS546B24A devices. Place the VDD5 high-frequency bypass capacitors as close as possible to the device pins, with a minimum return loop back to the Thermal Pad.
- The AVIN bypass capacitor should be placed close to the AVIN pin and provide a low-impedance path to PGND at the thermal pad. If AVIN is powered from PVIN for single supply operation, AVIN and PVIN should be separated with a 10- $\mu$ s R-C filter to reduce PVIN switching noise on AVIN.
- The BP1V5 bypass capacitor should be placed close to the BP1V5 pin and provide a low-impedance path to DRTN. DRTN should not be connected to any other pin or node. DRTN is internally connected to AGND and by external connection to System Ground. Connecting DRTN to PGND or AGND could introduce a ground loop and errant operation.
- Keep signal components local to the device, and place them as close as possible to the pins to which they are connected. These components include the VOSNS and GOSNS series resistors and differential filter capacitor as well as MSEL1, MSEL2, VSEL, and ADRSEL resistors. Those components can be terminated to AGND with a minimum return loop or bypassed to the copper area of a separate low-impedance analog ground (AGND) that is isolated from fast switching voltages and current paths and has single connection to PGND on the thermal pad through the AGND pin. For placement recommendations, see [Figure 10-1](#).
- The PGND pin (pin 26) must be directly connected to the thermal pad of the device on the PCB, with a low-noise, low-impedance path.
- Minimize the SW copper area for best noise performance. Route sensitive traces away from the SW and BOOT pins as these nets contain fast switching voltages and lend easily to capacitive coupling.
- Snubber component placement is critical for effective ringing reduction. These components must be on the same layer as the TPS546B24A devices, and be kept as close as possible to the SW and PGND copper areas.
- Route the VOSNS and GOSNS lines from the output capacitor bank at the load back to the device pins as a tightly coupled differential pair. These traces must be kept away from switching or noisy areas which can add differential-mode noise.
- Use caution when routing of the SYNC, VSHARE, BCX\_CLK, and BCX\_DAT traces for stackable configurations. The SYNC trace carries a rail-to-rail signal and should be routed away from sensitive analog signals, including the VSHARE, VOSNS, and GOSNS signals. The VSHARE traces must also be kept away from fast switching voltages or currents formed by the PVIN, AVIN, SW, BOOT, and VDD5 pins.

## 10.2 Layout Example

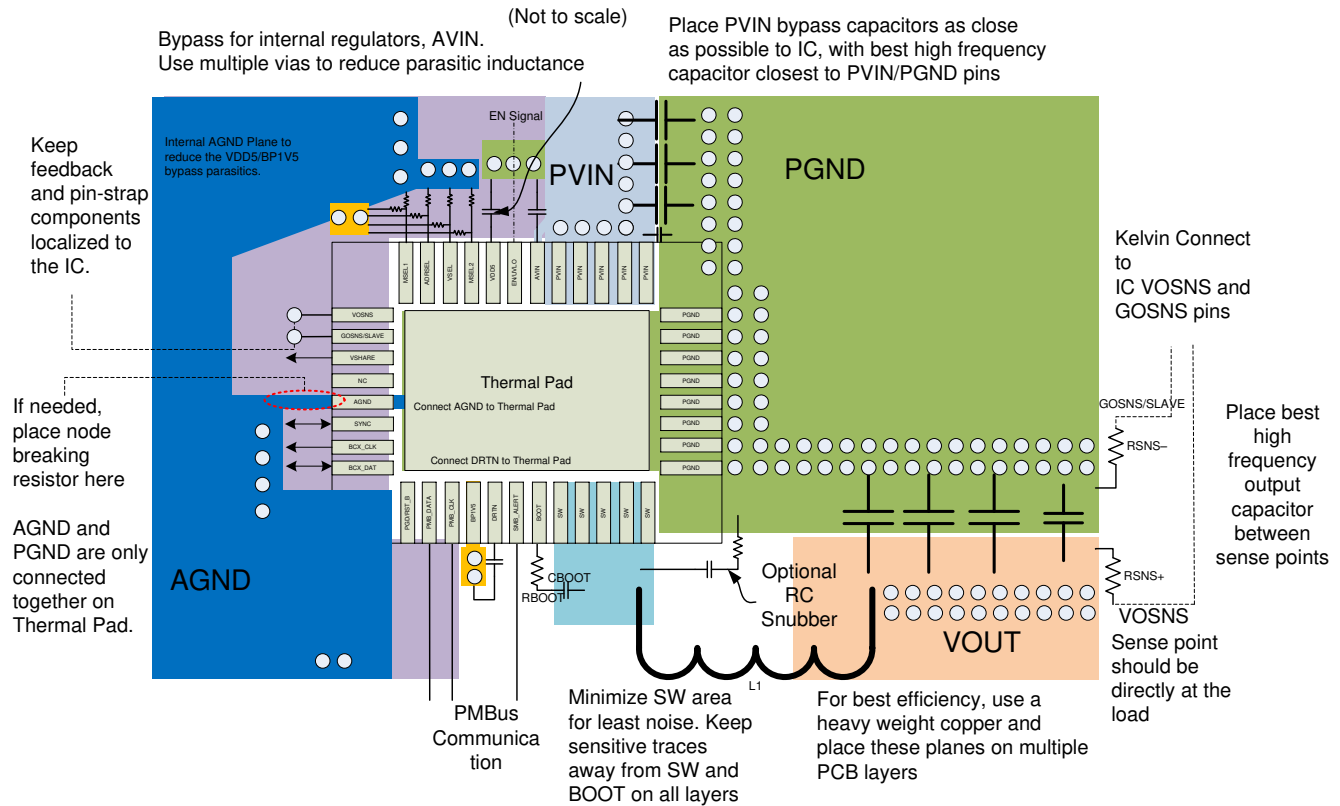


图 10-1. PCB Layout Recommendation

## 10.3 Mounting and Thermal Profile Recommendation

Proper mounting technique adequately covers the exposed thermal pad with solder. Excessive heat during the reflow process can affect electrical performance. 图 10-2 shows the recommended reflow-oven thermal profile. Proper post-assembly cleaning is also critical to device performance. Refer to SLUA271A for more information.

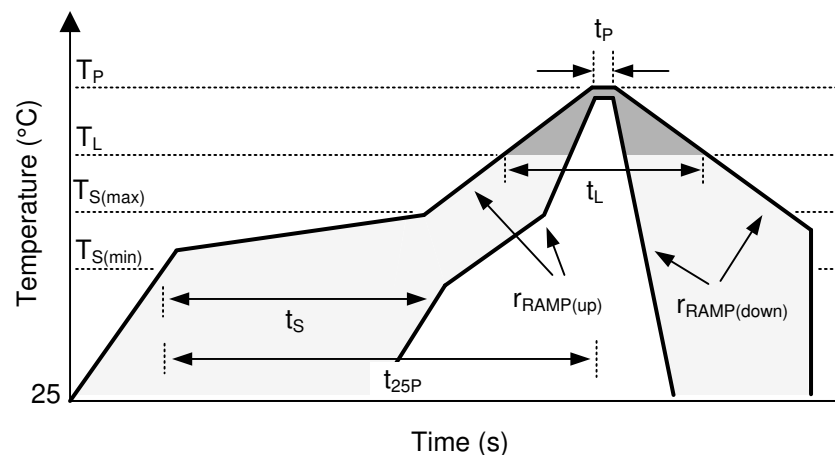


图 10-2. Recommended Reflow-Oven Thermal Profile

表 10-1. Recommended Thermal Profile Parameters

PARAMETER	MIN	TYP	MAX	UNIT
RAMP UP AND RAMP DOWN				

**表 10-1. Recommended Thermal Profile Parameters (continued)**

PARAMETER		MIN	TYP	MAX	UNIT
$r_{\text{RAMP(up)}}$	Average ramp-up rate, $T_{\text{S(max)}}$ to $T_{\text{P}}$			3	°C/s
$r_{\text{RAMP(down)}}$	Average ramp-down rate, $T_{\text{P}}$ to $T_{\text{S(max)}}$			6	°C/s
<b>PRE-HEAT</b>					
$T_{\text{S}}$	Preheat temperature	150		200	°C
$t_{\text{S}}$	Preheat time, $T_{\text{S(min)}}$ to $T_{\text{S(max)}}$	60		180	s
<b>REFLOW</b>					
$T_{\text{L}}$	Liquidus temperature		217		°C
$T_{\text{P}}$	Peak temperature			260	°C
$t_{\text{L}}$	Time maintained above liquidus temperature, $T_{\text{L}}$	60		150	s
$t_{\text{P}}$	Time maintained within 5°C of peak temperature, $T_{\text{P}}$	20		40	s
$t_{25\text{P}}$	Total time from 25°C to peak temperature, $T_{\text{P}}$			480	s

## 11 Device and Documentation Support

### 11.1 Device Support

#### 11.1.1 Third-Party Products Disclaimer

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#### 11.1.2 Development Support

##### 11.1.2.1 Texas Instruments Fusion Digital Power Designer

The TPS546B24ATPS546x24x devices are supported by Texas Instruments Digital Power Designer. Fusion Digital Power Designer is a graphical user interface (GUI) which can be used to configure and monitor the devices via PMBus using a Texas Instruments USB-to-GPIO adapter.

Click this link to download the Texas Instruments [Fusion Digital Power Designer](#) software package.

##### 11.1.2.2 Custom Design With WEBENCH® Tools

[Click here](#) to create a custom design using the TPS546B24A device with the WEBENCH® Power Designer.

1. Start by entering the input voltage ( $V_{IN}$ ), output voltage ( $V_{OUT}$ ), and output current ( $I_{OUT}$ ) requirements.
2. Optimize the design for key parameters such as efficiency, footprint, and cost using the optimizer dial.
3. Compare the generated design with other possible solutions from Texas Instruments.

The WEBENCH Power Designer provides a customized schematic along with a list of materials with real-time pricing and component availability.

In most cases, these actions are available:

- Run electrical simulations to see important waveforms and circuit performance
- Run thermal simulations to understand board thermal performance
- Export customized schematic and layout into popular CAD formats
- Print PDF reports for the design, and share the design with colleagues

Get more information about WEBENCH tools at [www.ti.com/WEBENCH](http://www.ti.com/WEBENCH).

### 11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 11.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

## 11.6 Glossary

### TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. These data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">TPS546B24ARVFR</a>	Active	Production	LQFN-CLIP (RVF)   40	2500   LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	TPS546B24A
TPS546B24ARVFR.A	Active	Production	LQFN-CLIP (RVF)   40	2500   LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	TPS546B24A
TPS546B24ARVFR.B	Active	Production	LQFN-CLIP (RVF)   40	2500   LARGE T&R	-	Call TI	Call TI	-40 to 150	
TPS546B24ARVFRG4	Active	Production	LQFN-CLIP (RVF)   40	2500   LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	TPS546B24A
TPS546B24ARVFRG4.A	Active	Production	LQFN-CLIP (RVF)   40	2500   LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	TPS546B24A
TPS546B24ARVFRG4.B	Active	Production	LQFN-CLIP (RVF)   40	2500   LARGE T&R	-	Call TI	Call TI	-40 to 150	

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

<sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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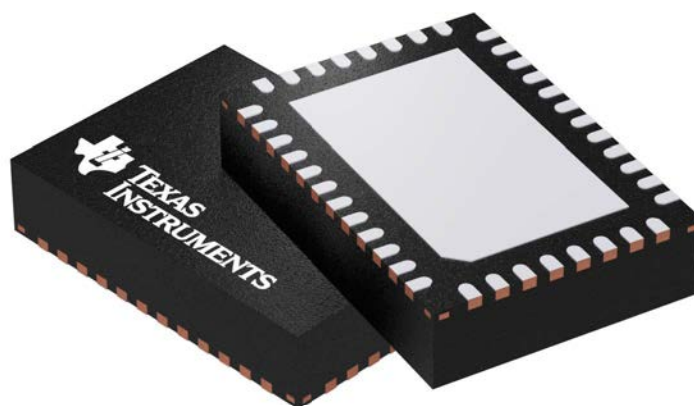


## GENERIC PACKAGE VIEW

**RVF 40**

**LQFN-CLIP - 1.52 mm max height**

PLASTIC QUAD FLATPACK - NO LEAD



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4211383/D



## LQFN-CLIP - 1.52 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



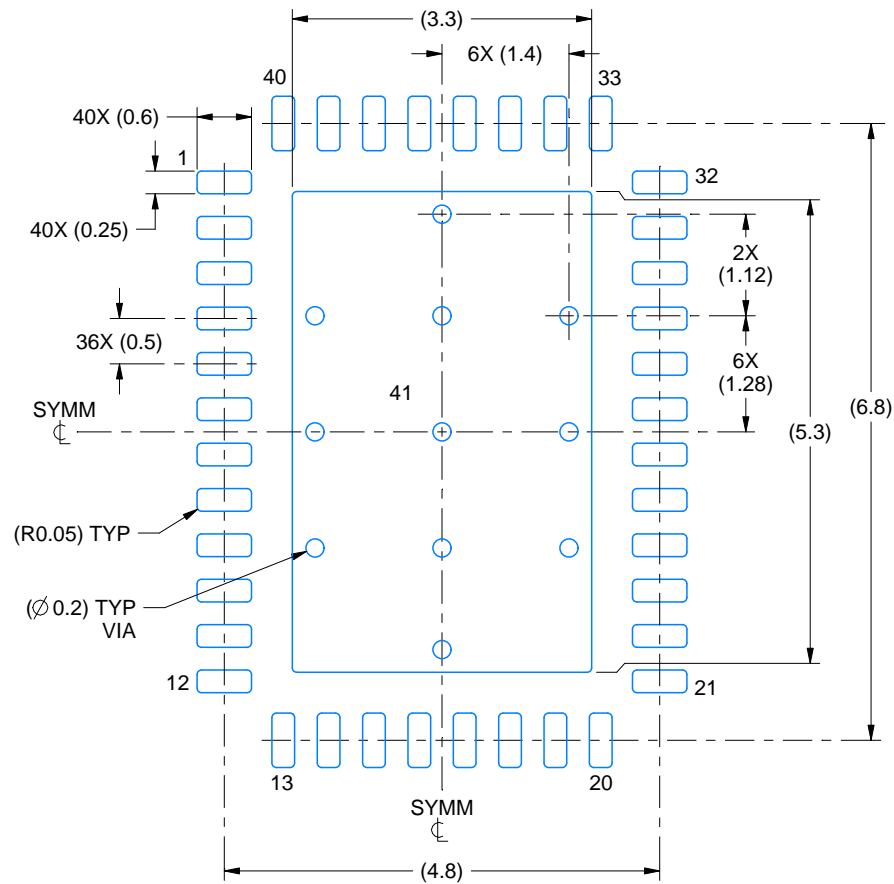
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
4. Reference JEDEC registration MO-220.

# EXAMPLE BOARD LAYOUT

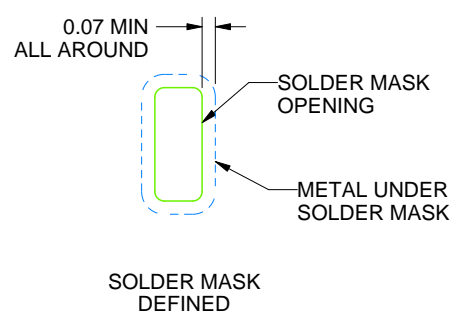
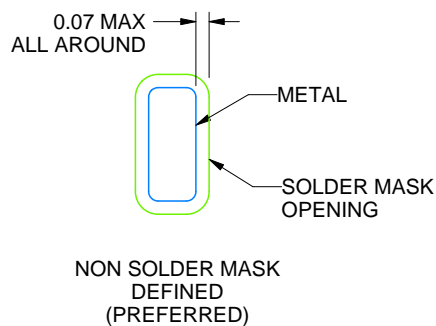
RVF0040A

LQFN-CLIP - 1.52 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE  
SCALE:12X



SOLDER MASK DETAILS

4222989/B 10/2017

NOTES: (continued)

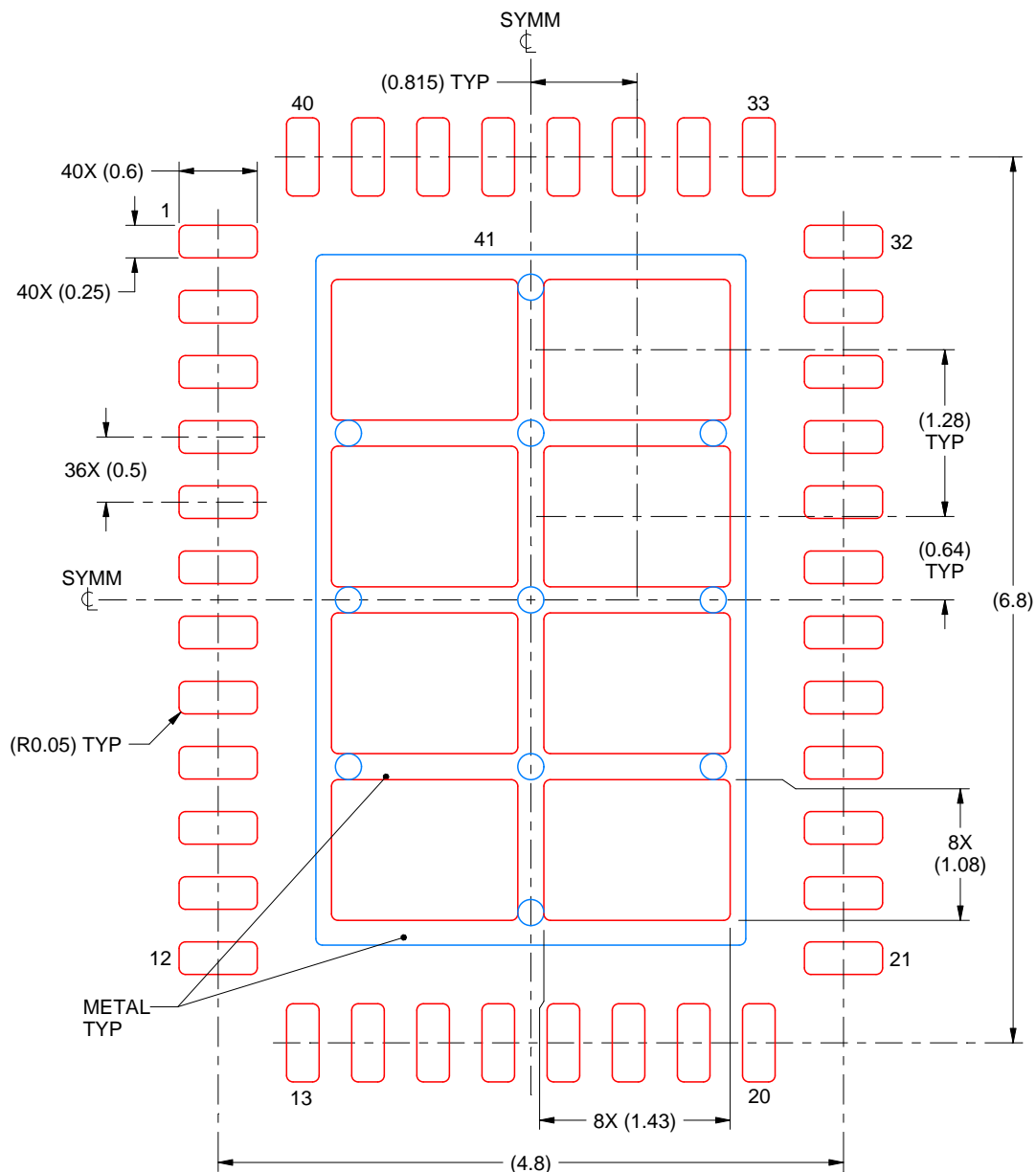
5. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).

# EXAMPLE STENCIL DESIGN

**RVF0040A**

**LQFN-CLIP - 1.52 mm max height**

PLASTIC QUAD FLATPACK - NO LEAD



**SOLDER PASTE EXAMPLE**  
 BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD  
 71% PRINTED SOLDER COVERAGE BY AREA  
 SCALE:18X

4222989/B 10/2017

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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